

Part I Basics of semiconductor QC

Part II Advances in semiconductor QC

**RIKEN Center for Emergent Matter Science &
Quantum Computing**

Seigo Tarucha

1. Fundamentals for quantum computer
2. Advances in spin quantum computer



Approx. 2,000 scientists
3,400 people

Tokyo



Pohan



RIKEN

SAITAMA

CHIBA

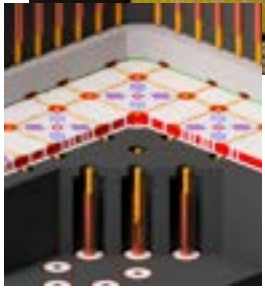
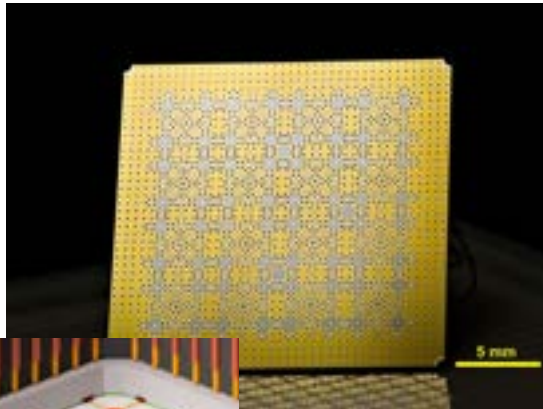
KANAGAWA

Tokyo Bay

10km

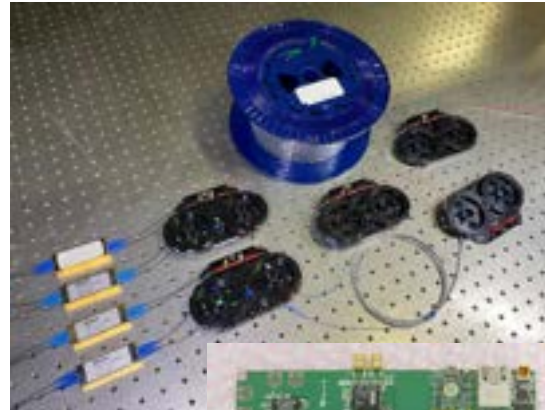
RIKEN Research Center for Quantum Computing

SC



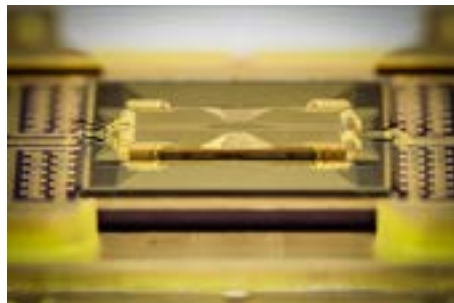
RIKEN/FUJII
• 64 qubit services

Optical



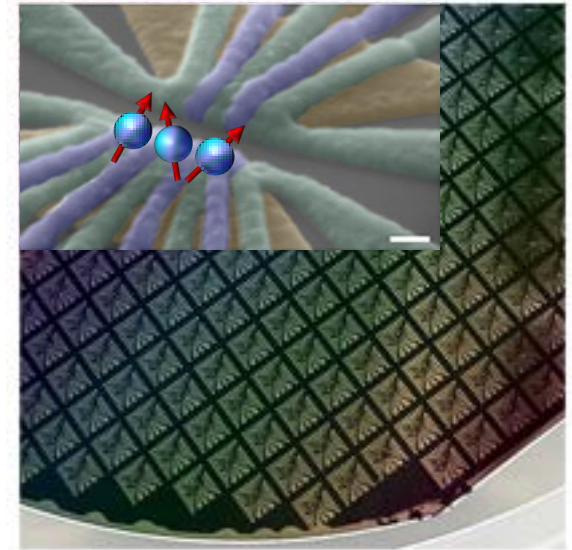
New project for integrated use of QC and supercomputers

Nov. 2023



Quantinuum Model H1

Semiconductor



- Spin-based QC in 28Si

ST and DL

Part I Basics of semiconductor QC

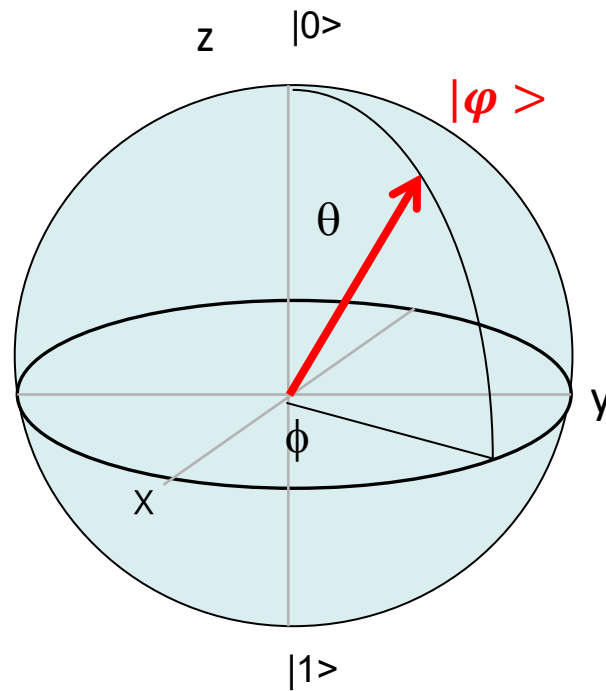
- Concepts of quantum bits and computation
- Implementation of single and two qubit gates
- Readout and initialization
- Quantum coherence and phase noise

Part II Advances in semiconductor QC

- Features of quantum computing in silicon
- High-fidelity quantum gates and readout
- Quantum error correction
- Multi-qubit devices for scale-up

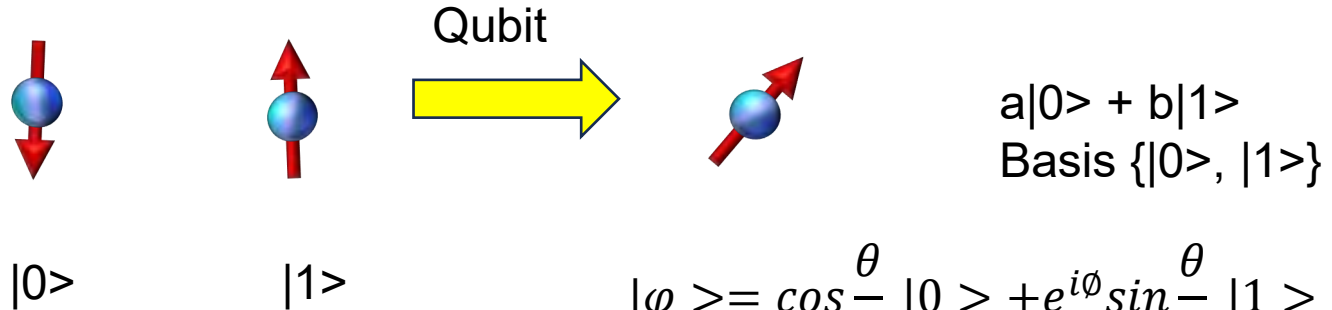
Spin Qubit

$$|\varphi\rangle = a|0\rangle + b|1\rangle$$

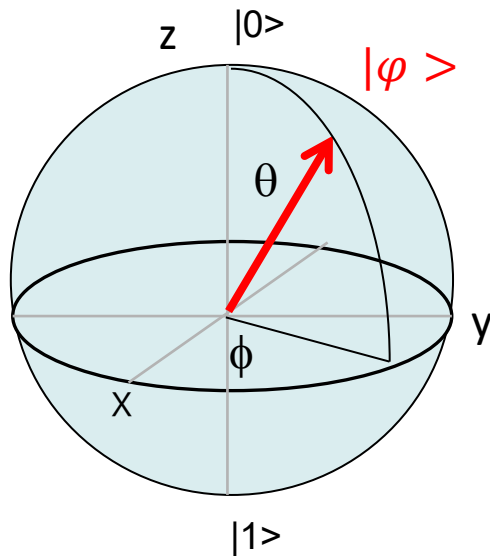


Qubit = Superposition of $|0\rangle$ and $|1\rangle$

Only for operation time < coherence time



$$|\varphi\rangle = \cos\frac{\theta}{2} |0\rangle + e^{i\phi} \sin\frac{\theta}{2} |1\rangle$$



$$i\hbar \frac{d|\varphi(t)\rangle}{dt} = \hat{H}|\varphi(t)\rangle$$

$$H = H_0 + H_1$$

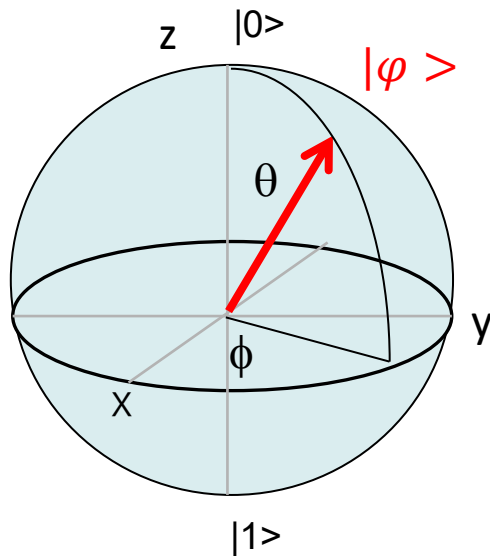
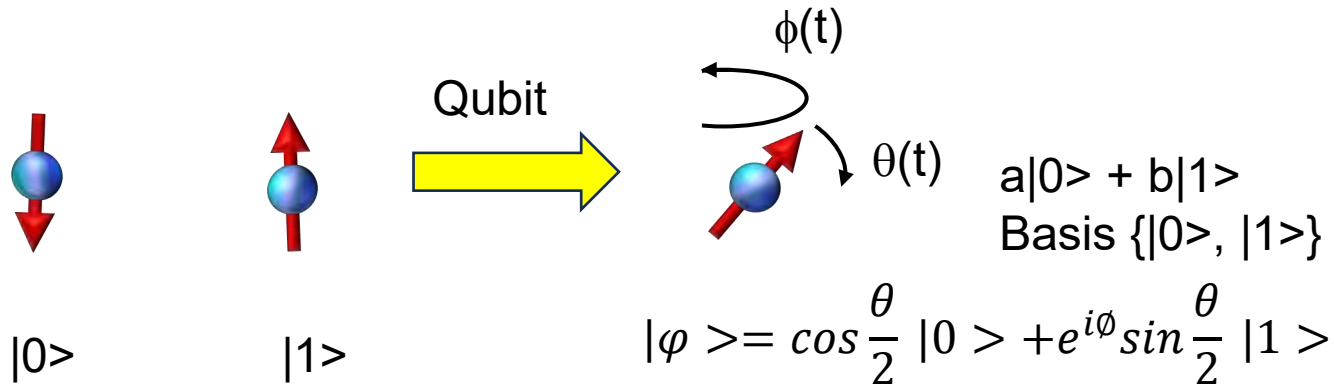
H_0 to define the steady states

$$H_0|0\rangle = E_0|0\rangle, H_0|1\rangle = E_1|1\rangle$$

H_1 to superpose the steady states

Spin Qubit Manipulation

Only for time < coherence time



$$i\hbar \frac{d|\varphi(t)\rangle}{dt} = \hat{H}_1 |\varphi(t)\rangle$$

$$U(t, 0) = \exp\left[-\frac{i}{\hbar} \hat{H}_1 t\right]$$

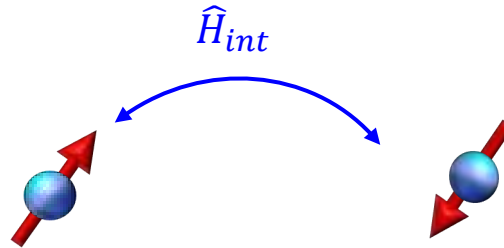
$$|\varphi(t)\rangle = a(t)|0\rangle + b(t)|1\rangle$$

$$= \begin{pmatrix} a(t) \\ b(t) \end{pmatrix} = U(t, 0) \begin{pmatrix} a(0) \\ b(0) \end{pmatrix}$$

Qubit control
= Control of rotation about x-axis, $\theta(t)$,
and z-axis, $\phi(t)$, respectively.

Spin Manipulation for Quantum Computing

Basis $\{|0\rangle_A|0\rangle_B, |0\rangle_A|1\rangle_B, |1\rangle_A|0\rangle_B, |1\rangle_A|1\rangle_B\}$
 $|00\rangle \quad |01\rangle \quad |10\rangle \quad |11\rangle$



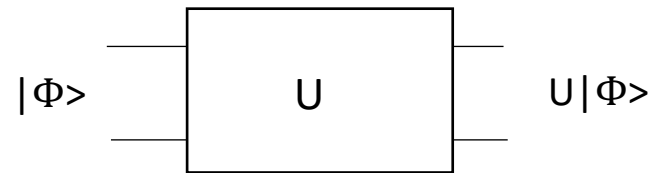
$$|\varphi\rangle = a|0\rangle + b|1\rangle$$

$$|\varphi\rangle = c|0\rangle + d|1\rangle$$

$$|\varphi_1, \varphi_2\rangle = \alpha|00\rangle + \beta|01\rangle + \gamma|10\rangle + \delta|11\rangle = \begin{pmatrix} \alpha(t) \\ \beta(t) \\ \gamma(t) \\ \delta(t) \end{pmatrix} = U(t,0) \begin{pmatrix} \alpha(0) \\ \beta(0) \\ \gamma(0) \\ \delta(0) \end{pmatrix}$$

$$i\hbar \frac{d|\varphi_1, \varphi_2\rangle}{dt} = \hat{H}|\varphi_1, \varphi_2\rangle$$

$$\hat{H} = \hat{H}_1 + \hat{H}_{int}$$



Quantum Entanglement

2qubit system

$$|A\rangle = a|0\rangle + b|1\rangle$$

$$|B\rangle = c|0\rangle + d|1\rangle$$

Simple product $|A\rangle \otimes |B\rangle = ac|0\rangle_A |0\rangle_B + ad|0\rangle_A |1\rangle_B + bc|1\rangle_A |0\rangle_B + bd|1\rangle_A |1\rangle_B$

Inseparable two-qubit state = $a|00\rangle + b|01\rangle + g|10\rangle + d|11\rangle$

$$\left\{ \begin{array}{l} \frac{|0\rangle|0\rangle \pm |1\rangle|1\rangle}{\sqrt{2}} \\ \frac{|0\rangle|1\rangle \pm |1\rangle|0\rangle}{\sqrt{2}} \end{array} \right. \quad \begin{array}{l} \text{Maximally entangled states} \\ = \text{Bell states} \end{array}$$

Spin singlet $|S\rangle$, Spin triplet $|T_0\rangle$

$$|S\rangle = \frac{|\downarrow\rangle|\uparrow\rangle - |\uparrow\rangle|\downarrow\rangle}{\sqrt{2}}$$

$$|T_+\rangle = |\uparrow\rangle|\uparrow\rangle$$

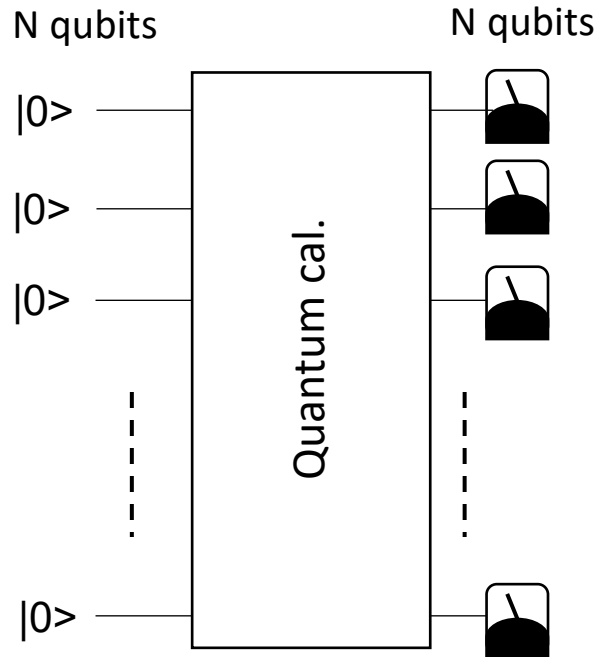
$$|T_0\rangle = \frac{|\downarrow\rangle|\uparrow\rangle + |\uparrow\rangle|\downarrow\rangle}{\sqrt{2}}$$

$$|T_-\rangle = |\downarrow\rangle|\downarrow\rangle$$

Logical Calculation

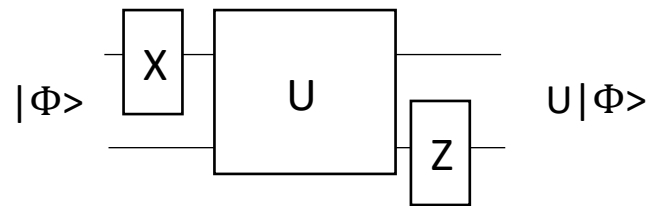
Fidelity > 99%

Initialization



Readout Fidelity > 99%

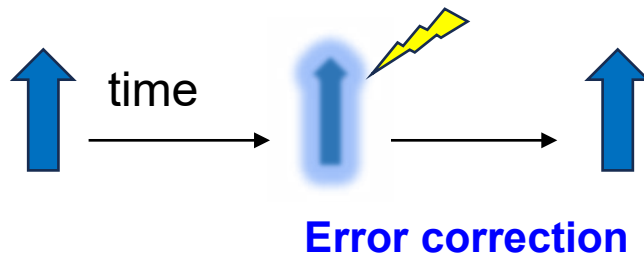
Multi-qubit gates consisting of single qubit gates and two-qubit gates



Single qubit op. Fidelity > 99.9%

Two-qubit op. Fidelity > 99%

Scale-up of qubit devices required for large scale calculation but all operations must complete within dephasing time.



DiVincenzo's criteria

1. Long coherence time
2. Universal quantum gate set
(Single and two-qubit gates)
3. Quantum bit readout
4. Quantum bit initialization
5. Qubit scalability

Summary: Why quantum computation fast?

1. Superposition of n qubits in 2^n basis states $\{|000..0\rangle, |000..1\rangle, \dots, |111..1\rangle\}$

$$|\varphi\rangle = \frac{1}{\sqrt{2^n}} [|000..0\rangle + |000..1\rangle + \dots + |111..1\rangle]$$

2. Quantum entanglement

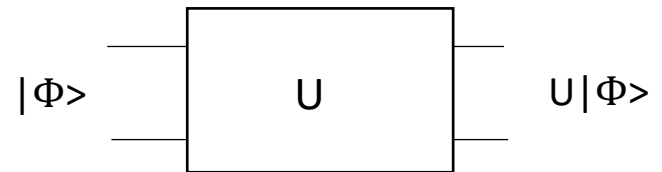
$$\frac{|0\rangle|0\rangle \pm |1\rangle|1\rangle}{\sqrt{2}} \quad \text{Correlation in 2 or more qubits}$$

Used in logical calculations

3. Quantum parallelism

Parallel calculation of superposed n qubits

$$U|\varphi\rangle = \frac{1}{\sqrt{2^n}} [U|000..0\rangle + U|000..1\rangle + \dots + U|111..1\rangle]$$



Part I Basics of semiconductor QC

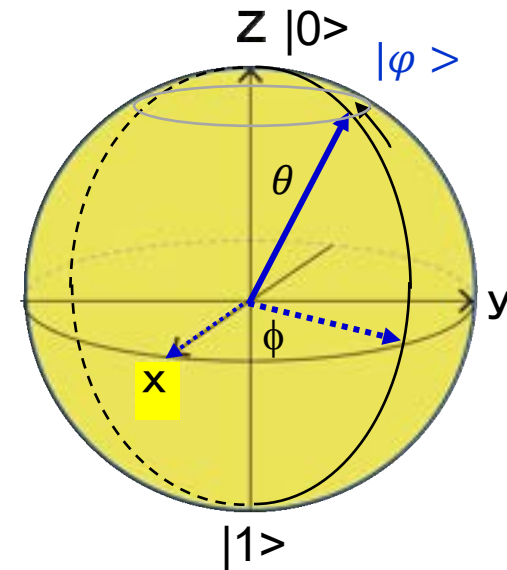
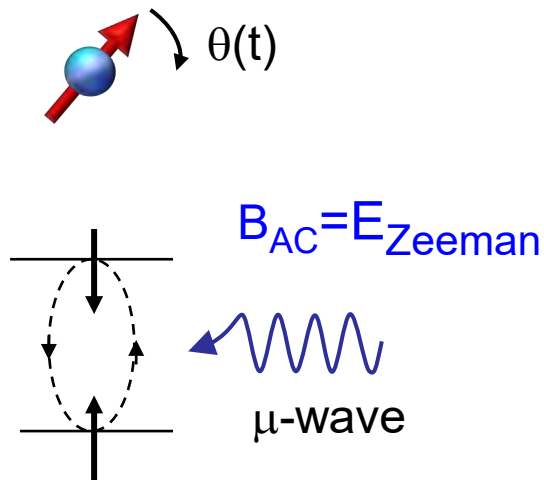
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Spin Qubit Manipulation using Concept of Spin Resonance

Rotation about x-axis

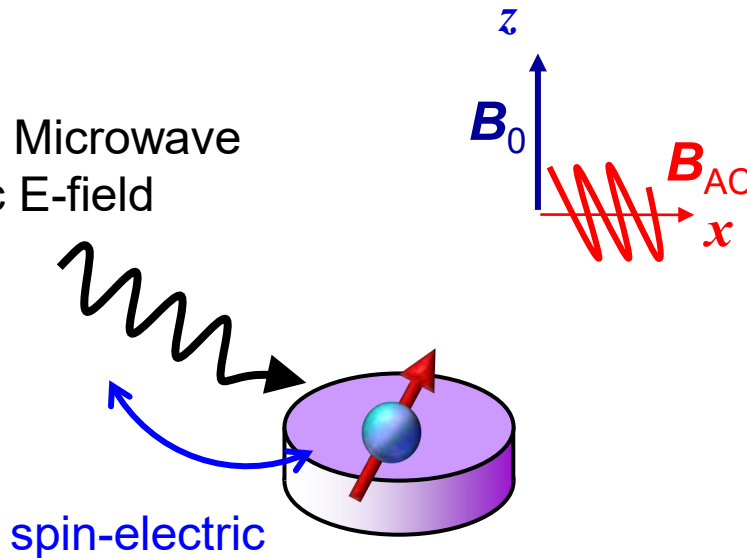


θ control by B_{AC} burst

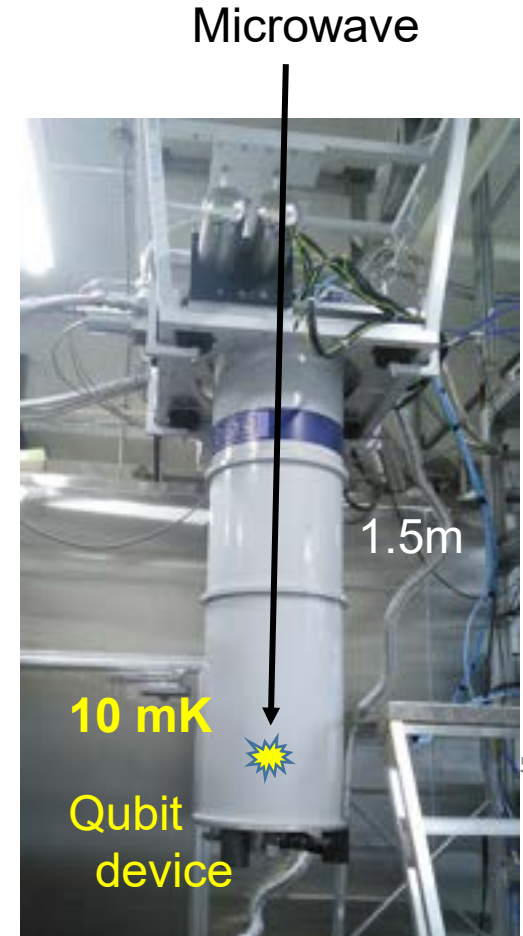
ϕ control by B_{AC} phase

Physical Implementation of Spin Qubits : Spin Resonance for Single Electrons in QD

ESR using Microwave
induced ac E-field

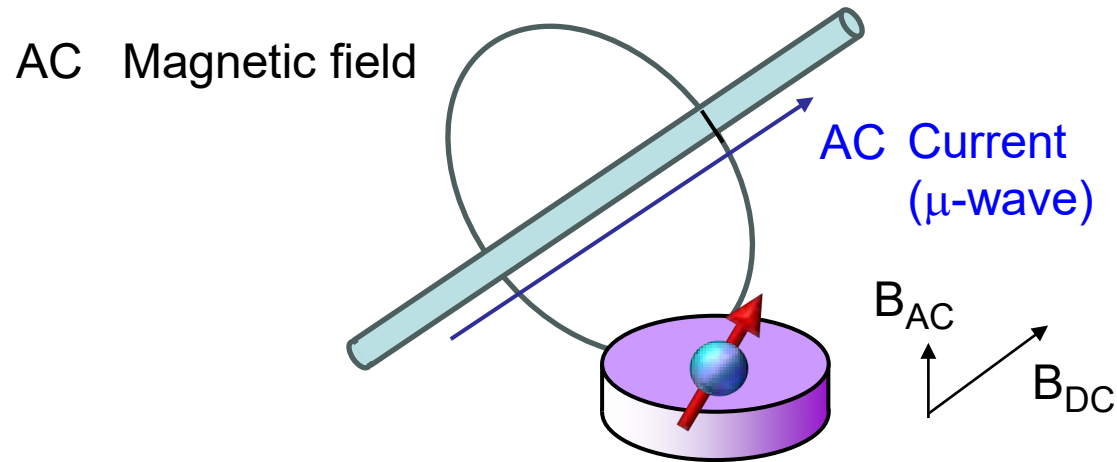


a.c. electric field of μ -wave is converted to a.c. magnetic field through spin-electric coupling mechanism of spin-orbit coupling, on-chip coil, μ -magnet,....



Generation of Local AC Magnetic Field

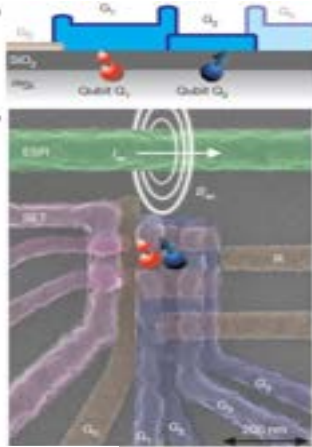
Ampère's circuital law



But the generated AC field is weak and the qubit rotation is slow.

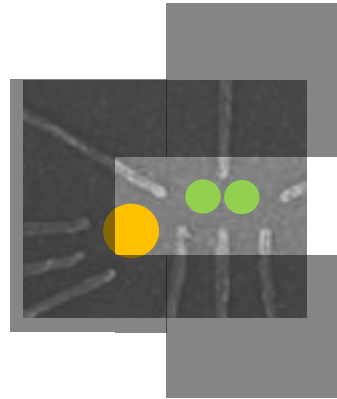
Spin Resonance with Spin-electric Coupling

UNSW

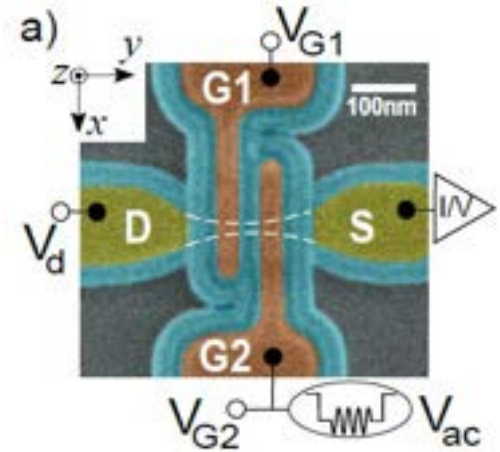


0.3 MHz

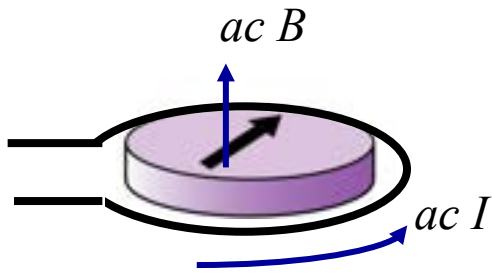
RIKEN, Wisconsin/TuDelft,
Princeton, Sherbrooke



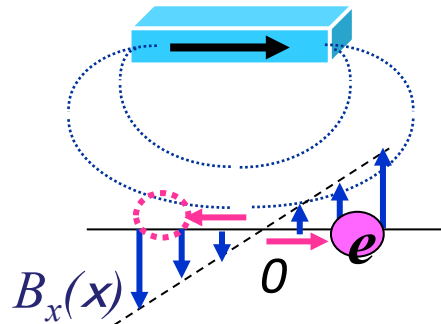
Grenoble/Leti



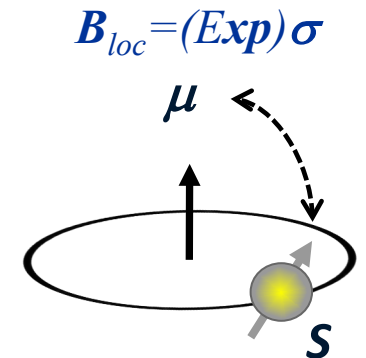
On-chip coil



μ -magnet

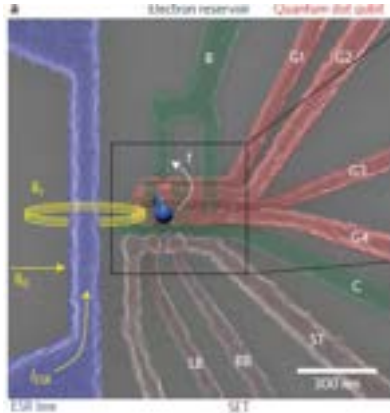


Spin-orbit int.



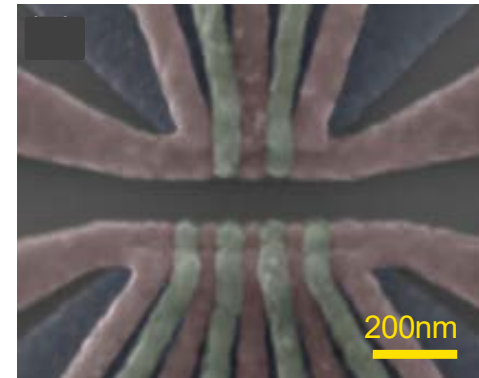
Spin Qubits in Si QD Devices

n-MOS with μ -wave antenna



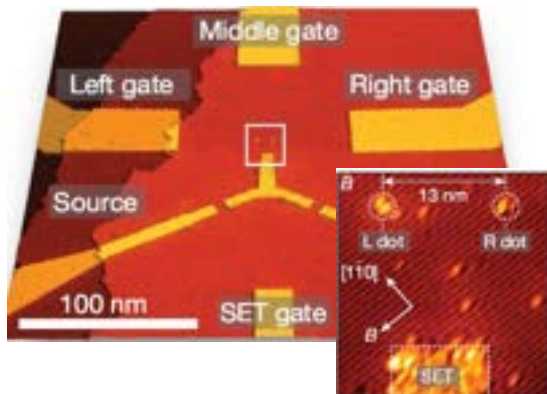
M. Veldhorst et al. Nat. Nanotechnol. 2014

Si/SiGe with μ -magnet



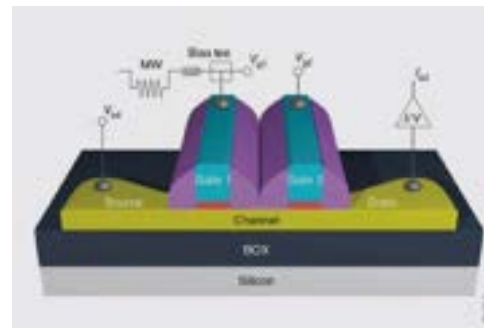
K. Takeda et al. Nat. Nanotechnol. 2021

P donors in Si with μ -wave antenna

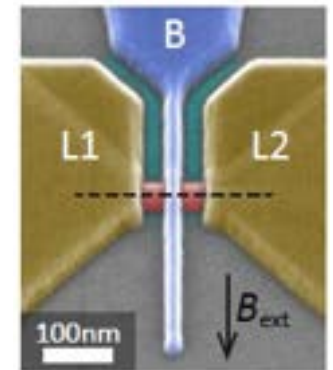


Y. He et al. Nature 2019

p-MOS with spin-orbit effect

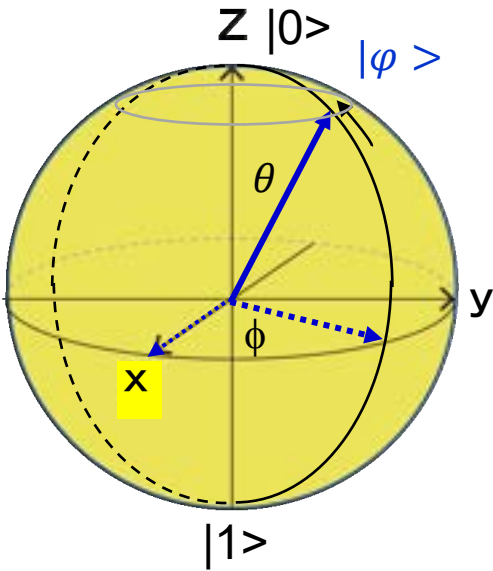


R. Maurand et al. Nat. Commun. 2016



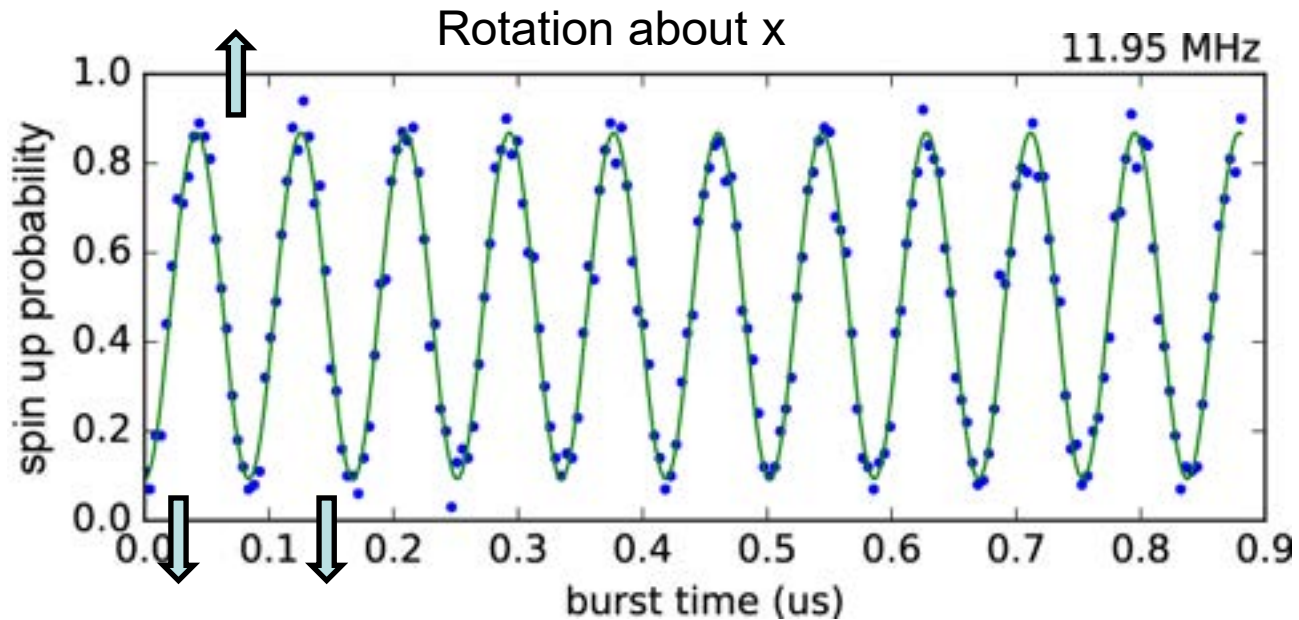
LC. Camenzind et al. Nat. Electron. 2020

Rotation about x-axis

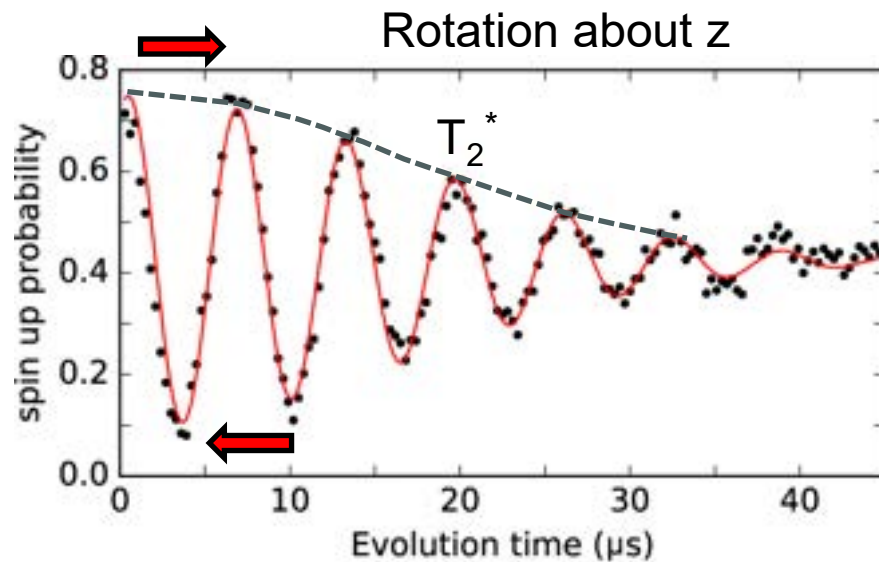
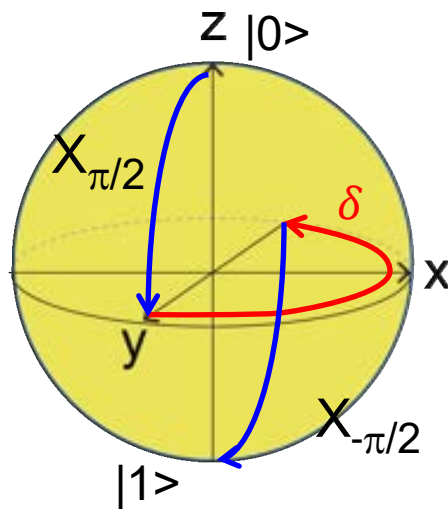


$$|\varphi\rangle = \cos\frac{\theta}{2}|0\rangle + e^{i\phi}\sin\frac{\theta}{2}|1\rangle$$

$$\theta = \frac{\omega_1 t}{2}$$

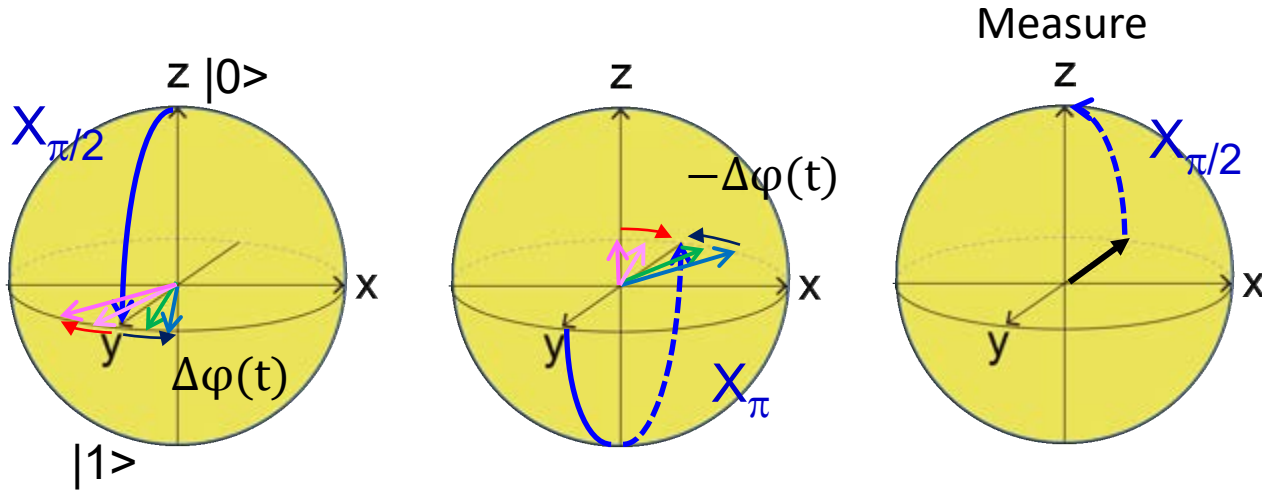


Measurement of Superposition State



$$A \cos(2\pi f t + \varphi) \exp\left(-\left(\frac{t}{T_2^*}\right)^2\right) + B$$

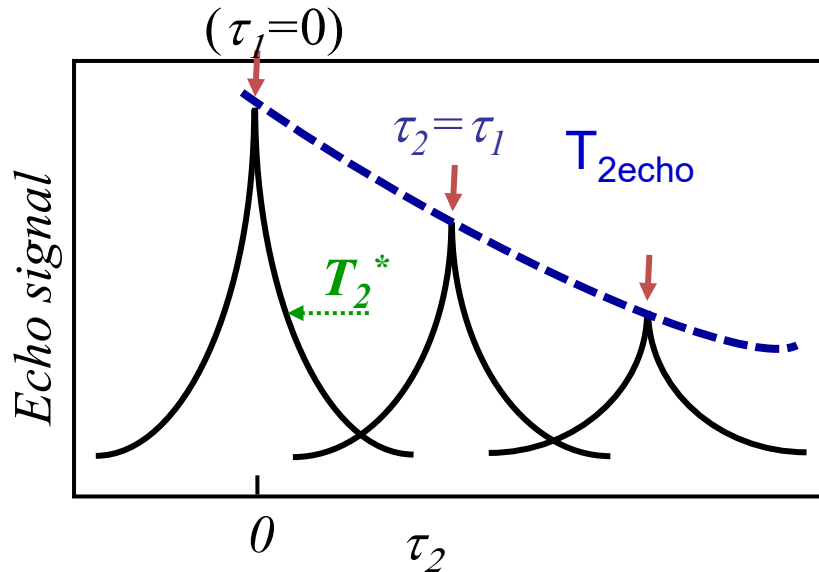
Spin Echo Measurement



Free evolution
In x-y with τ_1

Refocus in $\tau_2 = \tau_1$
after π -pulse

Measure after
 τ_2



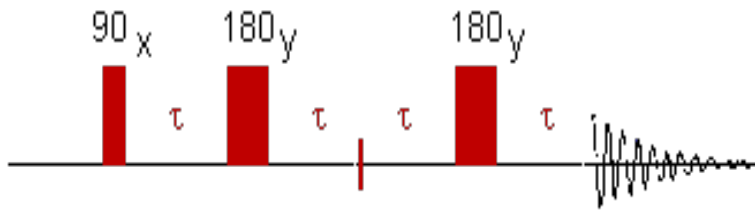
Only good for the phase fluctuation frequency lower than the focusing frequency.

➔ Compensation of the faster phase fluctuations.

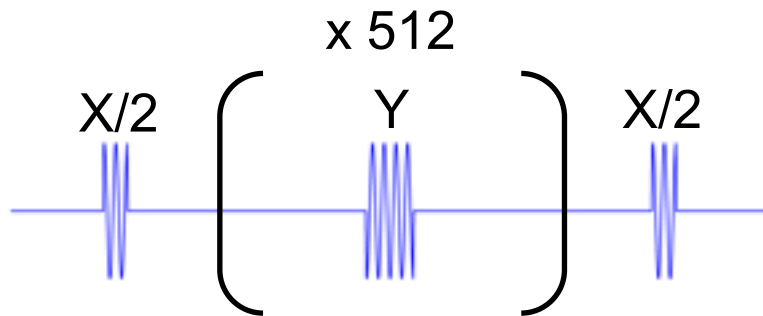
Hahn echo and CPMG

CP-Meiboom-Gill (CPMG) decoupling

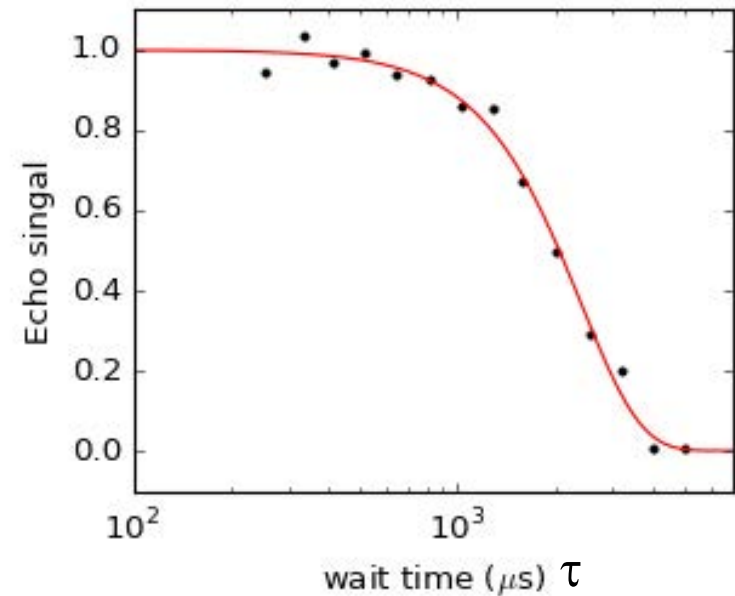
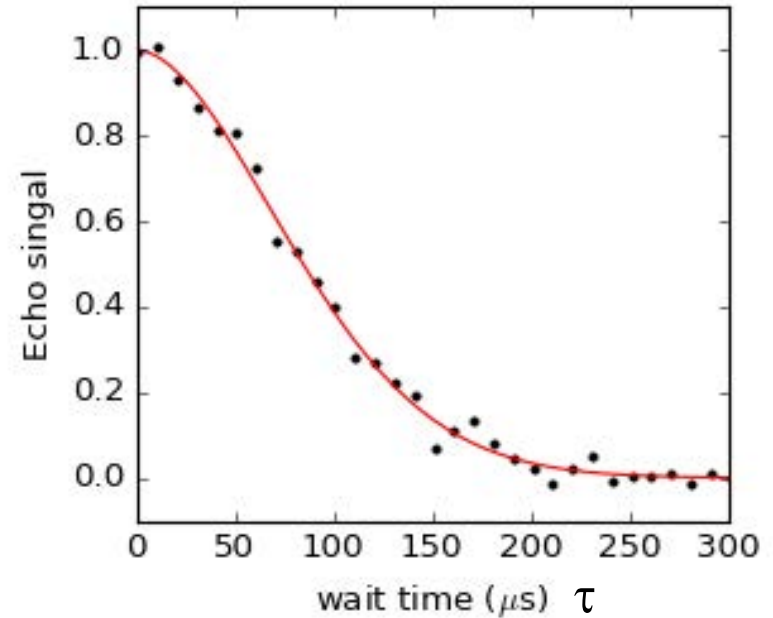
$$X/2 - (\tau - Y - \tau)_n - X/2$$



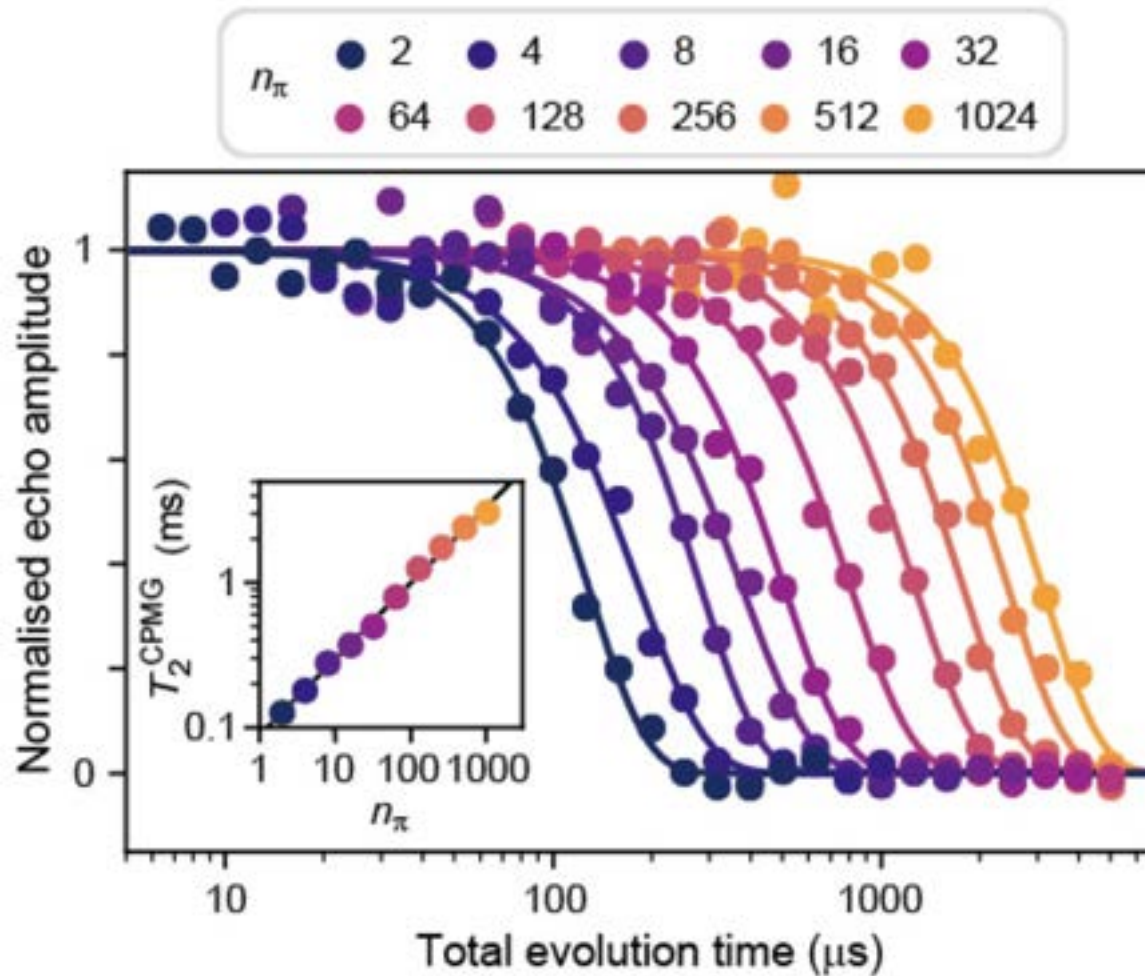
$n = 512$ number of π pulses



$$T_2^{\text{CPMG}} = 2.4 \text{ ms}$$



Hahn Echo and CPMG



$n_\pi=1$: Hahn echo

$$T_2^{\text{echo}} = 100 \mu\text{sec}$$

$n_\pi > 1$: power-law

$$T_2^{\text{echo}} \propto n_\pi^{0.526}$$

> msec

Ref.

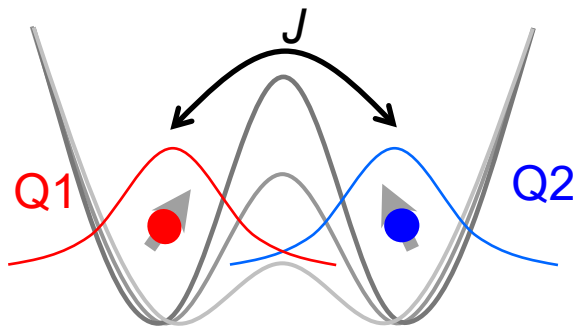
Medford et al. PRL 2012

$$A \exp\left(-\left(\frac{t_{\text{wait}}}{T_2^{\text{CPMG}}}\right)^2\right) + B$$

High-fidelity Two-qubit Gates

Two-qubit gate using spin-exchange interaction and Zeeman energy difference

Exchange coupling controlled by tunnel coupling (up to 10MHz)



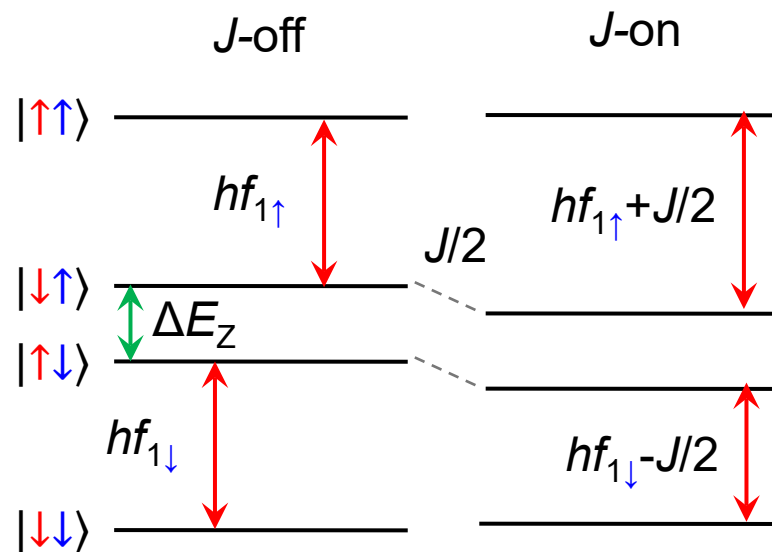
Zeeman energy gradient (ΔE_Z) induced by MM

$\Delta E_Z \sim$ a few 100 MHz

$$\Delta E_Z \gg J$$

“Heisenberg” “Ising”

$$H_{\text{int}} = \frac{J}{4} \boldsymbol{\sigma}_1 \cdot \boldsymbol{\sigma}_2 \approx \frac{J_{12}}{4} \sigma_{z1} \sigma_{z2}$$



CPHSE (CZ)

Energy shift $\Delta E=J/2$ for time t generates a phase accumulation in $|\uparrow\downarrow\rangle$ and $|\downarrow\uparrow\rangle$:

$$|\uparrow\downarrow\rangle \rightarrow e^{\frac{i\Delta Et}{\hbar}} |\uparrow\downarrow\rangle = i |\uparrow\downarrow\rangle \text{ for } Jt = \frac{\pi}{\hbar}$$

In	Out
$ \uparrow\uparrow\rangle$	$+ \uparrow\uparrow\rangle$
$ \uparrow\downarrow\rangle$	$i \uparrow\downarrow\rangle$
$ \downarrow\uparrow\rangle$	$i \downarrow\uparrow\rangle$
$ \downarrow\downarrow\rangle$	$+ \downarrow\downarrow\rangle$

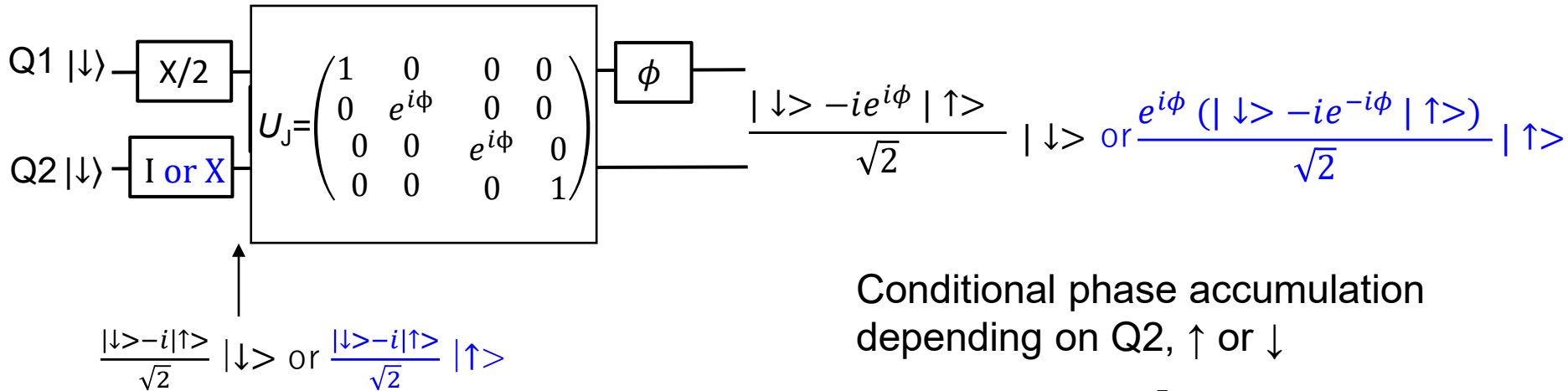
... represented by a unitary transformation:

$$U_{CZ} = \begin{pmatrix} 1 & 0 & 0 & 0 \\ 0 & 1 & 0 & 0 \\ 0 & 0 & 1 & 0 \\ 0 & 0 & 0 & -1 \end{pmatrix} = Z_1\left(-\frac{\pi}{2}\right)Z_2\left(-\frac{\pi}{2}\right) \begin{pmatrix} 1 & 0 & 0 & 0 \\ 0 & i & 0 & 0 \\ 0 & 0 & i & 0 \\ 0 & 0 & 0 & 1 \end{pmatrix}$$

Rotation about z-axis by $-\pi/2$

CPHSE (CZ)

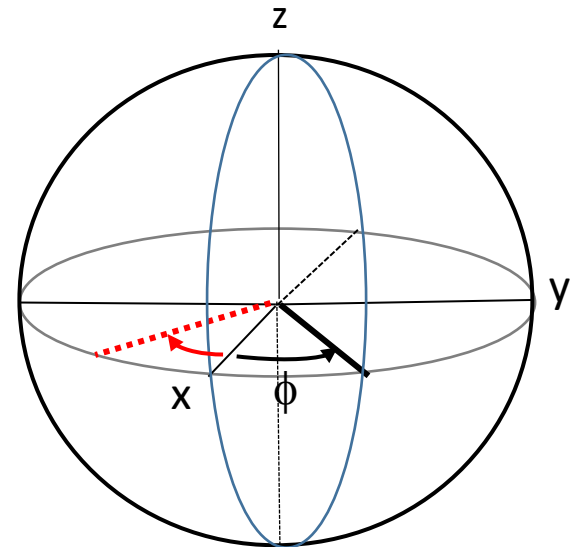
Additional phase of $\phi/2$ to the 1st bit



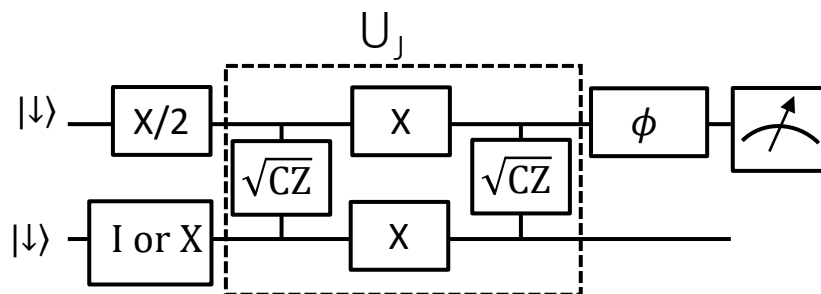
Conditional phase accumulation depending on Q2, \uparrow or \downarrow

If Q2 is $|\uparrow\rangle$, clockwise rotation of Q1 about z-axis or positive phase ϕ accumulation, while if Q2 is $|\downarrow\rangle$, counterclockwise rotation of Q1 or negative phase ϕ accumulation.

CPHASE is the case for $\phi = \pi/2$.

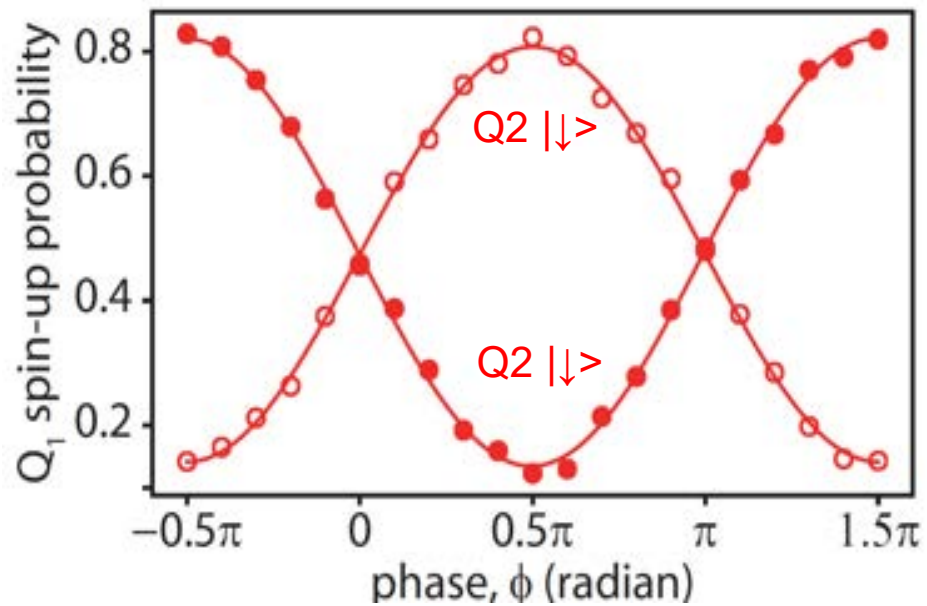


CPHASE



Q2 phase accumulation measurement

$\downarrow \bullet$ $\circ \uparrow$



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- Implementation of single and two qubit gates
- **Readout and initialization**
- Quantum coherence and phase noise

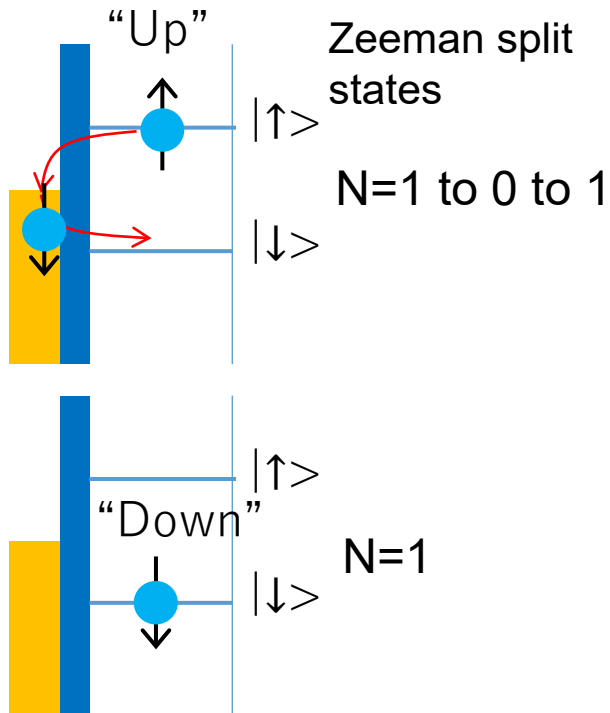
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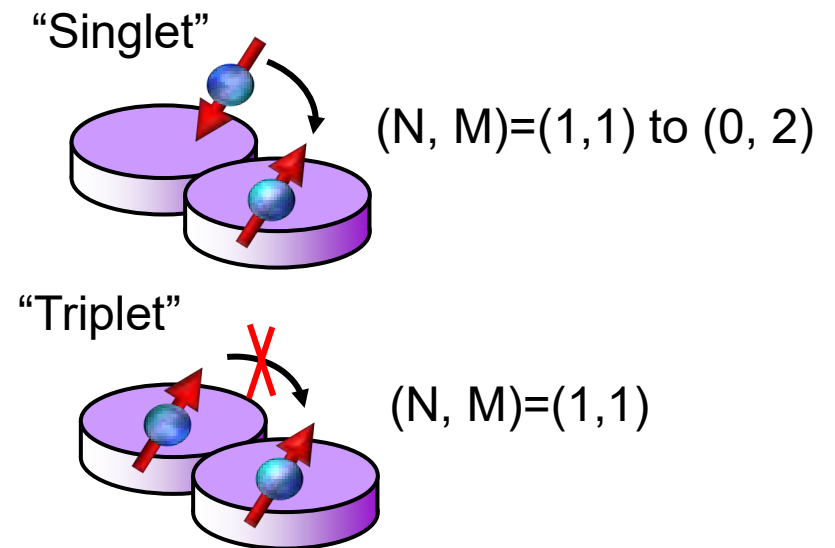
Spin Readout

Information conversion from spin to charge

Spin-dependent dot to lead tunneling



Pauli spin blockade between dots

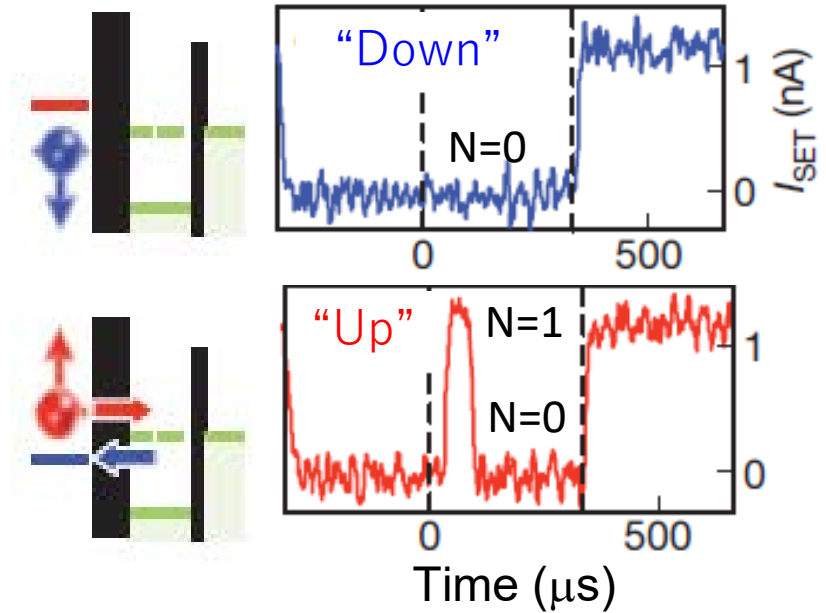
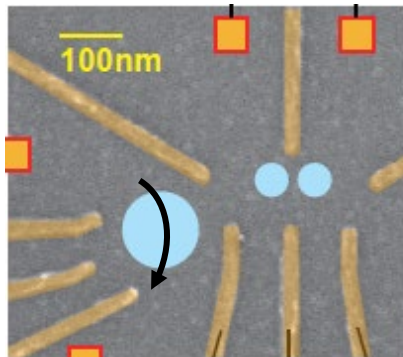
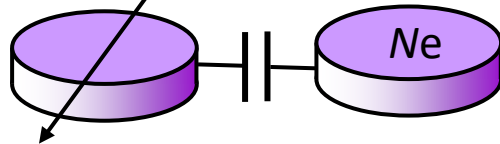


Charge State Detection

Measurement of conductance change with N

Conductance

Sensor



A. Morello et al., Nature 2010

Advanced Method of Charge Sensing

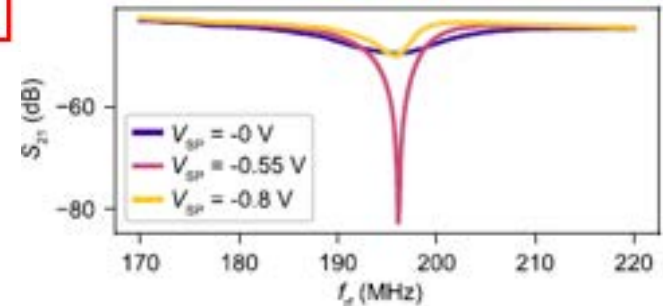
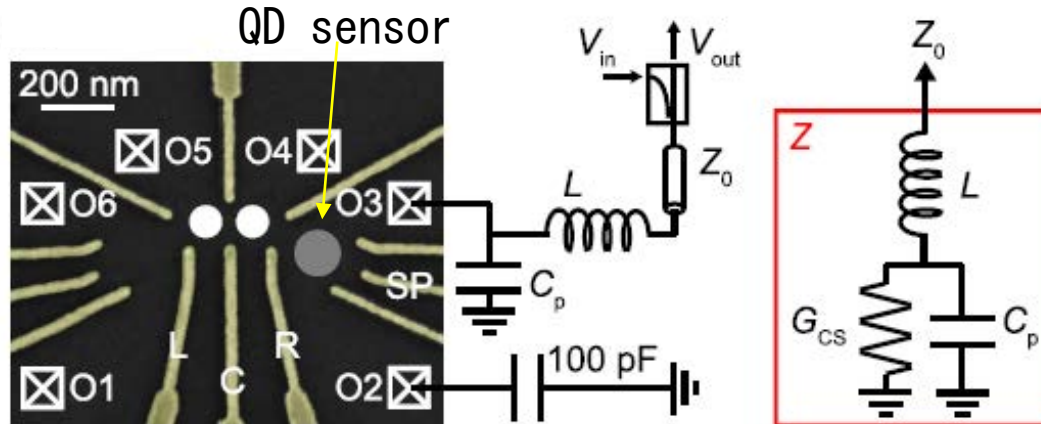
conductance measurement
with RF reflectometry

Resonance circuit

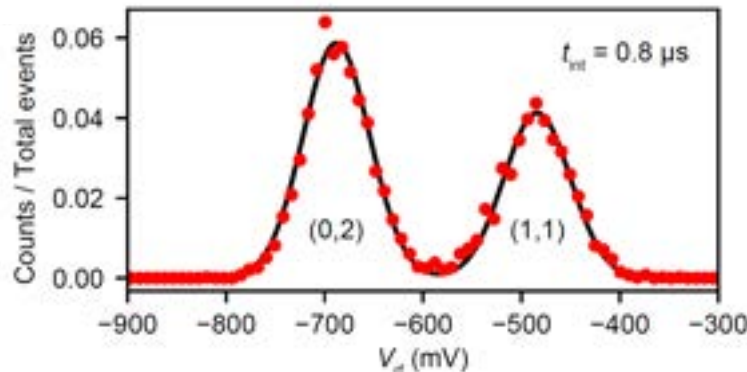
Change of charge
number in objective QD

↓
Change of sensor QD
conductance, G_{CS}

↓
Change of resonance
characteristic



D. Reilley et al.
Appl. Phys. Lett.
(2007)

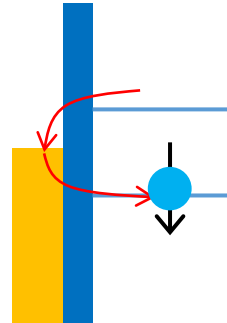
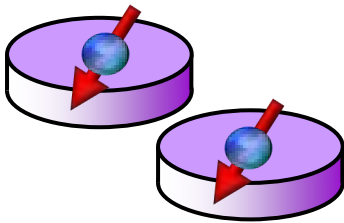


SNR = 6 (F>99%) @0.8 μ s (SiGe)
 \ll T1 (10 to 100msec)

A. Noiri et al., Nano Lett. (2020).

Initialization

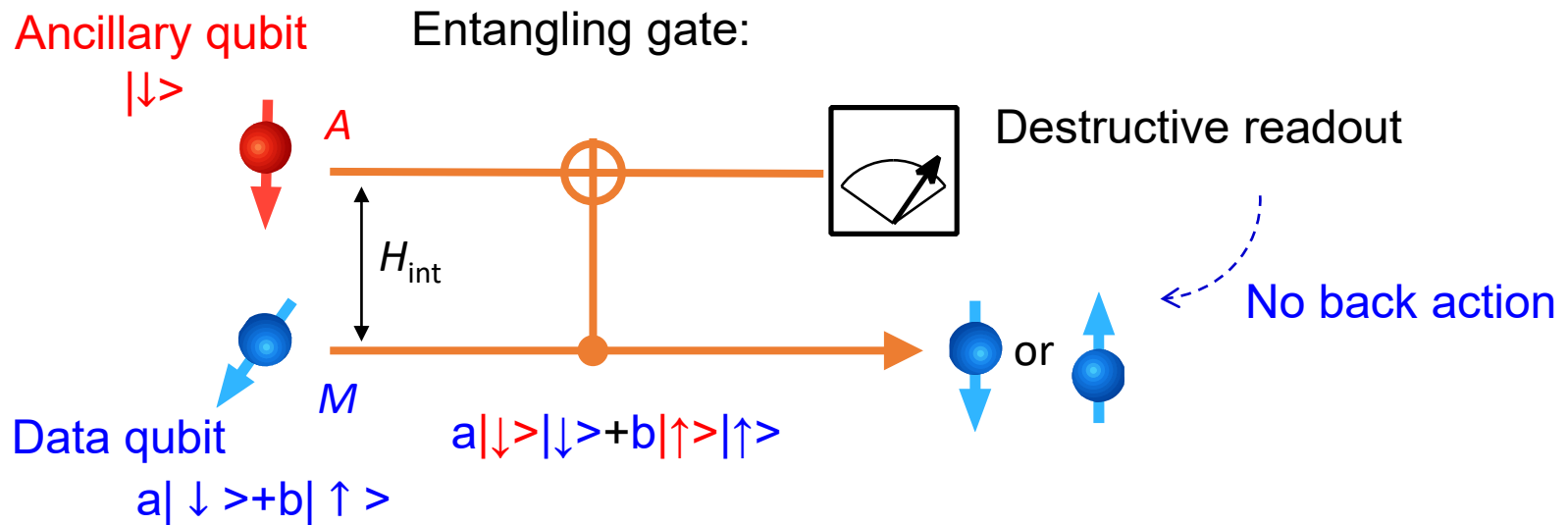
Final state after spin readout is $|0\rangle = \text{Initialization}$



Long-time waiting ($\gg T_1$) provides $|0\rangle$.

Application of Entanglement I: Quantum Non-demolition Readout using an Ancillary Qubit

... useful to improve the readout and initialization fidelity



Previous work Quantum optics: Grangier et al. Nature 1998; Nougues et al. Nature 1999.
Cavity QED with Rydberg atoms: Geremia et al. Science 2004
Trapped single electrons: Peil et al. PRL 1999
Superconducting circuits: Lupascu et al. Science 2007
Nuclear spin with donor P: Pla et al. Nature 2013

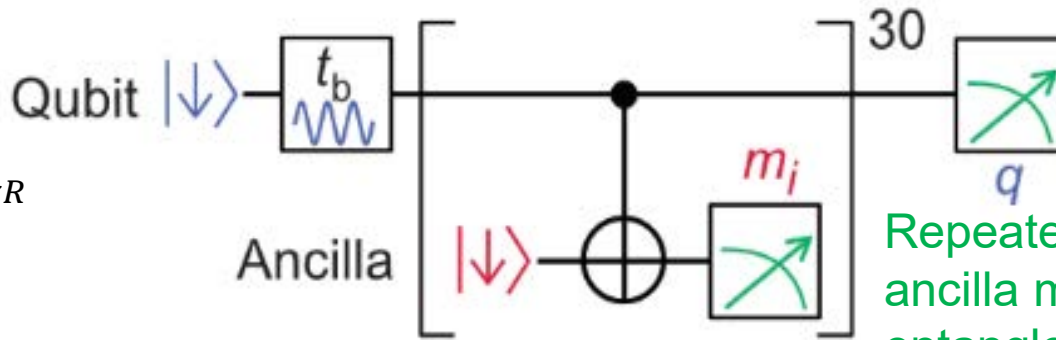
QND Measurement with Si/SiGe DQD

J. Yoneda et al. Nat. Commun. 2020

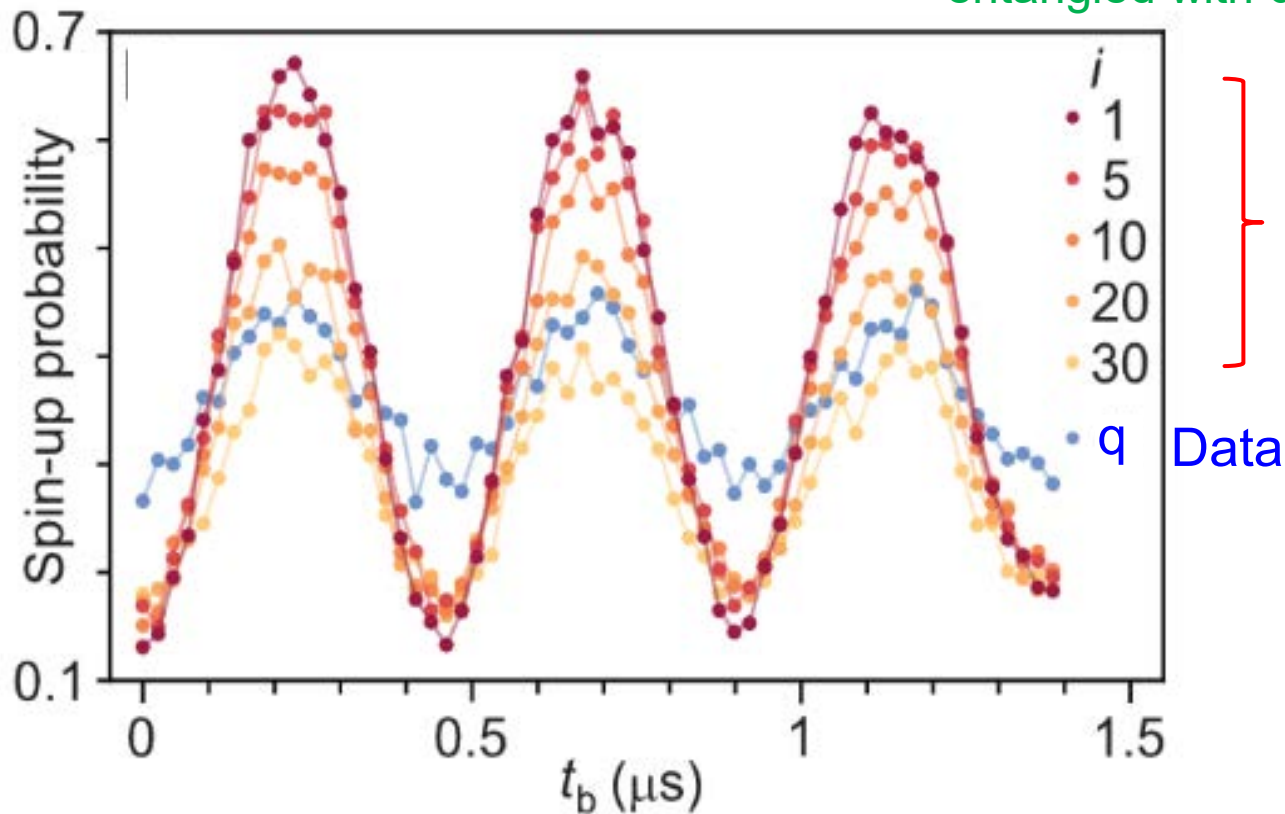
Rabi measurement
after a waiting time

$$H_{\text{int}} = \frac{J_{12}}{4} \sigma_{zL} \sigma_{zR}$$

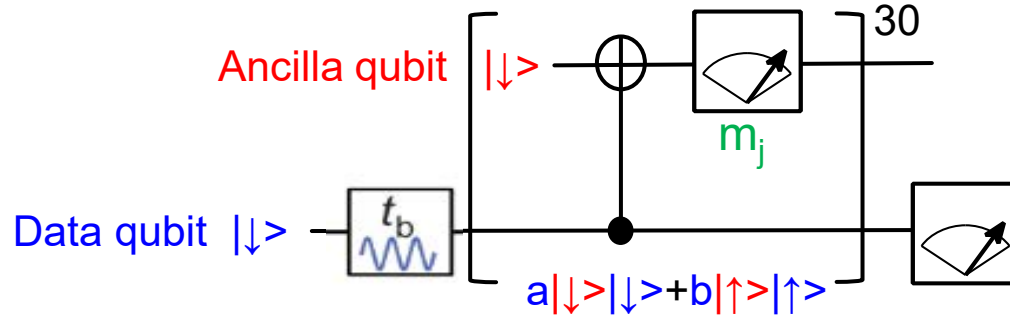
for $E_z \gg J_{12}$



Repeated cycle (60 μs):
ancilla measured after
entangled with data

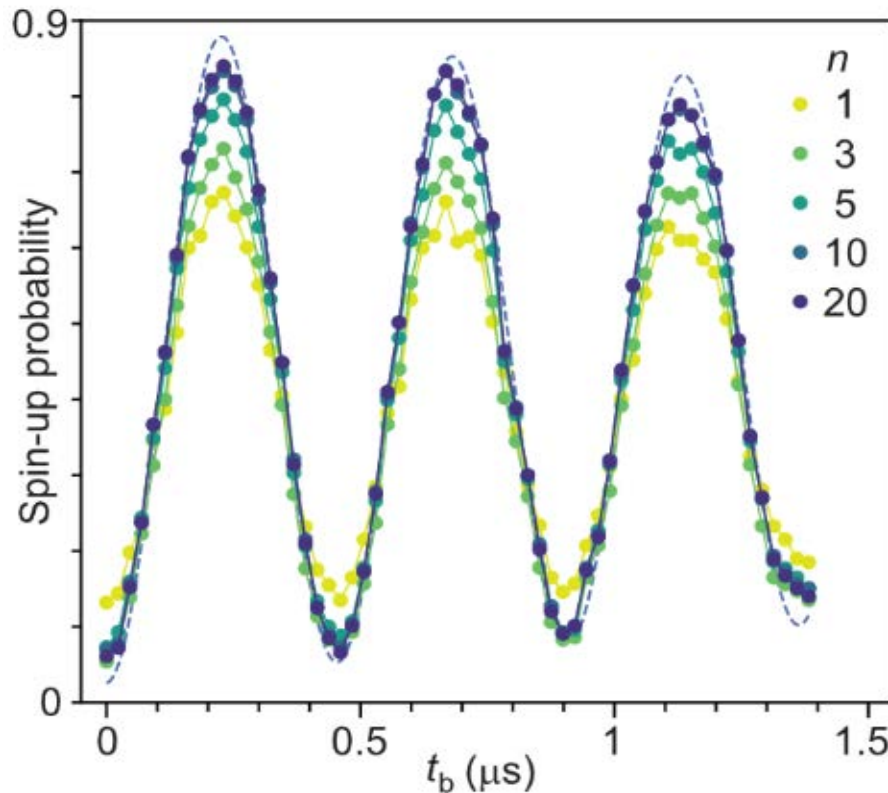


Improved Readout and Initialization Fidelity by QND Measurement



T. Nakajima et al. Nature Nanotechnol. 2019; J. Yoneda et al. Nature Commun. 2020

Accumulation of repeated QND ancilla measurements



Measurement fidelity :

By repeated QND measurement

$$F_M^{\downarrow(\uparrow)} = 88 \% \text{ for } n=1 \text{ (} 60 \mu\text{s} \ll T1\text{)}$$

$$95.6\% \text{ (} 94.6\%\text{) for } n = 20$$

$$\text{(} 1.2 \text{ msec} \ll T1\text{)}$$

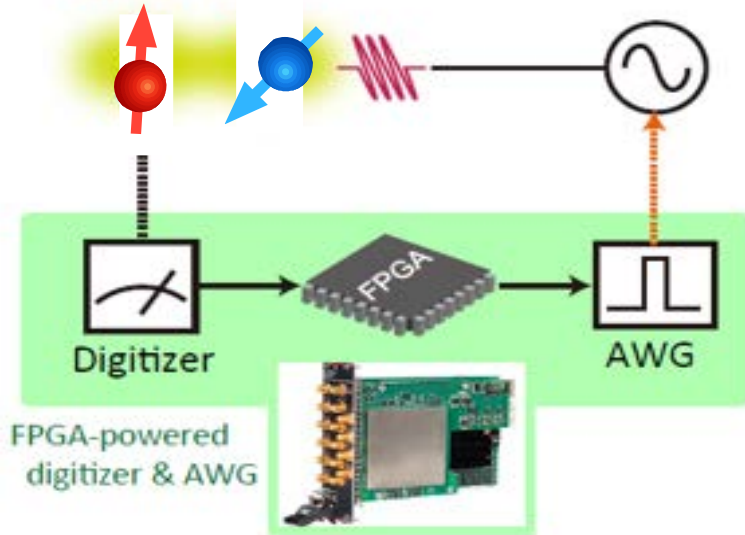
Measurement-based Initialization

T. Kobayashi et al. (2021)

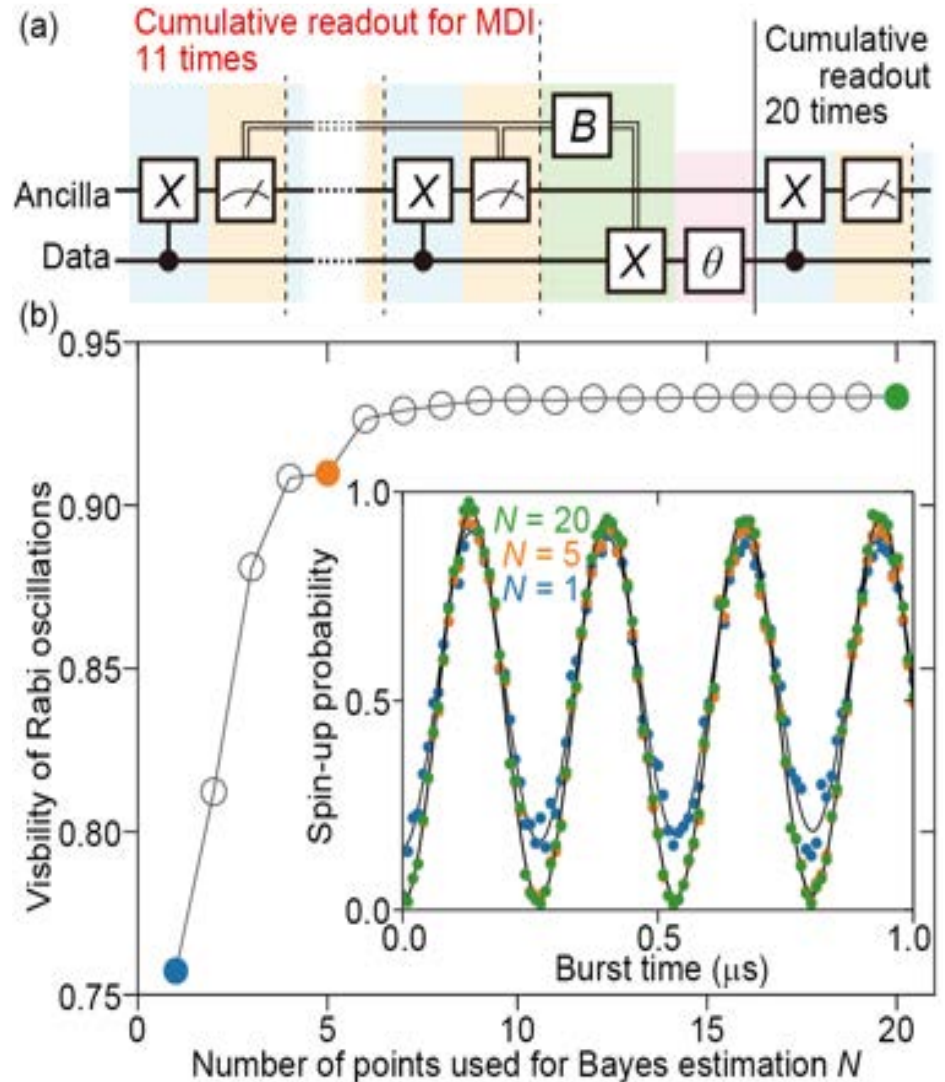
Initialization of the data qubit to spin-down

$$a|\downarrow\rangle|\downarrow\rangle + b|\uparrow\rangle|\uparrow\rangle$$

ancilla data



Initialization fidelity increased from 86 to 97%.



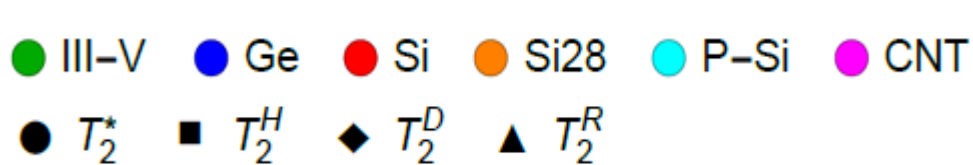
Part I Basics of semiconductor QC

- Concepts of quantum bits and computation
- Implementation of single and two qubit gates
- Readout and initialization
- **Quantum coherence and phase noise**

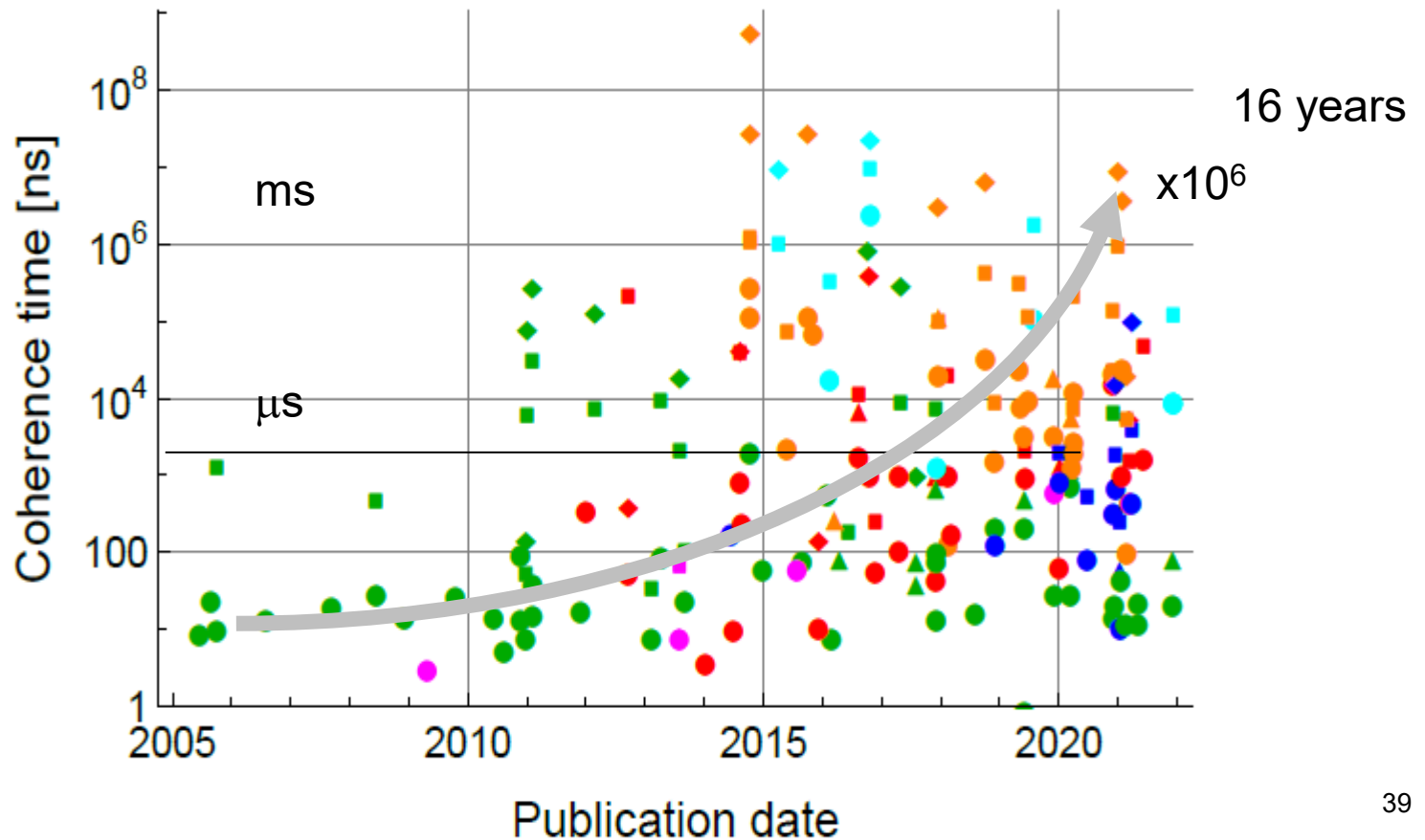
Part II Advances in semiconductor QC

- Features of quantum computing in silicon
- High-fidelity quantum gates and readout
- Quantum error correction
- Multi-qubit devices for scale-up

Dephasing time T_2^* , Hahn-echo time T_2^H , CPMG time T_2^C and Rabi decay time T_2^R



Stano & Loss
Nat. Phys. Rev. 2022



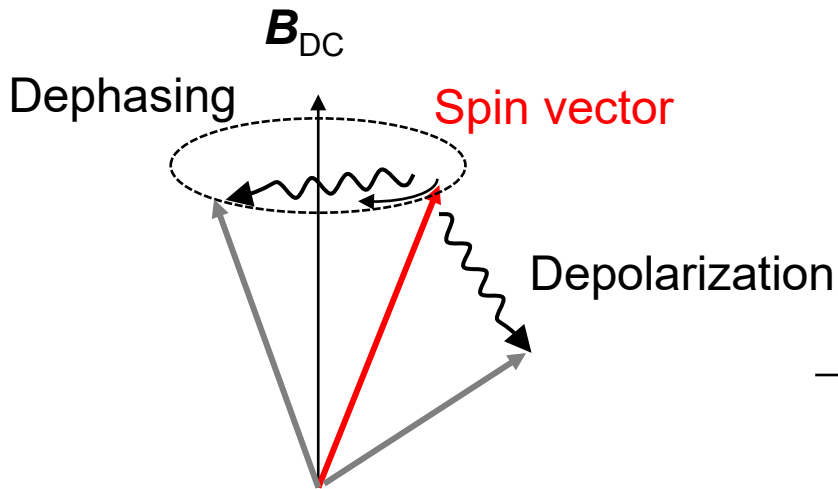
Dephasing and Depolarization of Spin

Larmor precession about \mathbf{B}_{DC}

: Coherent state

$$|\varphi\rangle = a|0\rangle + be^{i\omega_L t}|1\rangle$$

$$\omega_L = g\mu_B B_{DC}/\hbar$$



Dephasing T_2^* due to magnetic noise

$$\longrightarrow |a|^2|0\rangle\langle 0| + |b|^2|1\rangle\langle 1|$$

$$T_2^* = \frac{1}{\pi\sqrt{2}\langle\delta\omega^2\rangle}$$

$$\text{Measure } \delta\omega_L = \frac{g\mu_B}{\hbar}\delta B$$

Depolarization T_1
due to phonon+spin orbit interaction

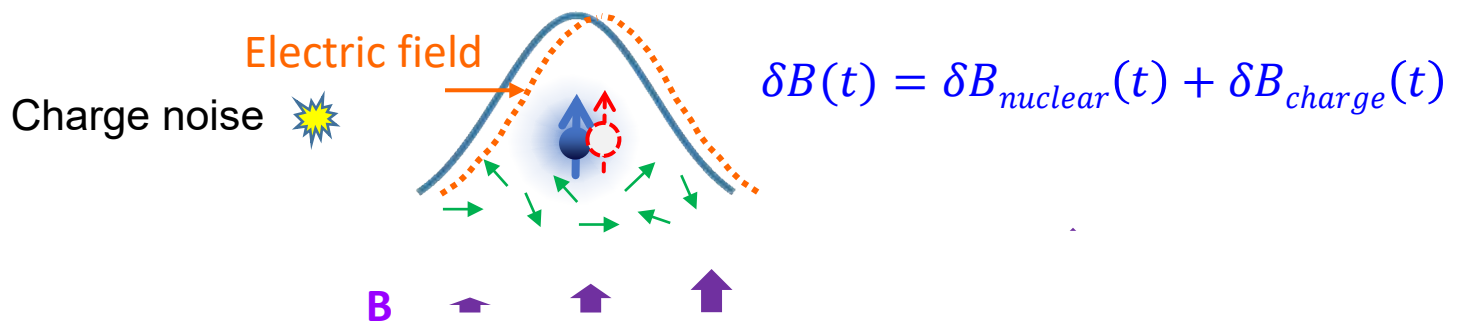
$$\longrightarrow (1-p)|0\rangle\langle 0| + p|1\rangle\langle 1|$$

$$\text{Measure polarization } p = e^{-\frac{t}{T_1}}$$

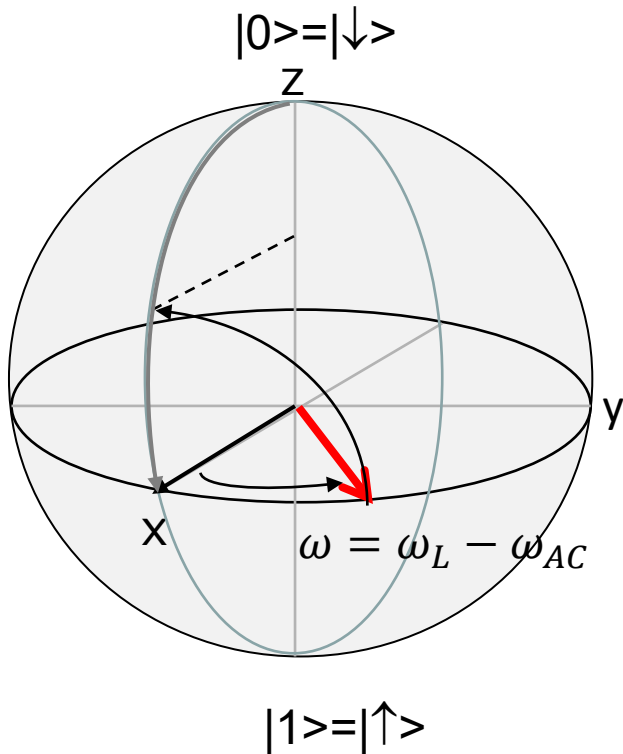
Charge Noise and Nuclear Spin Noise in GaAs and Si

- 1) Ensembles of nuclear spins cause statistical fluctuations of B field
- 2) Two-level fluctuators (impurities, defects,..) cause fluctuation of electron position. This causes fluctuation of electron Zeeman energy in the presence of magnetic field inhomogeneity or spin-orbit interaction.

Nuclear spin noise $H_{\text{HF}} = A|\psi(\mathbf{x})|^2 \left(\frac{I_+ S_- + I_- S_+}{2} + I_z S_z \right)$



Phase Measurement of Spin



Prepare a state along x-axis : $\frac{|0\rangle + |1\rangle}{\sqrt{2}}$

Rotation about z-axis with detuning frequency $\omega = \omega_L - \omega_{AC}$ ($\ll \omega_L$)

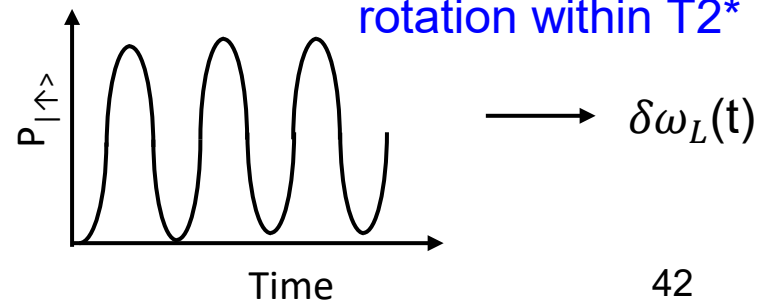
$$|\varphi\rangle = \frac{|0\rangle + e^{i\omega t}|1\rangle}{\sqrt{2}} \quad \text{Rotating frame about z with } \omega_{AC}$$

After $\pi/2$ rotation about x-axis

Probability of finding the state in $|\downarrow\rangle$

$$= \frac{1 + \sin\omega t}{2}$$

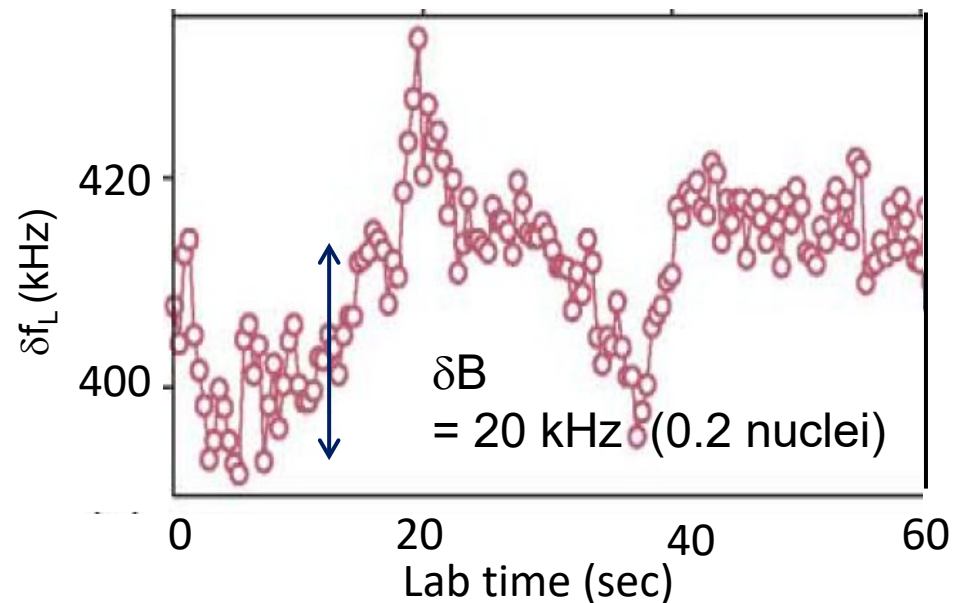
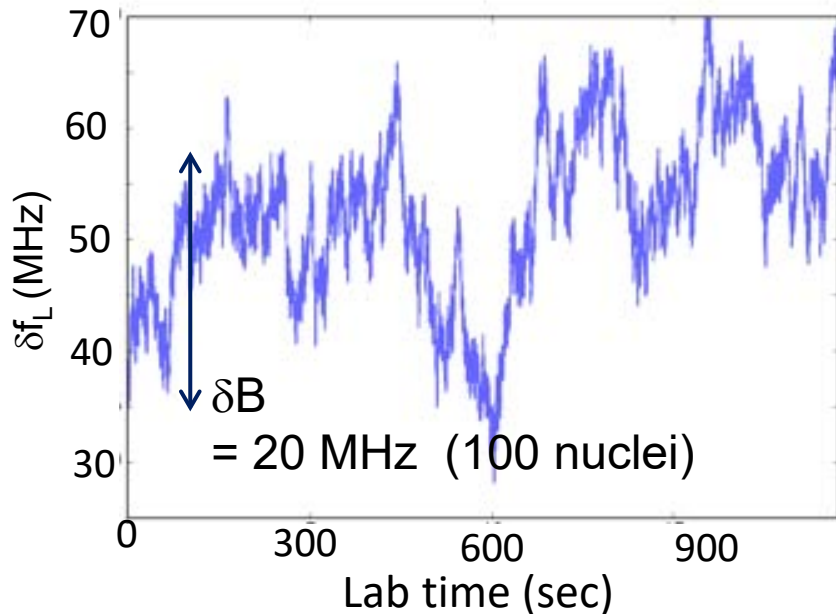
Measure $\omega(t)$ for z-axis rotation within T_2^*



Ramsey Measurement to Evaluate the Fluctuating B_{Zeeman}

GaAs: 10^5 to 10^6 n-spins

^{28}Si (0.08% ^{29}Si): 10 to 10^2 n-spins



$$\delta B_{1\text{nuc}} = \frac{A(\text{GaAs})}{\sqrt{N}}$$

$$= 20 \text{ MHz}$$

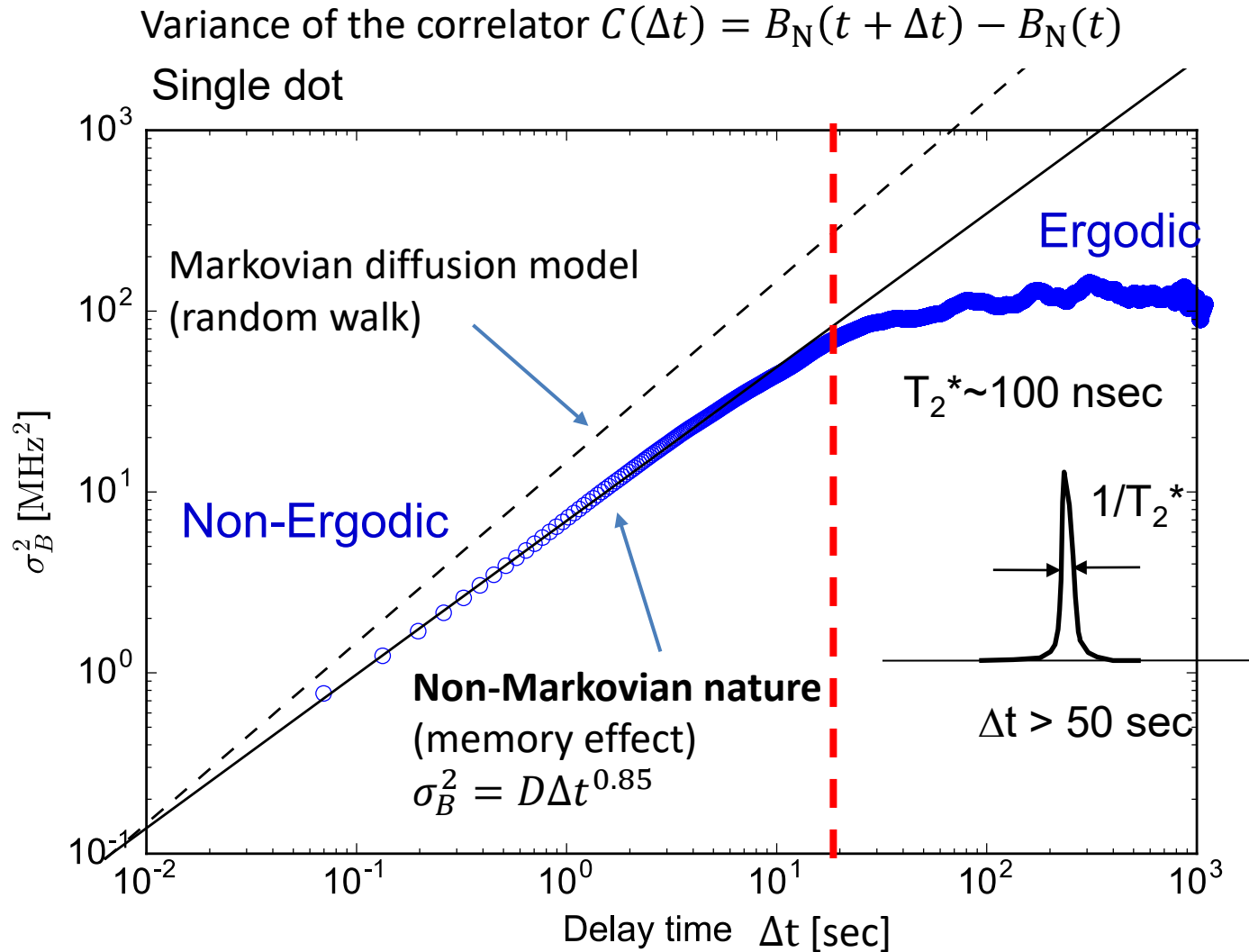
$$\delta B_{1\text{nuc}} = \frac{A(^{29}\text{Si})}{\sqrt{N}}$$

$$= 0.1 \text{ MHz}$$

Time resolution = $100 \mu\text{s}$
($= 1 \mu\text{s} \times 100$)

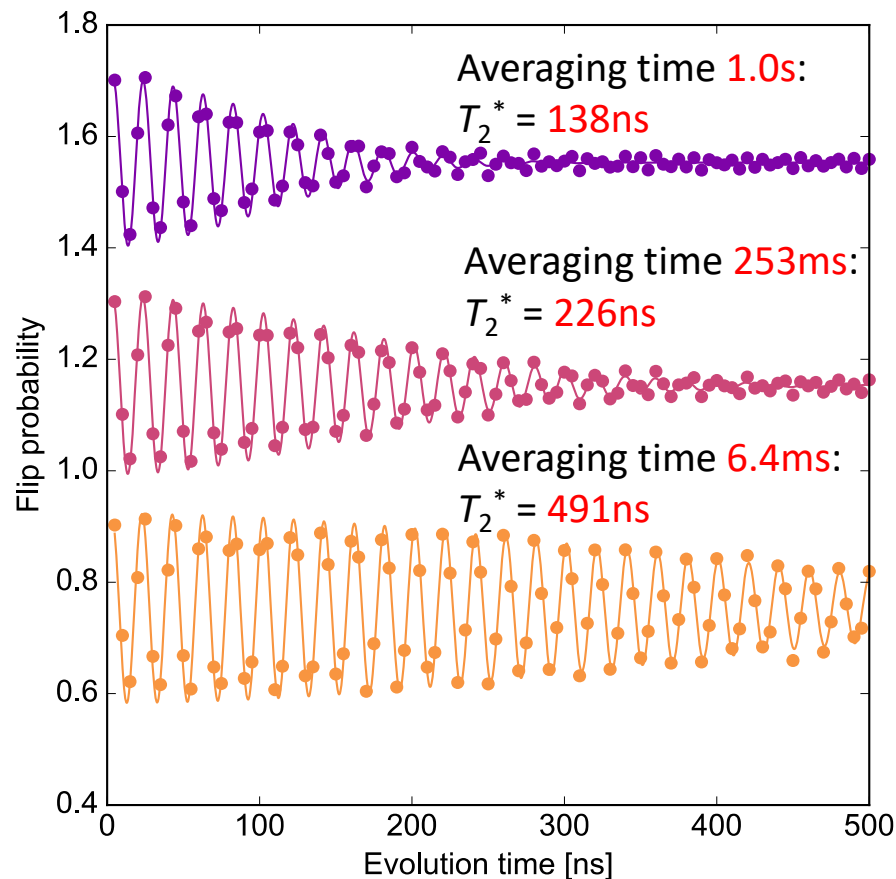
Dynamics of Nuclear Spin Fluctuation

Magnetic, Non-Markov, Non-ergodic, Diffusive,...



Reduced Dephasing of Single Spins by Fast Measurement

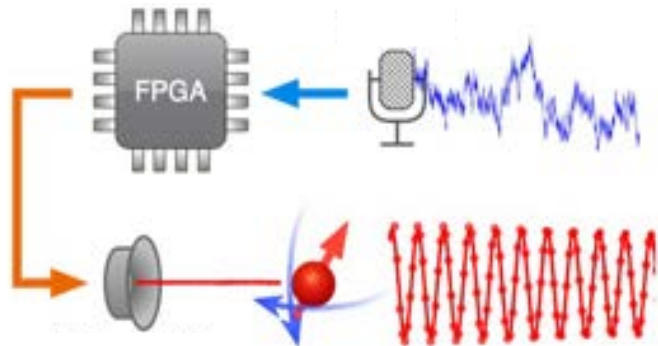
- Non-ergodic spin dynamics in the fluctuating environment is demonstrated
- Two-orders of magnitude improvement of the spin coherence with a feedback control is shown



Real-time Feedback of Spin Noise Measurement to Control Spin Dynamics

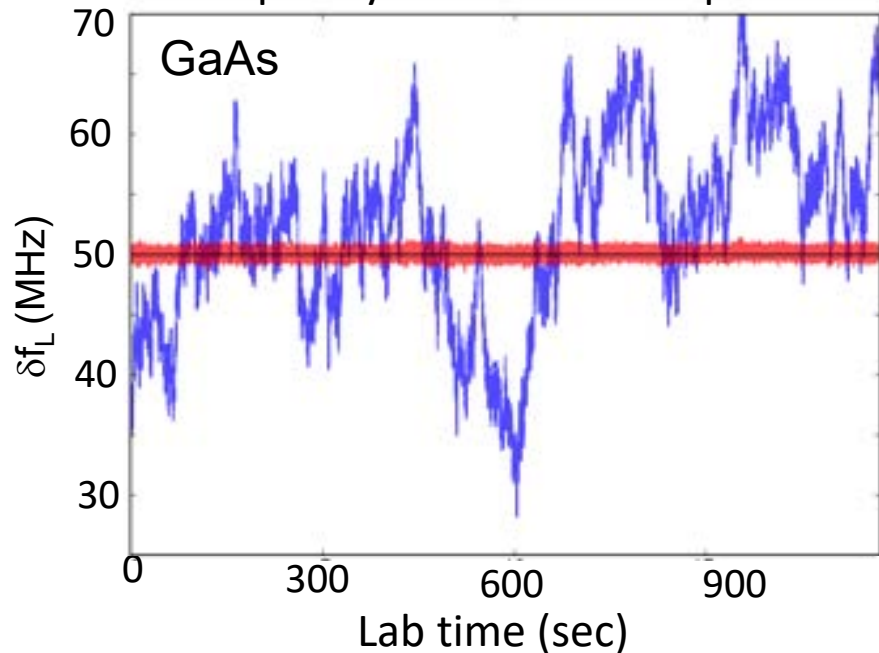
Realtime analysis

Noise detection



Feedback

Low-frequency fluctuation compensated

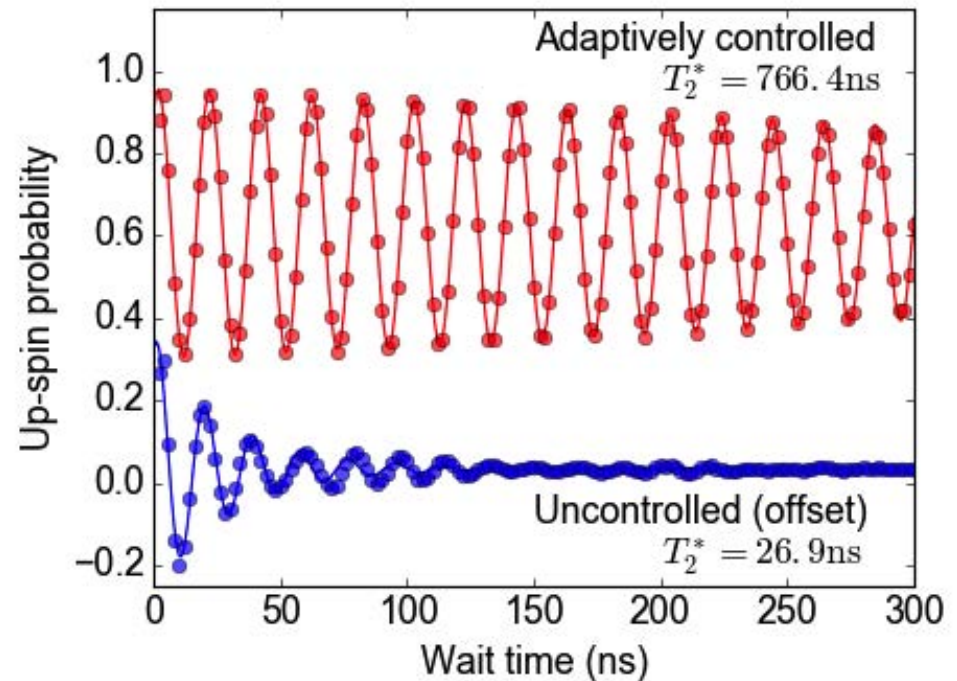


$$T_M + T_{FB} < T_1 (> 10 \text{ msec}), \quad F > 99\%$$

Tracking the magnetic field fluctuation by changing the MW frequency

M. Delbecq et al. Phys. Rev. Lett.

T. Nakajima et al. Phys. Rev. X 2019



Nuclear Spins in GaAs, nat. Si and 28Si

	GaAs	Nat. Si	28Si
Nuclear spin	100%	4.7%	0.08%
T2*	10 nsec	1.5 μsec	10 μsec
Noise source	nuclear spin (>> charge noise)	nuclear spin (> charge noise)	charge noise (>> nuclear spin)

$$H_{\text{HF}} = A |\psi(\mathbf{x})|^2 \left(\frac{I_+ S_- + I_- S_+}{2} + I_Z S_Z \right)$$

T1 > 10 to 1000 msec

Statistical fluctuation : $\delta A = A/\sqrt{N}$

Part I Basics of semiconductor QC

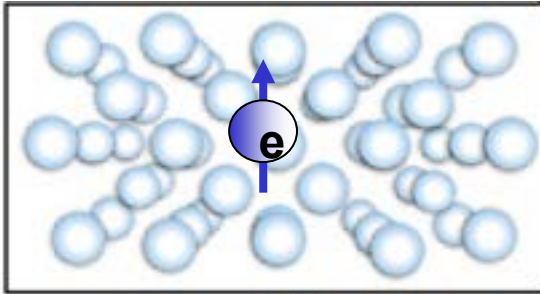
- Concepts of quantum bits and computation
- Implementation of single and two qubit gates
- Readout and initialization
- Quantum coherence and phase noise

Part II Advances in semiconductor QC

- **Features of quantum computing in silicon**
- High-fidelity quantum gates and readout
- Quantum error correction
- Multi-qubit devices for scale-up

Why Silicon?

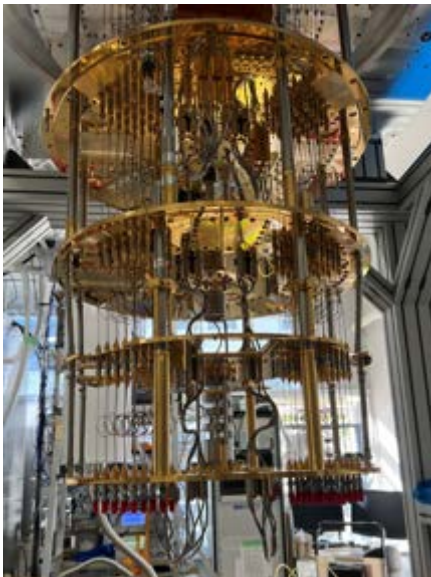
^{28}Si



Long-intrinsic coherence time in isotopically purified ^{28}Si

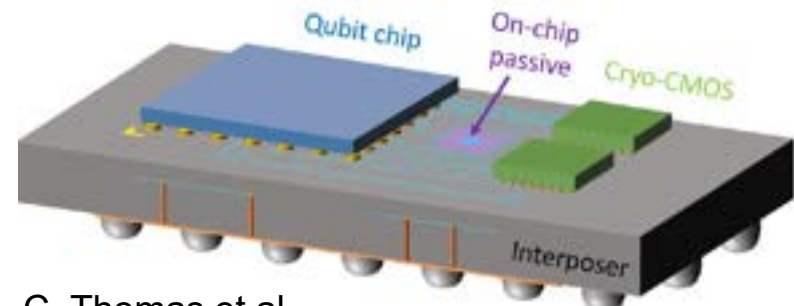
Compatibility with CMOS based manufacturing techniques

Possible high-temperature operation at $> 1\text{ K}$
A larger number of qubits
On-chip integration with cryo-electronics



← $> 1\text{ K}$

← $< 0.1\text{ K}$
Quantum processor



C. Thomas et al.
arXiv: 2022

Integration of Quantum Processors and Cryo-CMOS Controller

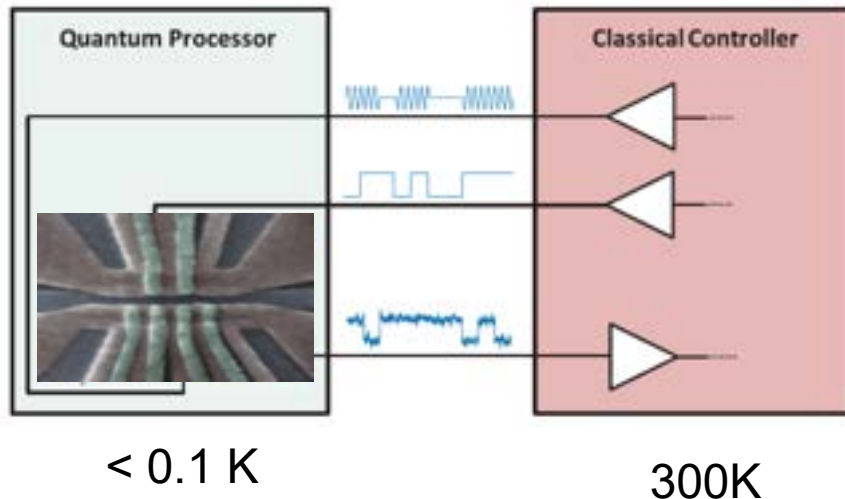
B. Patra et al. IEEE J. Solid-State Circuits, 33, 309 (2018)

E. Charbon et al., IEDM Tech. Dig., 5 (2016)

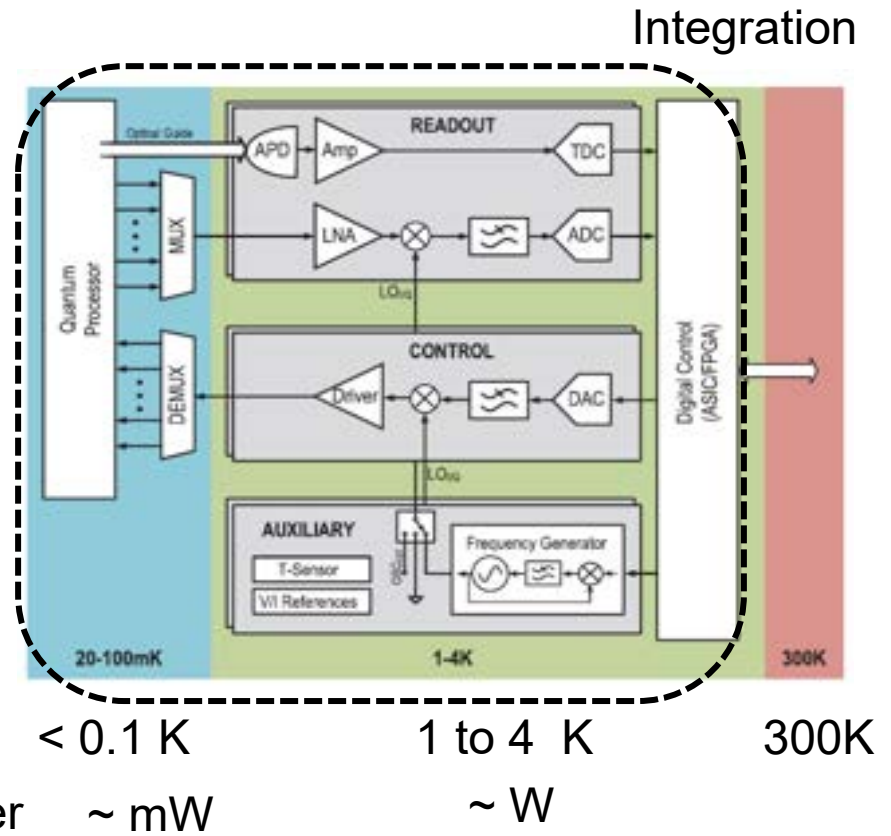
F. Sebastiano et al., Proc. 54th Annu. Des. Autom. Conf. (DAC) 13-1 (2017).

C. Thomas et al. arXiv: 2206.14082

Quantum processor vs classical control for control/readout



Block diagram of cryo-CMOS controller for the control and readout of qubits.



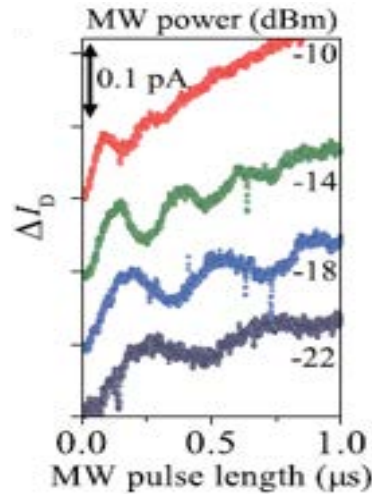
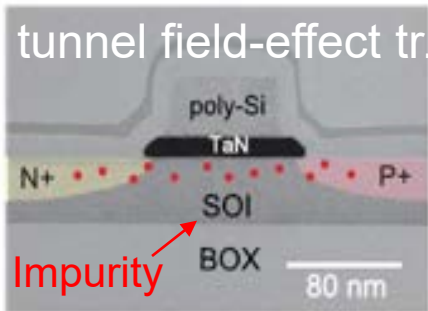
X. Xue et al. Nature 2021

Si Qubits at High Temperature > 1 K

High-temperature operation of a Si qubit

K. Ono et al. RIKEN
Sci. Rep. 2019

1.5 K to 10 K



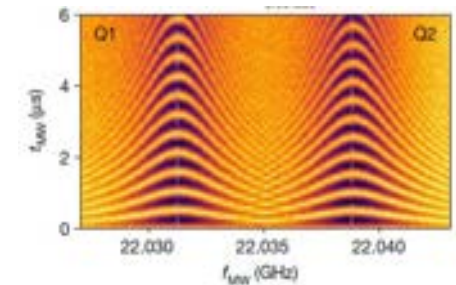
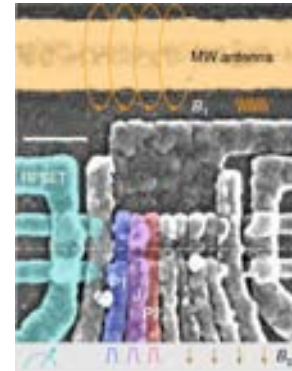
Si quantum processor unit cell operation > 1K

CH Yang et al. UNSW
Nature 2020, 2024

single qubit $F=99.85\%$

DCZ $F=98.92\%$

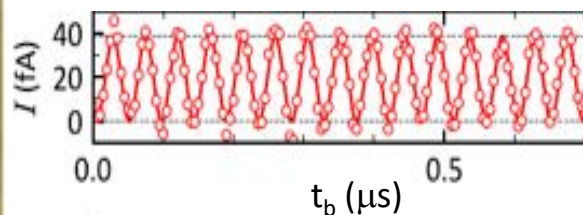
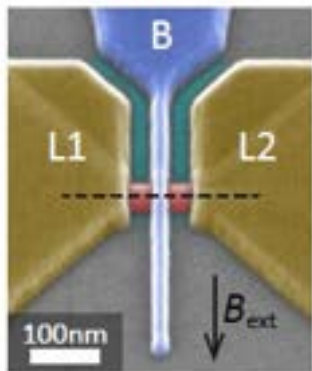
^{28}Si n-MOS



High-temperature operation of hole qubit

LC. Camenzind et al. Basel, IBM Zurich
arXiv 2103.07369v1 2021

1.5K hole qubit $F=98.9\%$



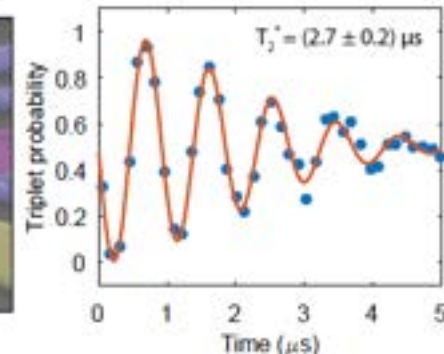
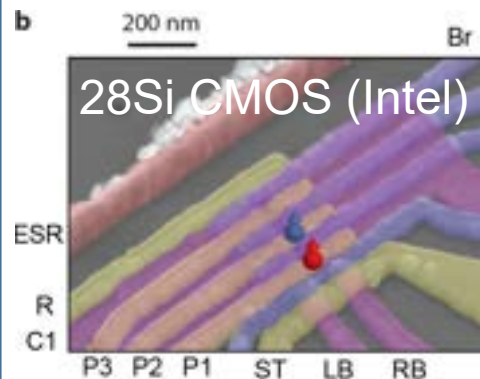
nat. Si Fin-FET

Universal logic in hot Si qubits

L. Petit et al. TuDelft
Nature 2020

1.1K single qubit $F=99.3\%$

Two qubit CROT $F=86\%$



Part I Basics of semiconductor QC

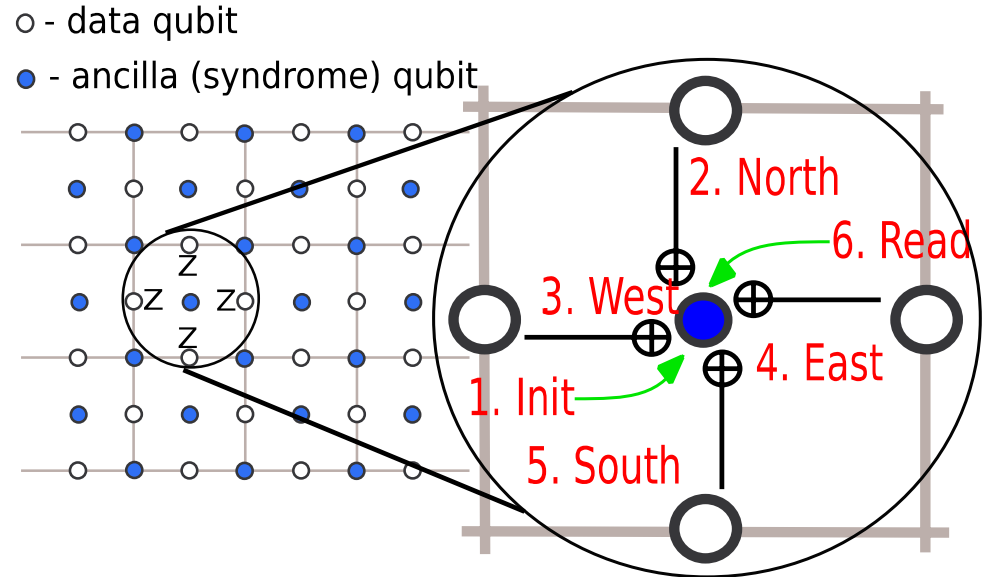
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Part II Advances in semiconductor QC

- Features of quantum computing in silicon
- **High-fidelity quantum gates and readout**
- Quantum error correction
- Multi-qubit devices for scale-up

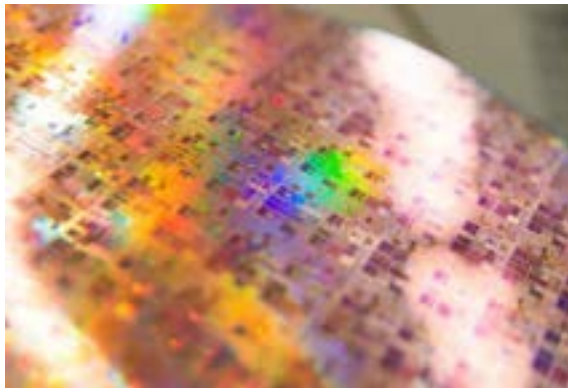
Challenges in Si QC

High fidelity in two-qubit gates
Error correction
Scale-up
... not yet well studied in
semiconductor QC before



A. G. Fowler *et al.*, *Phys. Rev. A* (2009)

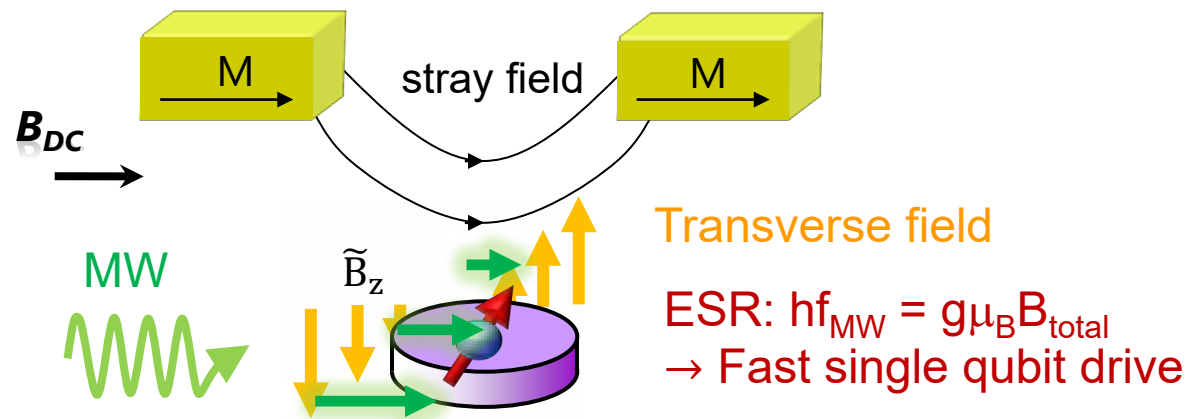
Introduction of semiconductor
manufacturing tech. for scale-up



Error correction thresholds

Fidelity (1 qubit) > 99.9%
Fidelity (2 qubit) > 99%
Initialization F > 99%
Readout F > 99%

Micro-magnet Method for Implementing Spin Qubits Based on ESR

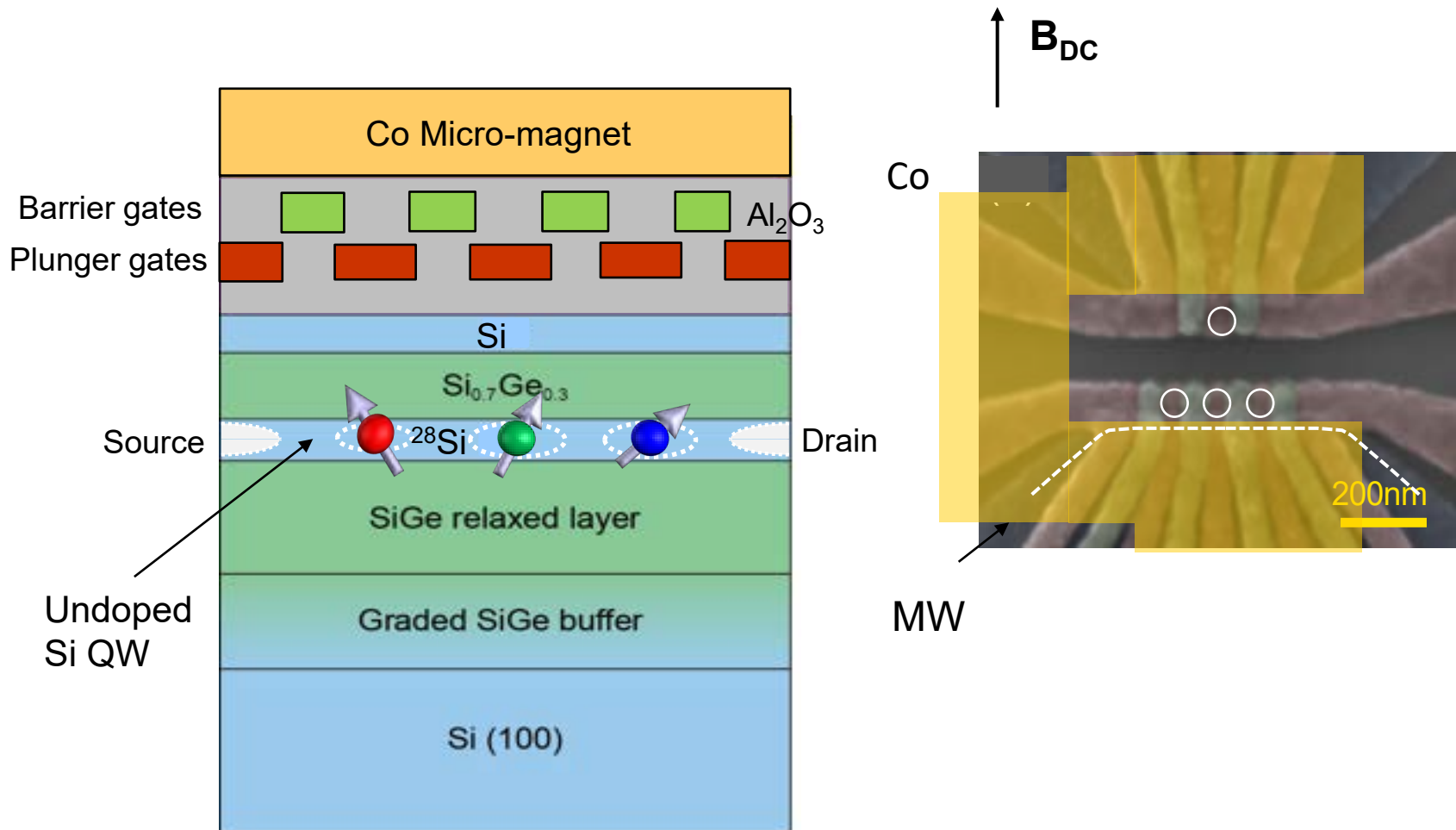


Longitudinal field

- ΔE_{Zeeman} between QDs
- Addressability to each qubit
- Fast two-qubit gate

Y. Tokura et al. PRL 2008;
M. Pioro-Ladriere et al. Nature Phys. 2011

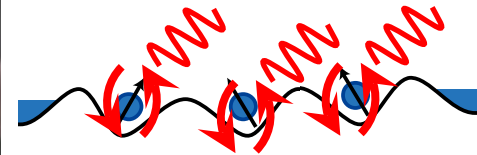
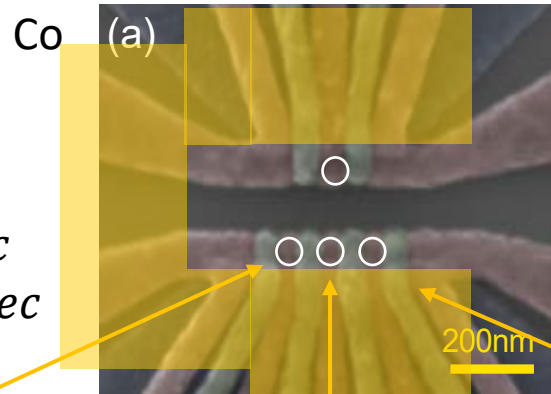
Three Qubit Si/SiGe Device with a Micro-magnet



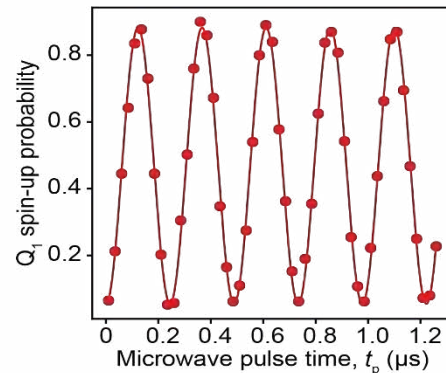
High-fidelity of three single qubits

Nat. Nanotechnol. 2021

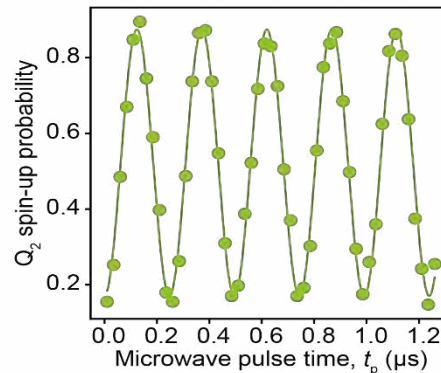
$f_{\text{Rabi}} = 5 \text{ MHz}$
Ramsey $T_2^* \cong 1.5 \mu\text{sec}$
Hahn echo $T_2 \cong 15 \mu\text{sec}$



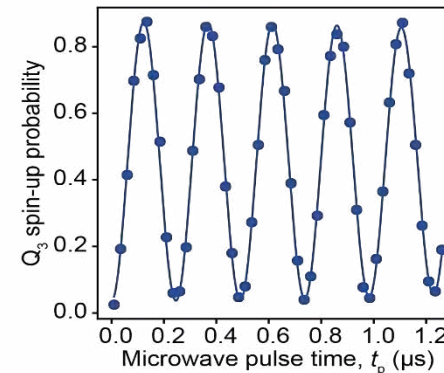
Qubit 1



Qubit 2



Qubit 3

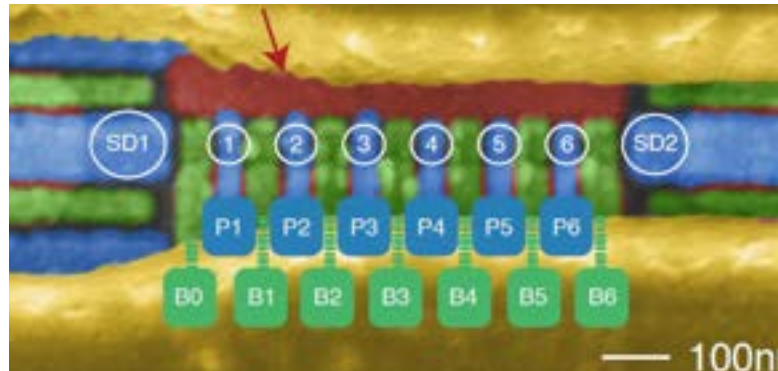


$$\Delta f_{\text{Larmor}} = 400 \text{ to } 500 \text{ MHz}$$

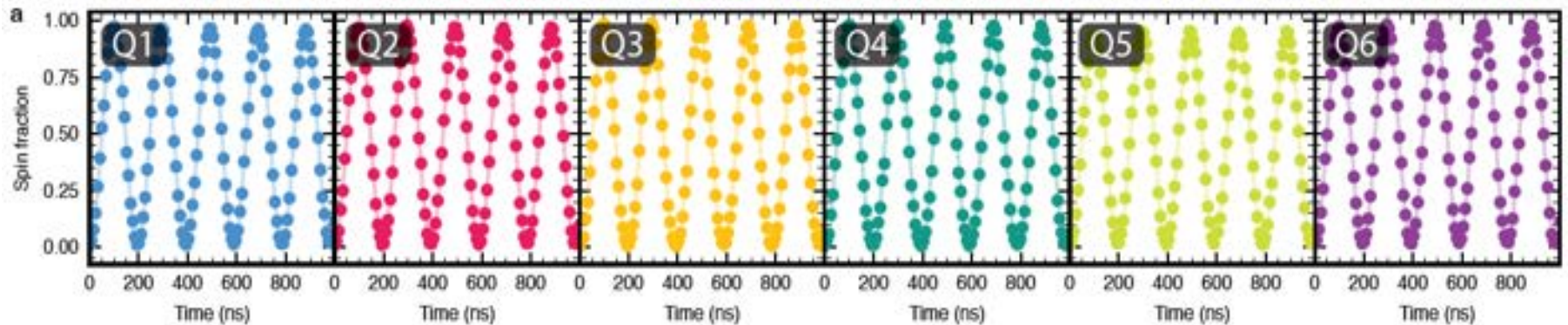
Fidelity = 99.6 % on average for Nat. Si/SiGe
 = 99.8 % on average for $^{28}\text{Si}/\text{SiGe}$

Toward Multiple Qubits

6 qubits in 1x6 $^{28}\text{Si}/\text{SiGe}$ QDs

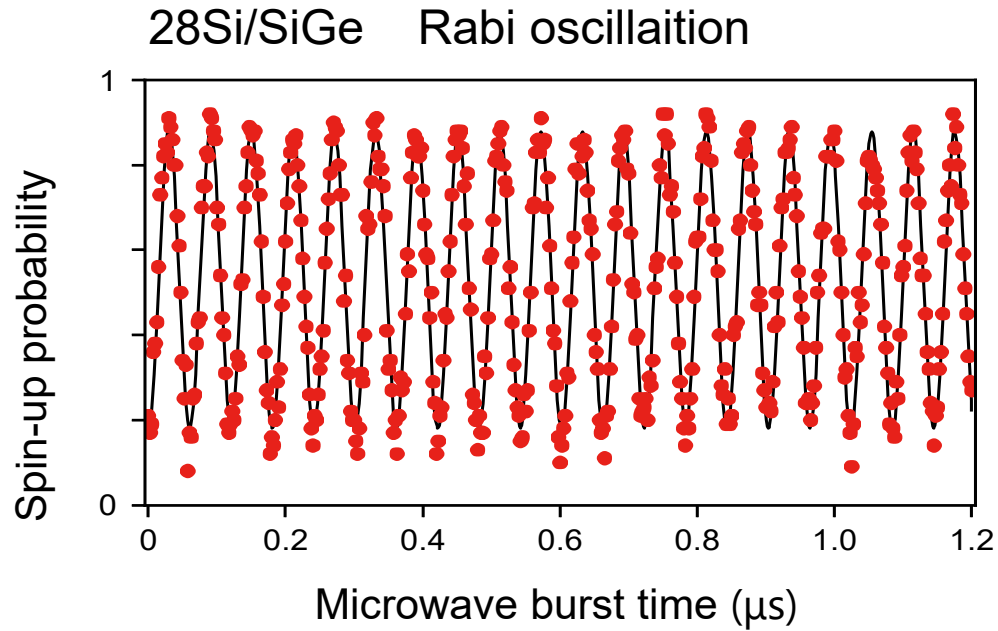


S.G.J. Philips et al.
Nature (2022)



Fidelity = 99.77 to 99.96 %

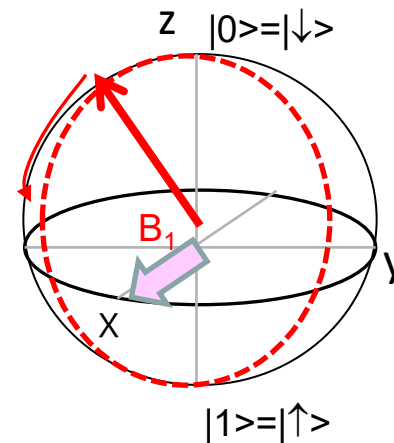
Spin Qubits using a μ -magnet Method



$T_2^* = 20 \mu\text{sec}$

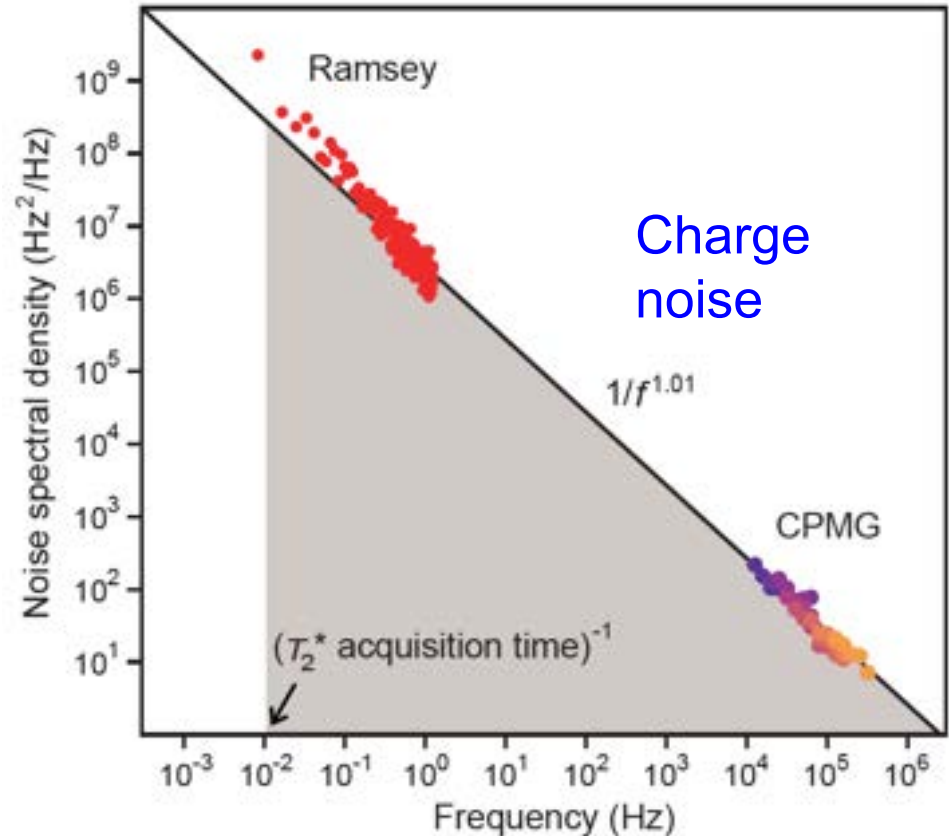
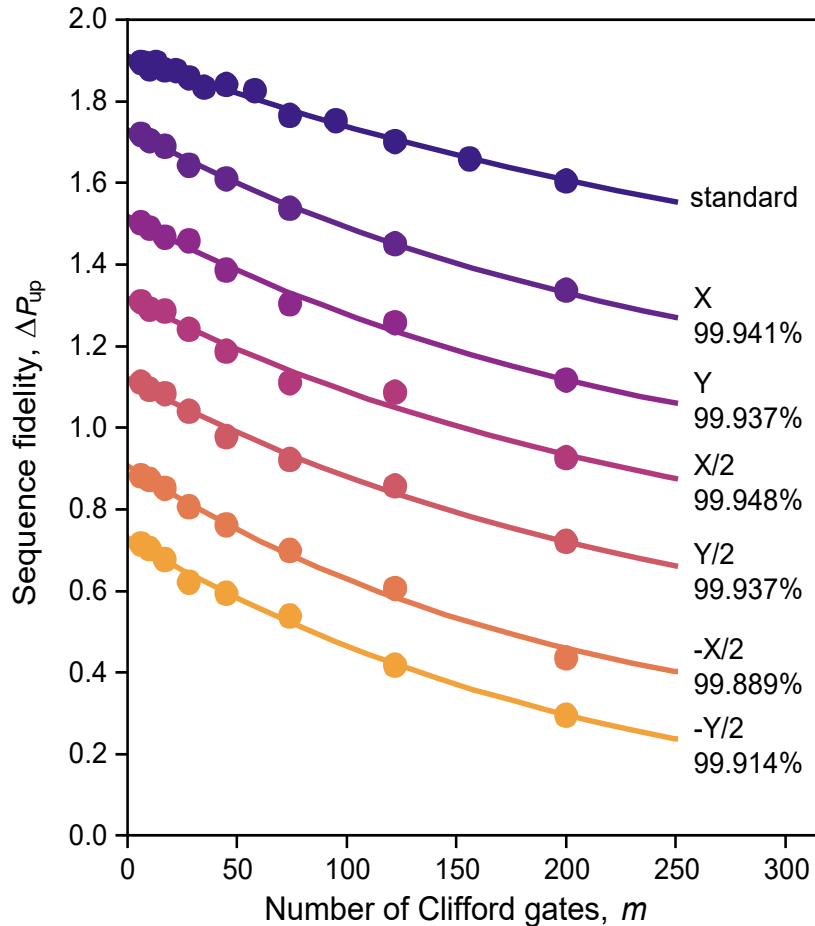
$F = 99.93\%$

J. Yoneda et al., Nat.
Nanotechnol. 2018



Environment Noise Limited Fidelity in $^{28}\text{Si}/\text{SiGe}$

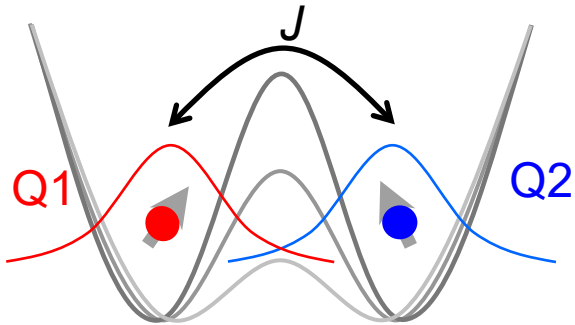
Random Bench Marking Qubit
Fidelity > 99.9 %



High-fidelity Two-qubit Gates

Two-qubit gate using spin-exchange interaction and Zeeman energy difference

Exchange coupling controlled by tunnel coupling (up to 10MHz)



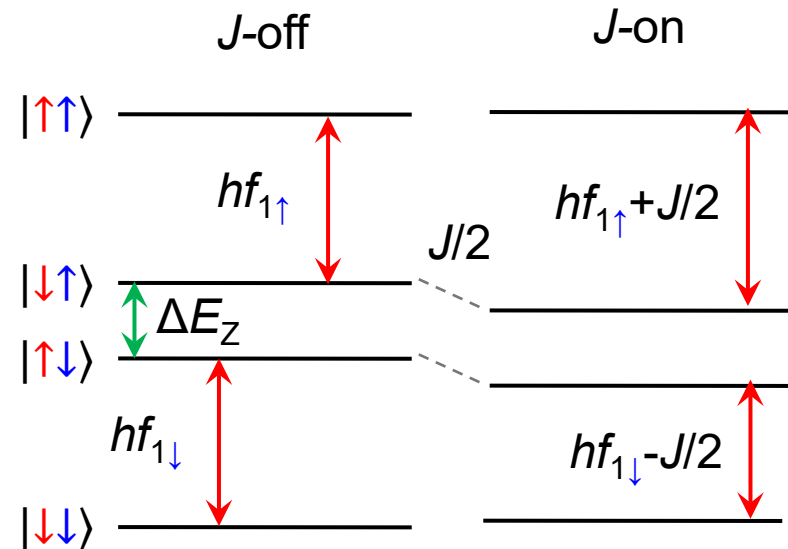
Zeeman energy gradient (ΔE_Z) induced by MM

$\Delta E_Z \sim$ a few 100 MHz

$$\Delta E_Z \gg J$$

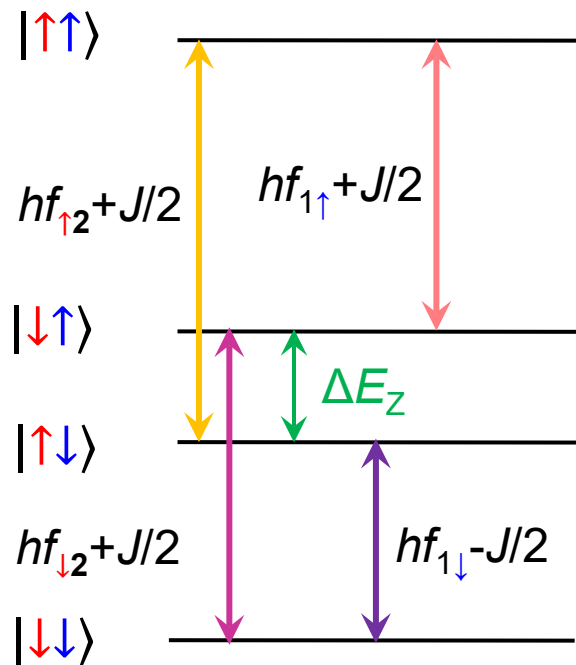
“Heisenberg” “Ising”

$$H_{\text{int}} = \frac{J}{4} \boldsymbol{\sigma}_1 \cdot \boldsymbol{\sigma}_2 \approx \frac{J_{12}}{4} \sigma_{z1} \sigma_{z2}$$



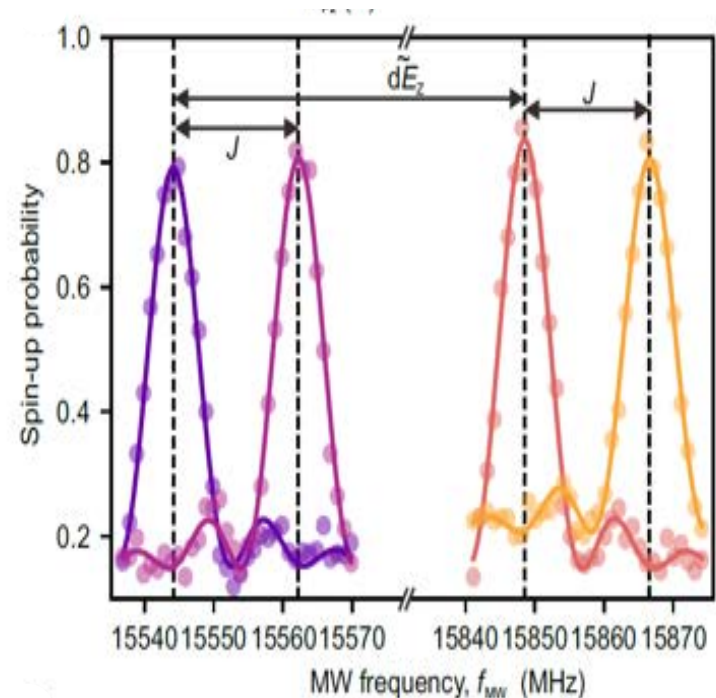
Single-step Two Qubit Gate

Basis states



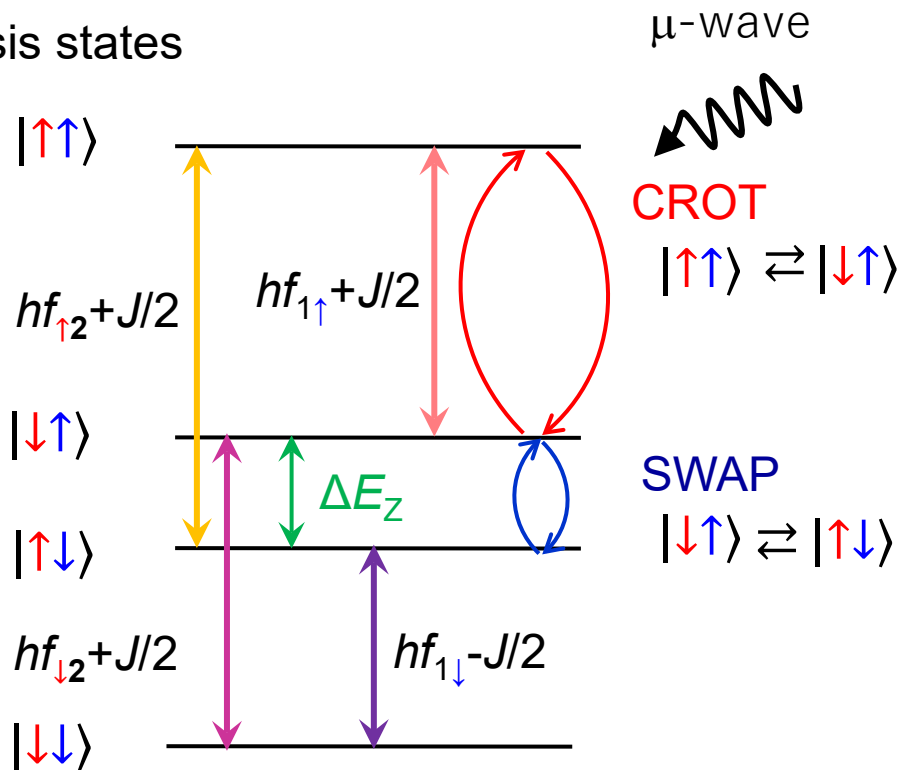
Conditional transitions to rotate one of the two spins depending on the other spin's orientation, up or down

Each transition induced by μ -wave excitation



Single-step Two Qubit Gate

Basis states



target control

$$CNOT |\downarrow\downarrow\rangle = |\downarrow\downarrow\rangle$$

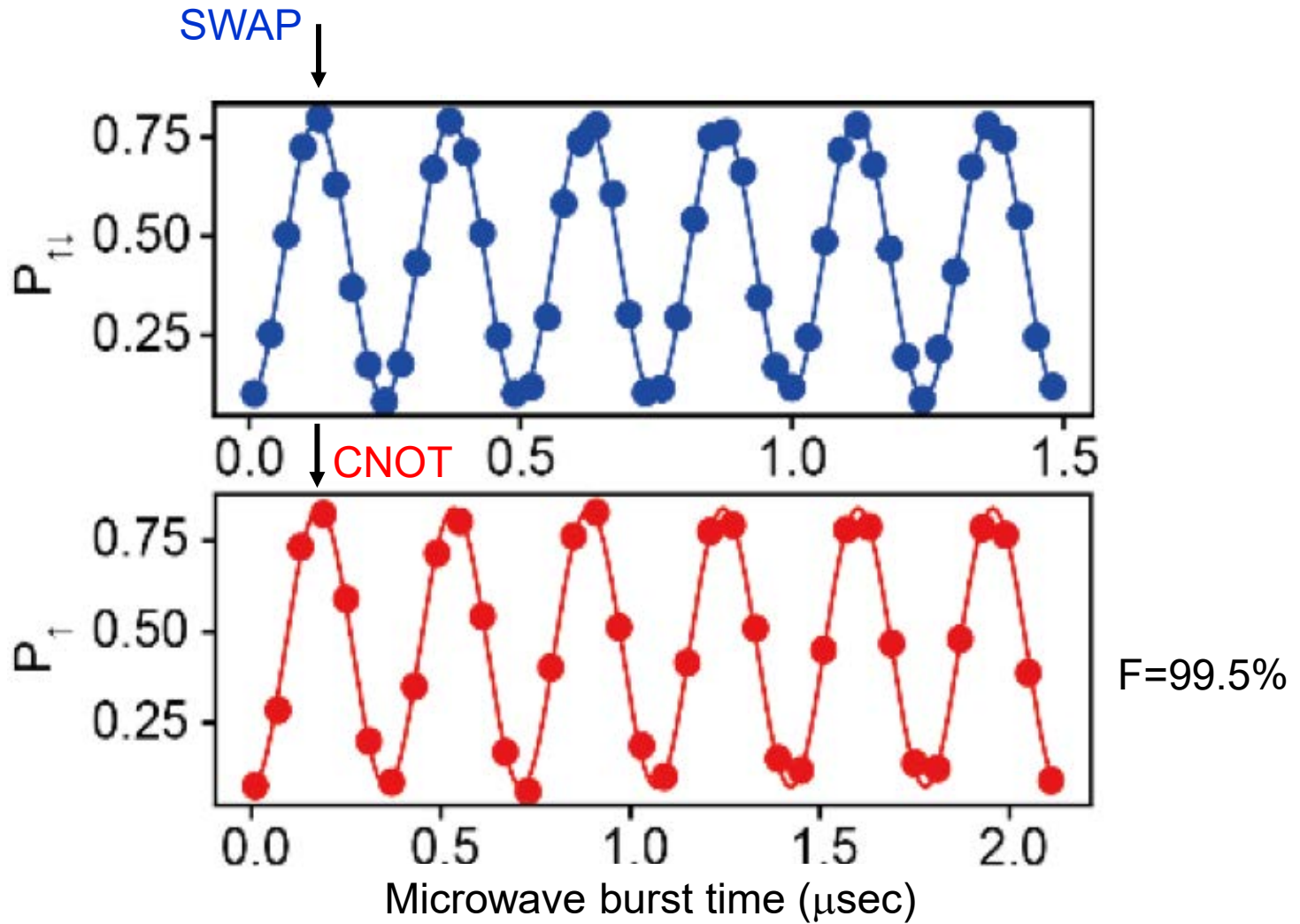
$$CNOT |\uparrow\downarrow\rangle = |\uparrow\downarrow\rangle$$

$$CNOT |\downarrow\uparrow\rangle = |\uparrow\uparrow\rangle$$

$$CNOT |\uparrow\uparrow\rangle = |\downarrow\uparrow\rangle$$

With resonant μ -wave excitation, left spin flips when right spin up

SWAP and CNOT

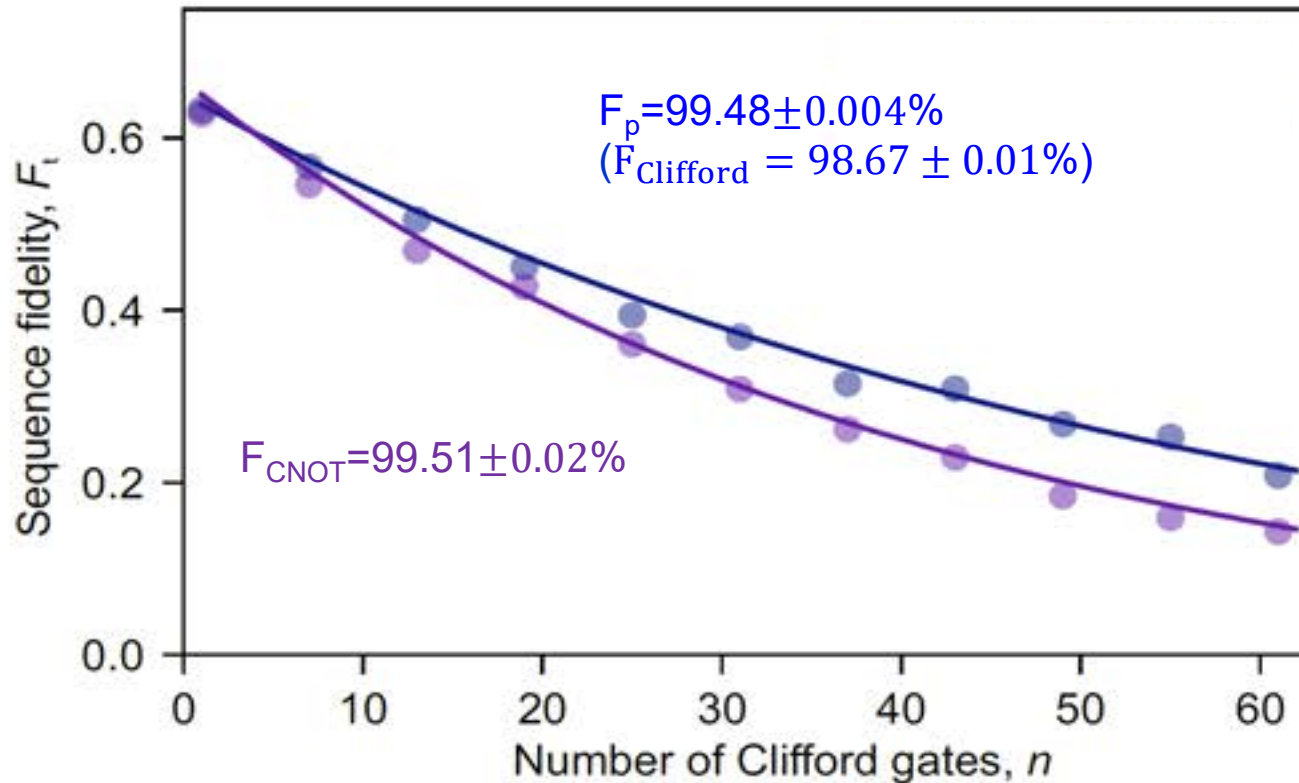


$T_{\text{CPHASE}} = 5.5.\text{nsec to } 1 \text{ msec}$

Fidelities of Two Qubit Gates

A. Noiri et al. Nature 2022

Clifford gate random benchmark



- The Rabi freq. range of 3 to 5 MHz is an order of magnitude higher than in previous work.

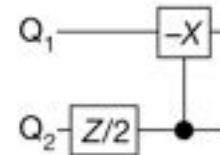
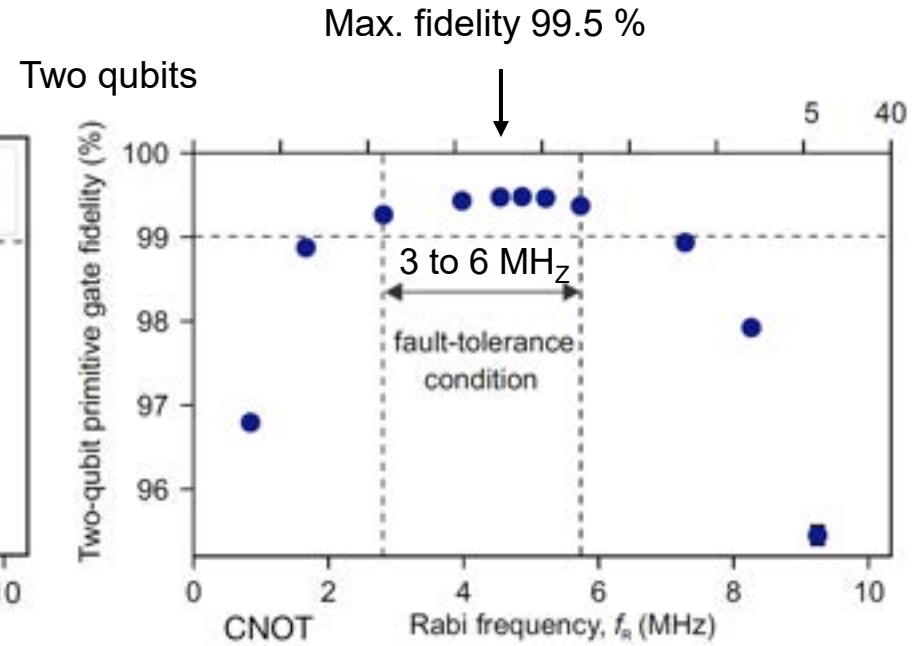
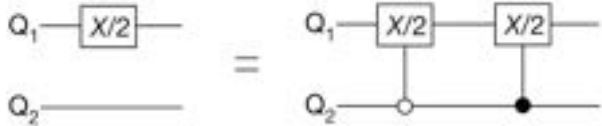
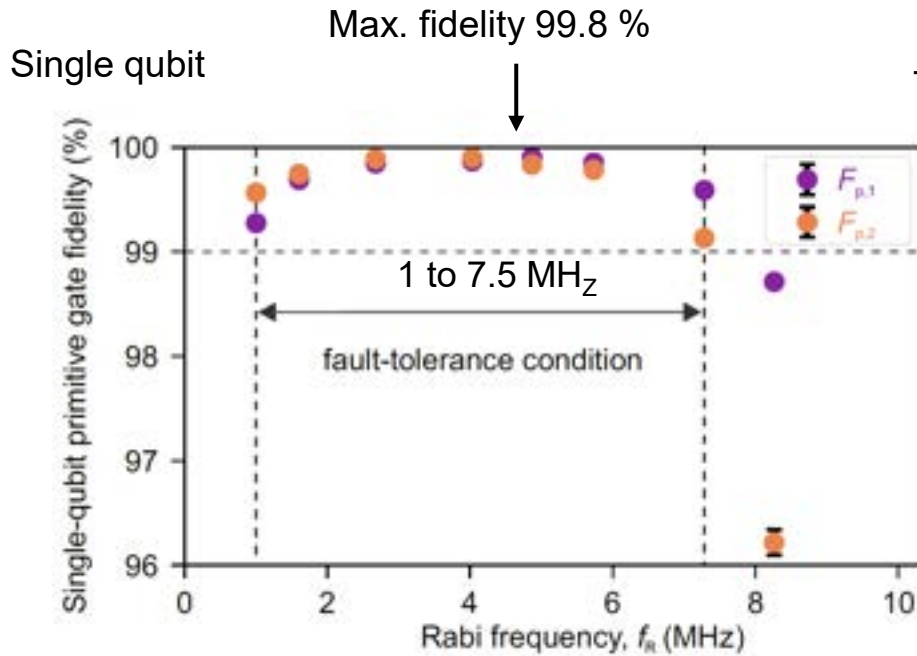
Two-spin qubit gate fidelity

> 99.5 % for $^{28}\text{Si}/\text{SiGe}$ from TuDelft, Nature 2022; > 99% for $^{28}\text{Si}/\text{SiGe}$ from Princeton Adv. Sci. 2022
99.4 % for two ^{31}P nuclear qubits with a shared electron from UNSW, Nature 2022

Single and Two-qubit Gate Fidelities

A. Noiri et al. Nature 2022

28Si/SiGe (G. Scappuci)



- The freq. range of 3 to 5 MHz is an order of magnitude higher than in previous work.

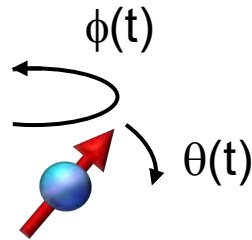
Part I Basics of semiconductor QC

- Concepts of quantum bits and computation
- Implementation of single and two qubit gates
- Readout and initialization
- Quantum coherence and phase noise

Part II Advances in semiconductor QC

- Features of quantum computing in silicon
- **High-fidelity quantum gates and readout**
- Quantum error correction
- Multi-qubit devices for scale-up

Errors in Quantum Bits

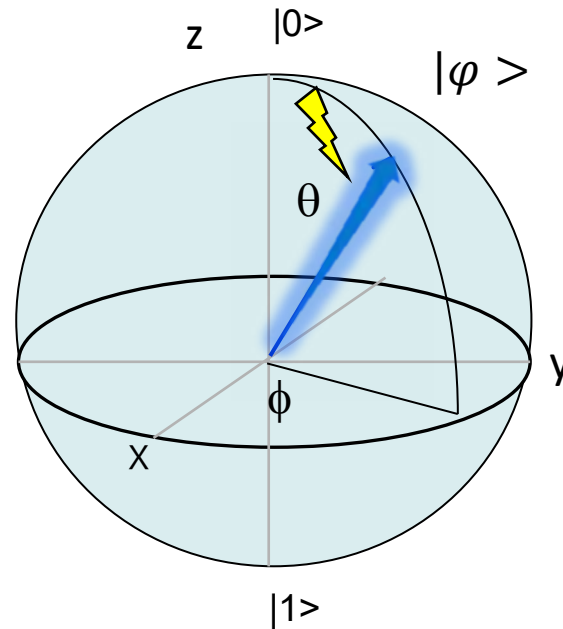


$$|\varphi\rangle = \cos\frac{\theta}{2}|0\rangle + e^{i\phi}\sin\frac{\theta}{2}|1\rangle$$

Fluctuation of ϕ : phase error
Fluctuation of θ : bit error



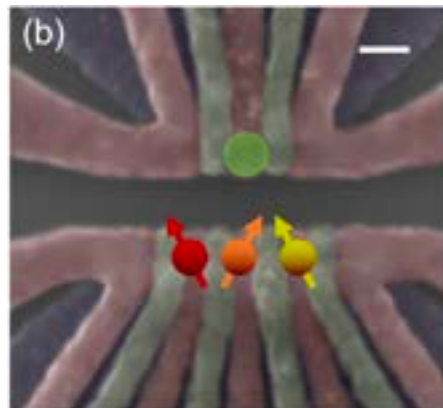
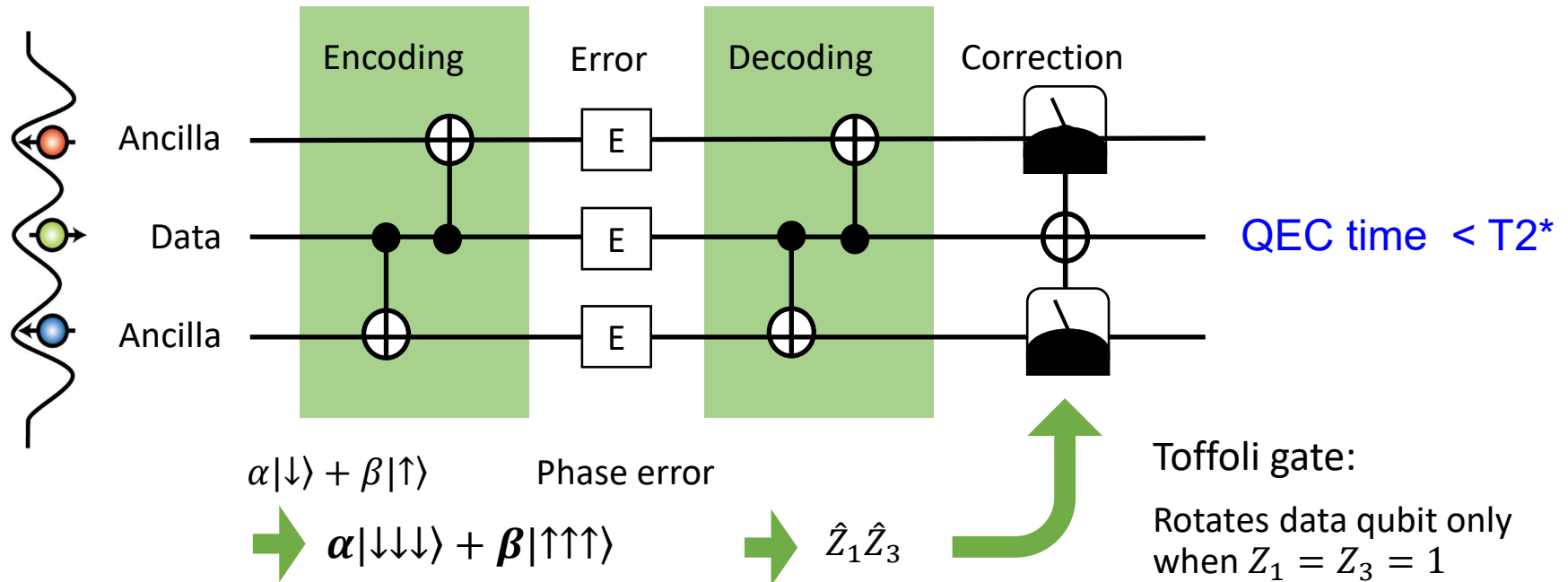
Detect and
correction of phase
error



Phase error \gg Bit error in
semiconductors

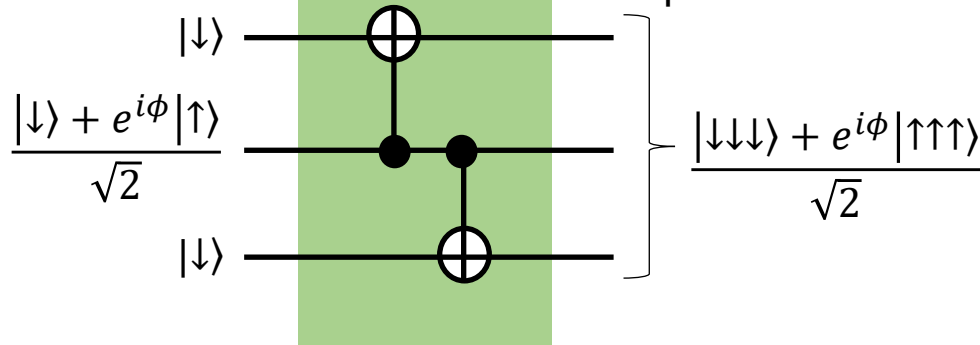
Circuit of 3Q Quantum Error Correction (QEC)

QEC for phase error (Phase error rate \gg Bit error rate)

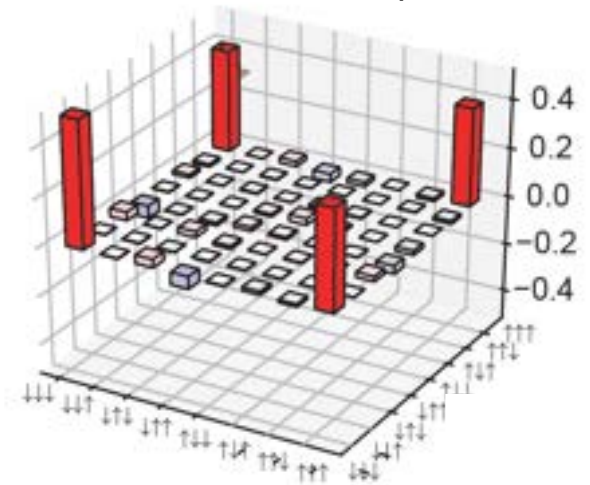


Generation of GHZ State

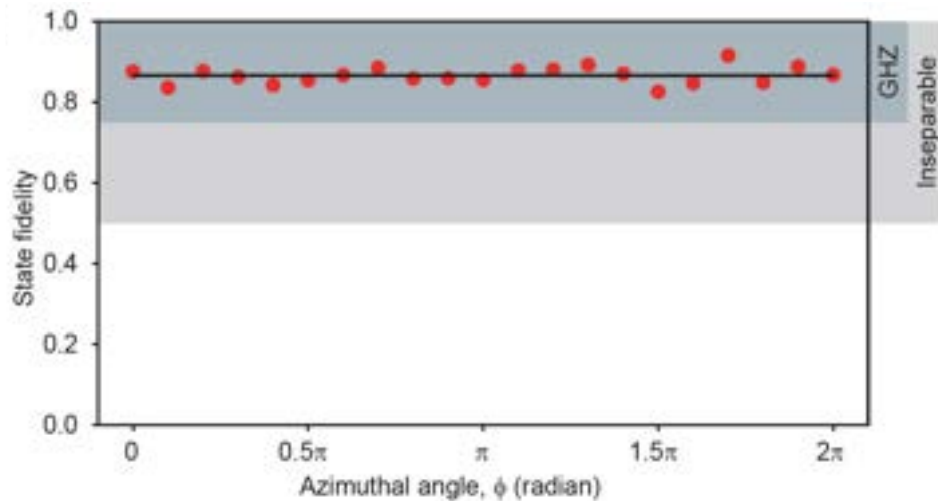
Input:
Product state



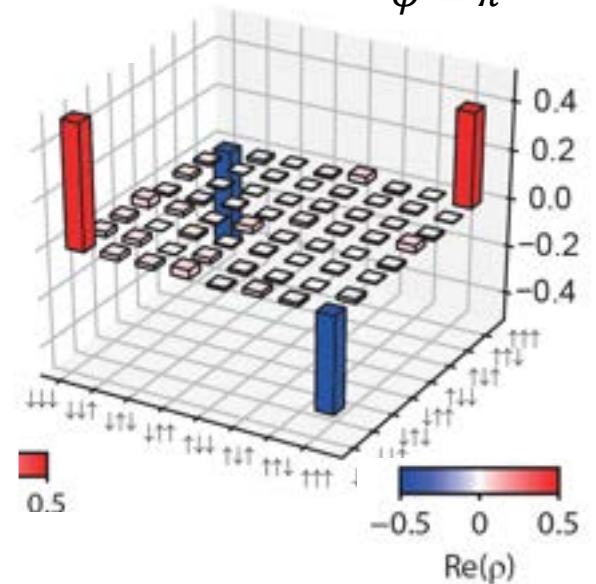
$\phi = 0$



Fidelity 88%

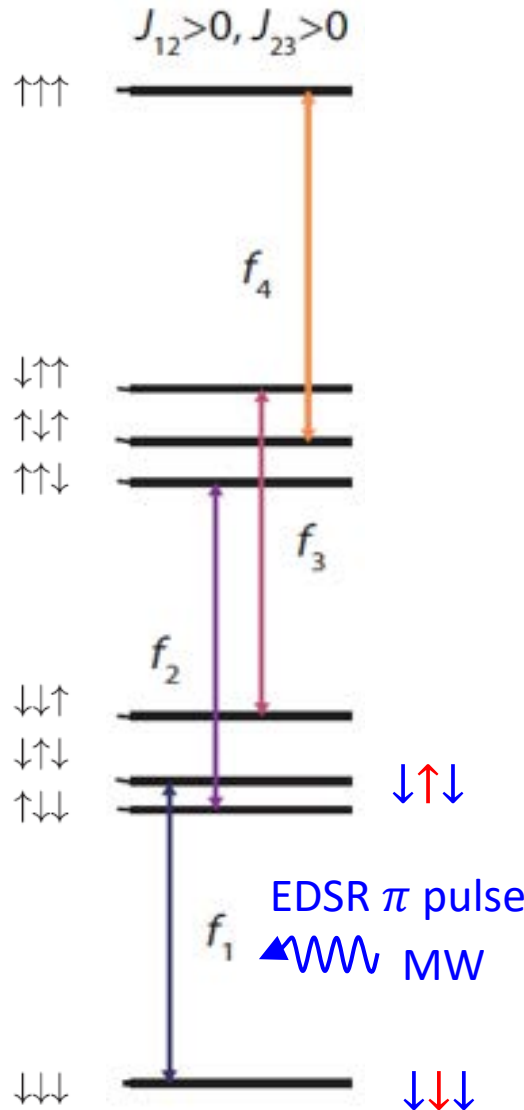
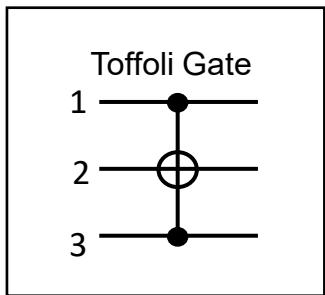


$\phi = \pi$

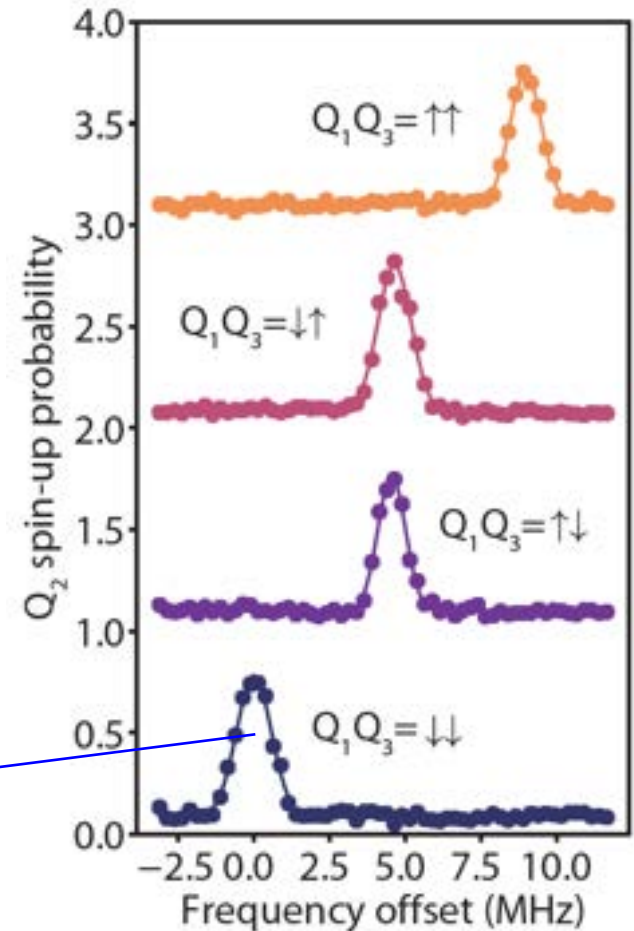


Error Correction by Single Step Toffoli Gate

K. Takeda et al. Nature 2022



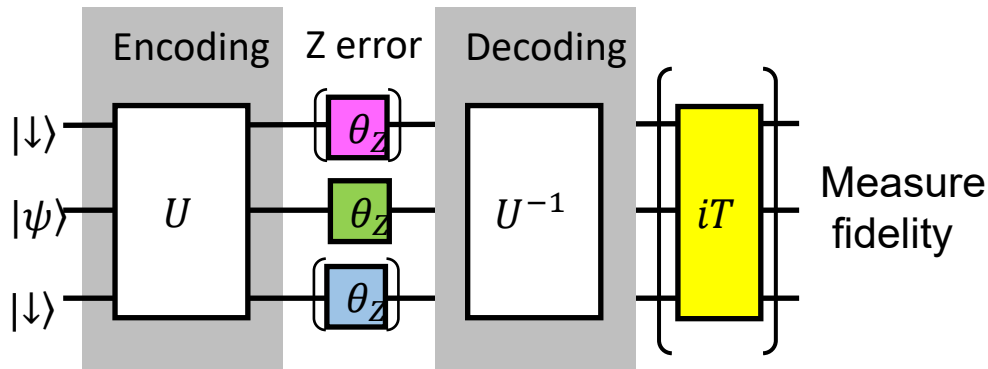
Flipping the center spin with the other two spins fixed



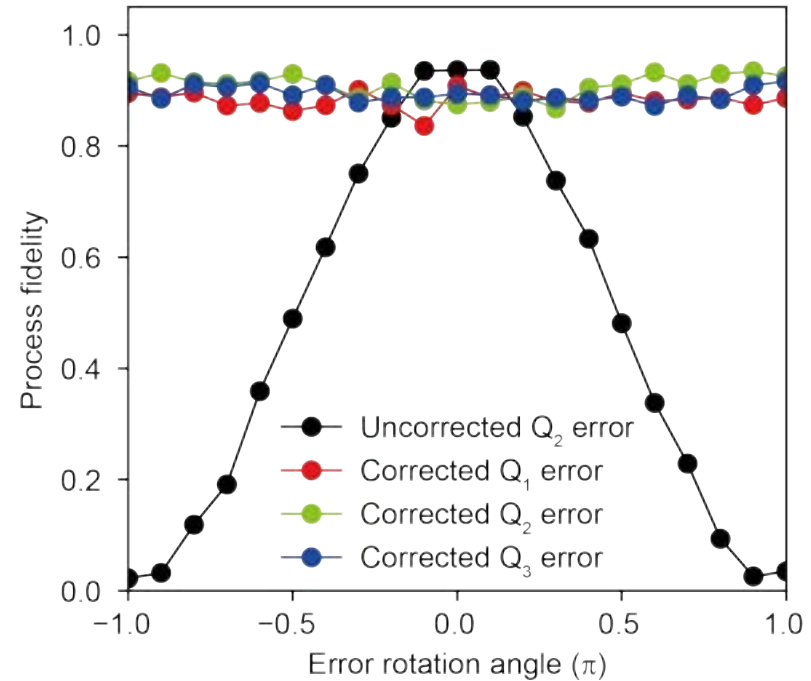
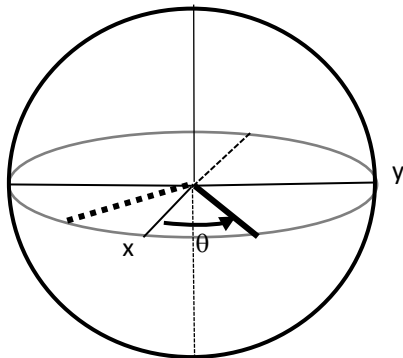
1 Qubit Phase Error Correction Experiment

K. Takeda et al. Nature 2022

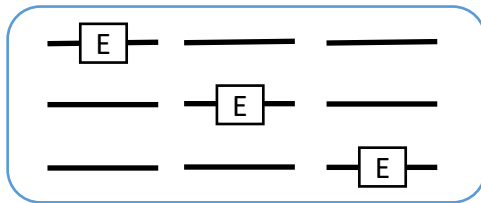
Nat.Si/SiGe



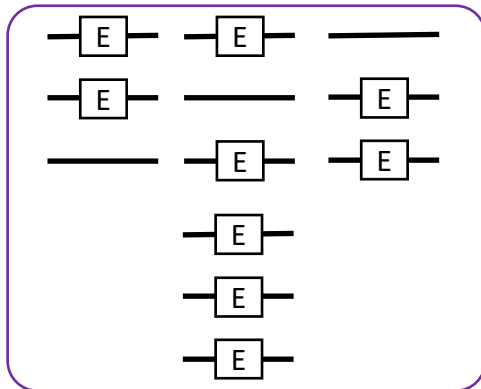
Phase error with angle θ



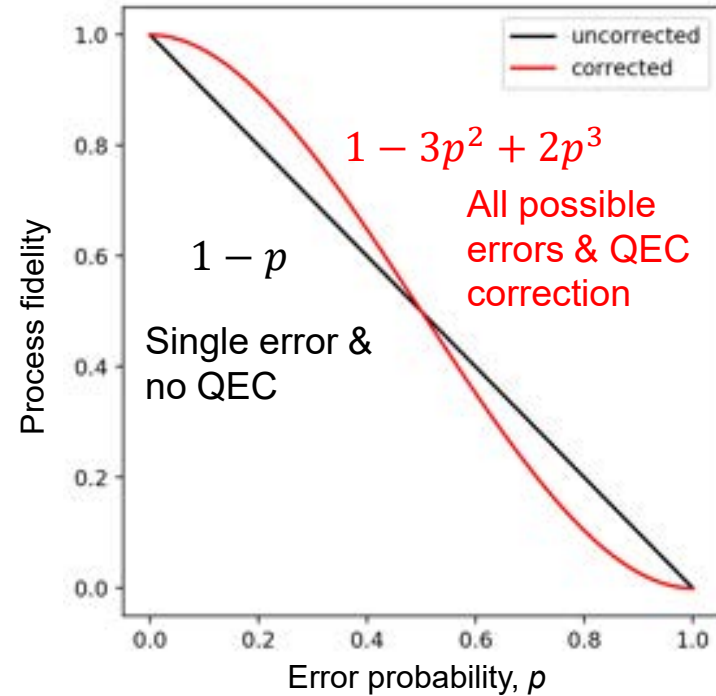
Outline of 3Q Quantum Error Correction



1Q error:
corrected



2Q & 3Q error:
uncorrected

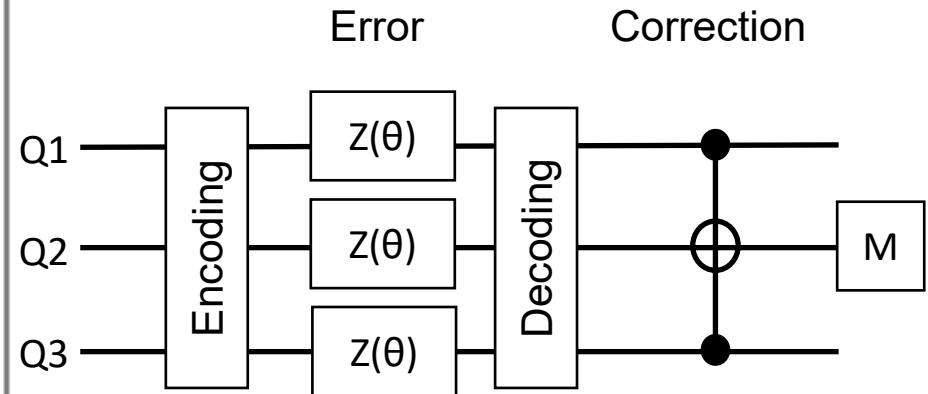
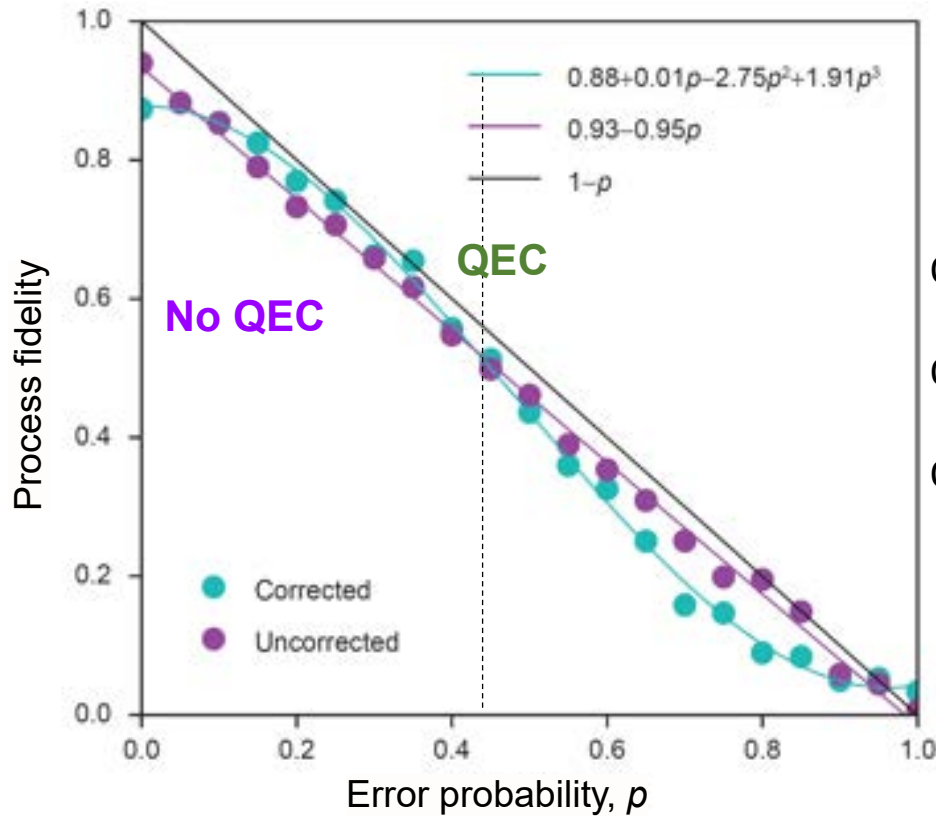


$$p = \sin^2 \theta / 2$$

- Corrected infidelity $1 - F(p) = O(p^2)$
- Improvement for $p < 0.5$ if all qubits have the same error rate

QEC for Three-qubit Phase Error

K. Takeda et al. Nature 2022



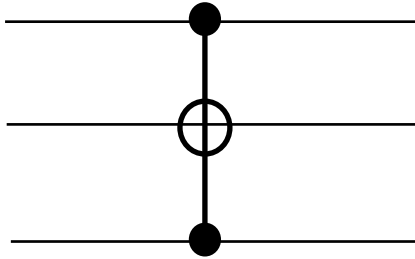
- Fidelity almost first-order insensitive to p
- Improvement for $p < 0.45$



Indication of presence of correlated phase error between qubits

Error Detection and Correction

Toffoli

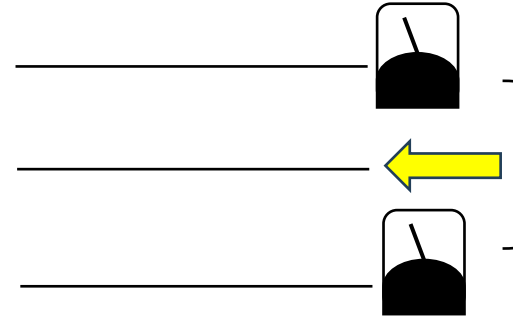


Fast

$$T_{\text{Toffoli}} < T2^* (\sim 10 \mu\text{sec})$$

Small code

Measurement & correction



Relatively slow to retain high $F > 99\%$

$$T^{\text{Meas}} > T2^*$$

Large code

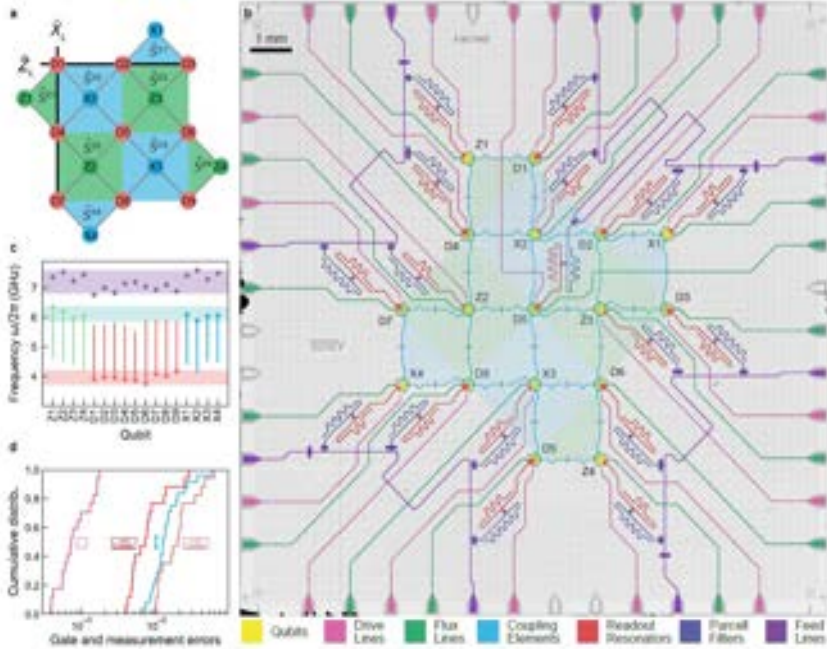


Fast ($< 1 \mu\text{sec}$) and High-fidelity ($> 99\%$) measurement

Realizing Repeated Quantum Error Correction in a Distance-Three Surface Code

Krinner et al. Nature 2022

17 physical qubits



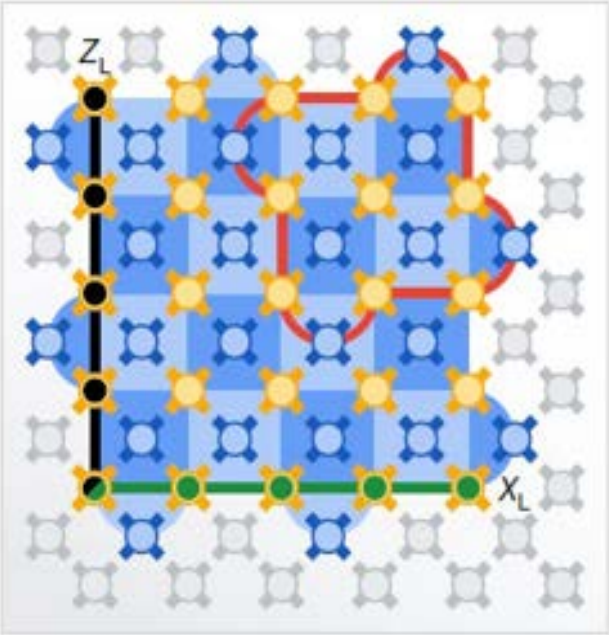
3x3 data qubits
 4 & 4 auxiliary qubits
 2 or 4 data qubit measurements

Suppressing quantum errors by scaling a surface code logical qubit

-Exceeding the QEC break-even point-

Google Quantum AI, Nature 2023

Superconducting 49 qubits



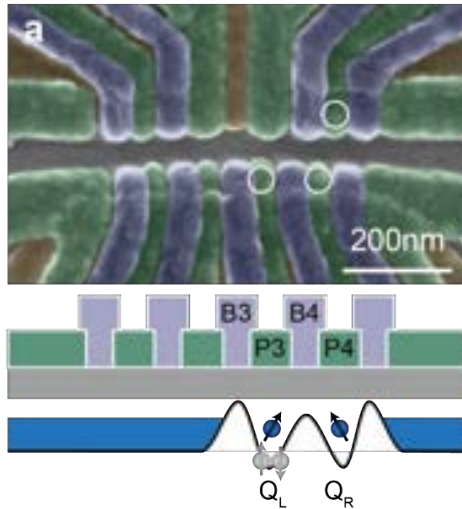
Distance 5
 5x5 data qubits
 24 measurement qubits

- Data qubit (d^2)
- Measure qubit ($d^2 - 1$)
- Unused
- Subset distance-3

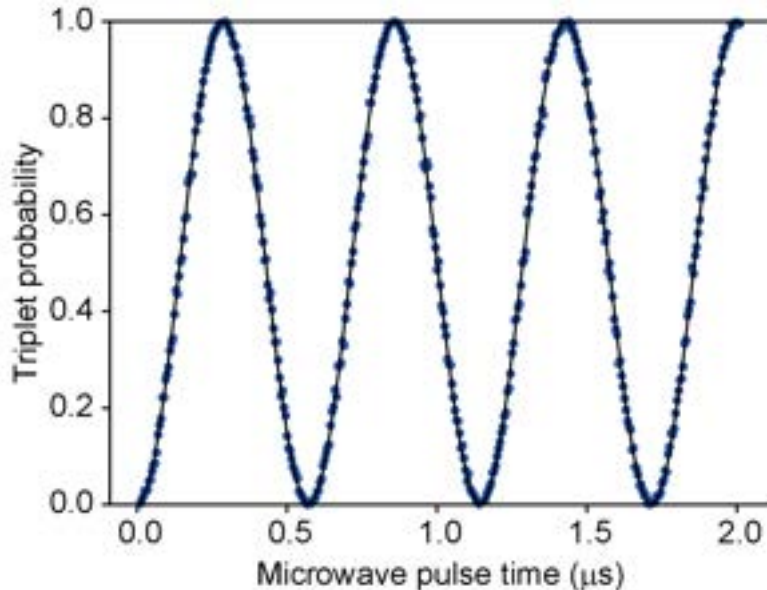
Fast, High-fidelity Spin Readout for QEC

K. Takeda et al. npj QI (2024)

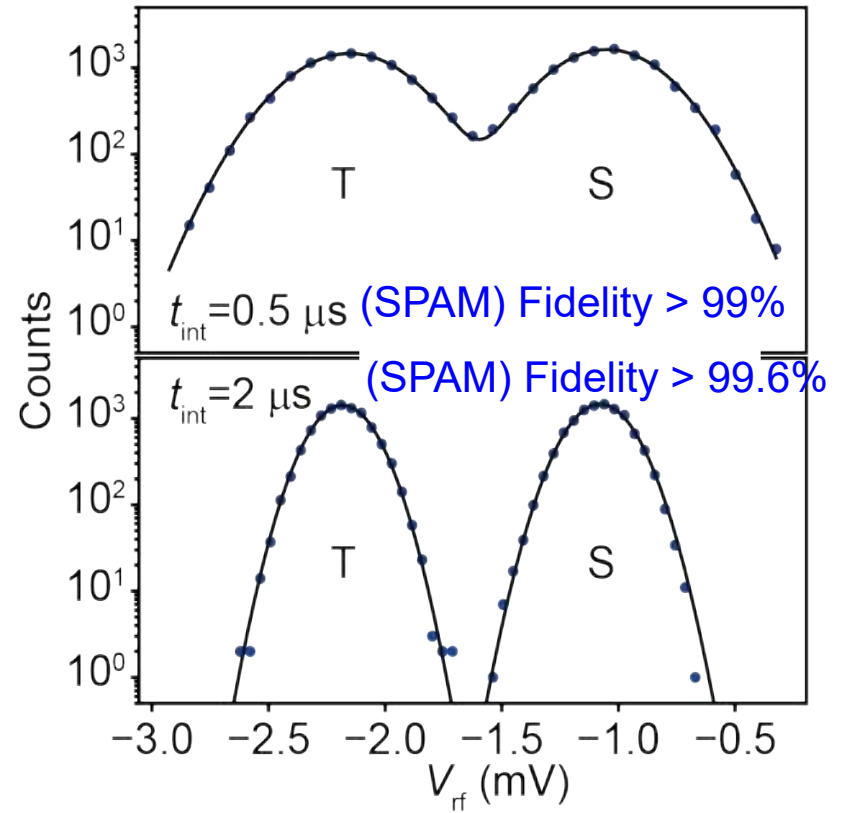
Singlet-triplet probability using Pauli Spin Blockade



$t_{\text{int}} = 3 \mu\text{s}$



RF reflectometry signal from charge sensor



Rabi visibility
= 99.6%

Initial. error : 0.2%

Part I Basics of semiconductor QC

- Concepts of quantum bits and computation
- Implementation of single and two qubit gates
- Readout and initialization
- Quantum coherence and phase noise

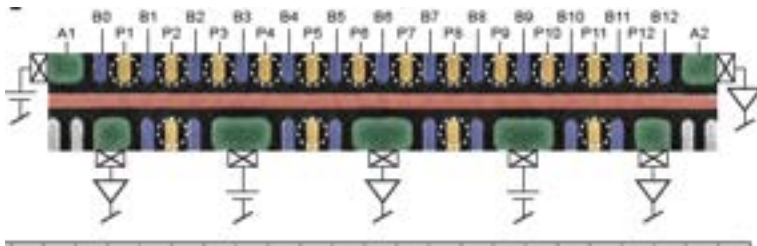
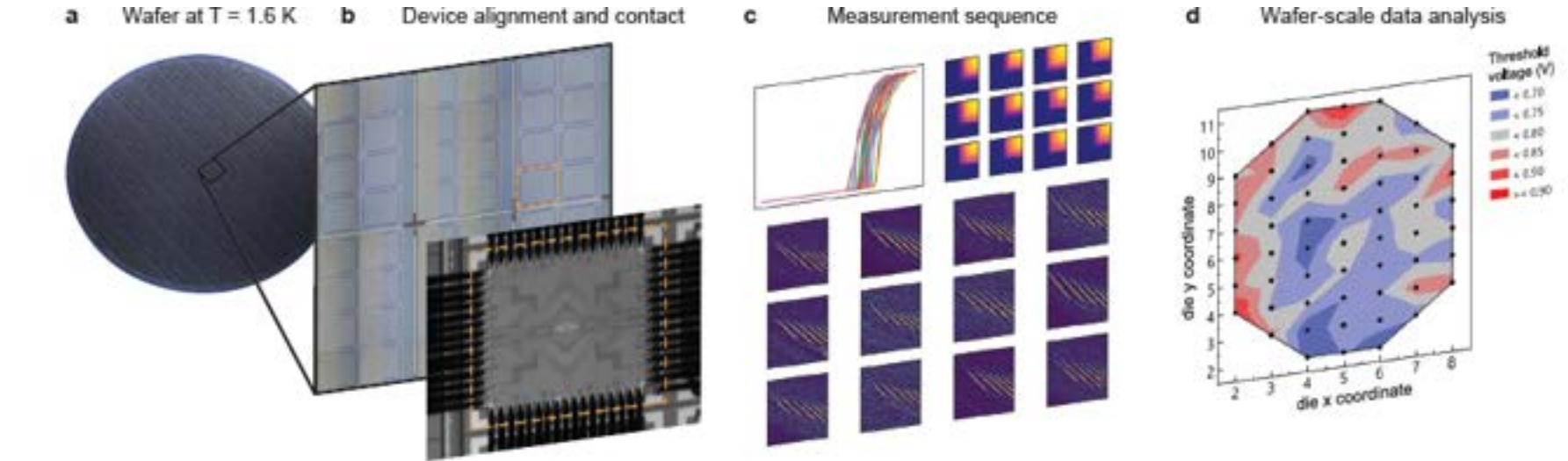
Part II Advances in semiconductor QC

- Features of quantum computing in silicon
- High-fidelity quantum gates and readout
- Quantum error correction
- Multi-qubit devices for scale-up

Probing single electrons across 300 mm spin qubit wafers

Intel

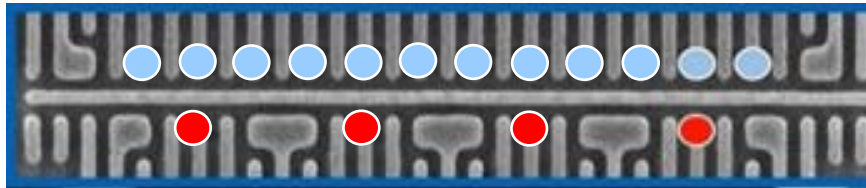
Neyens et al., arXiv: 2307.04812v1



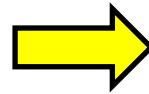
Component	Yield	Good count	Total count
Ohmics	100%	1624	1624
Gates	100%	10208	10208
Quantum dots	99.8%	3703	3712
12QD arrays	96%	223	232

Development of Multi-qubit Devices

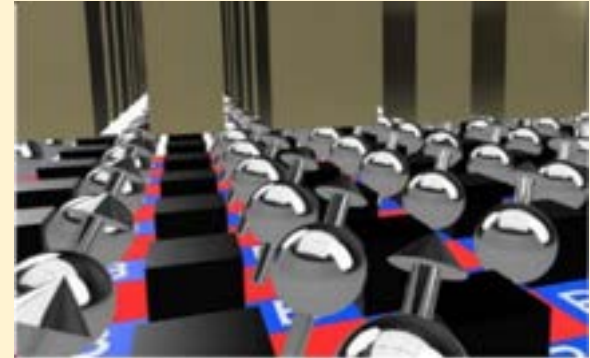
Industrial tech. for Si/SiGe and MOS 1D qubit array



2D array



Simulation of
 40×40 QD array



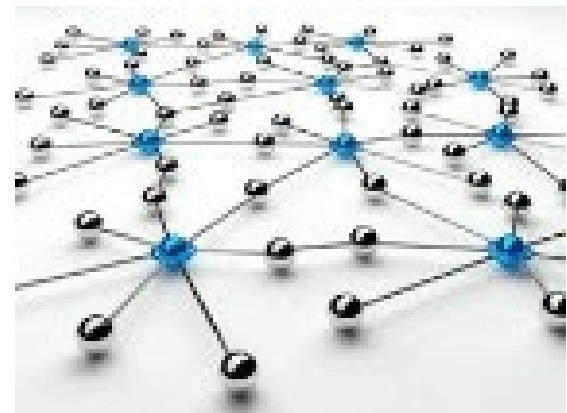
Tadokoro et al. Sci. Rep. 2021

12 qubit chips in Conf. talks
by J. Clark, Intel

Jun 15 2023

<https://www.intc.com/news-events/press-releases/detail/1626/intels-new-chip-to-advance-silicon-spin-qubit-research>

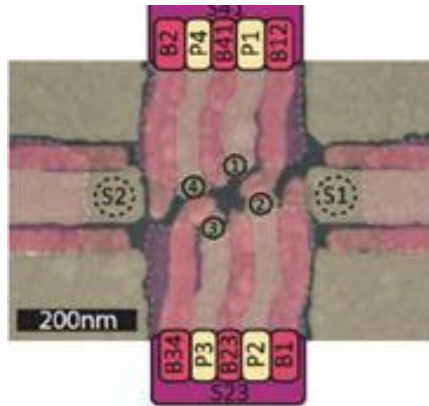
Quantum
link



Shuttling-based two-qubit gate
Noiri et al., Nat. Commun. 2022

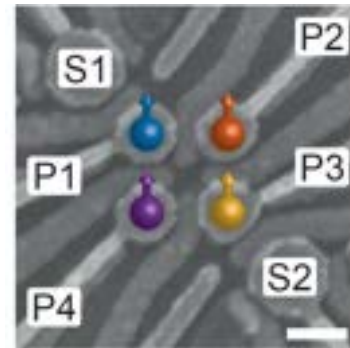
Toward Multiple Qubits

2x2 qubits in Si/SiGe



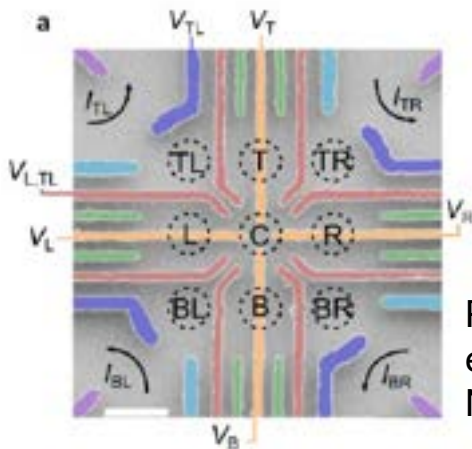
FK. Unseld et al. APL 2023
(APS March 2024)

2x2 qubits in Ge/SiGe QDs



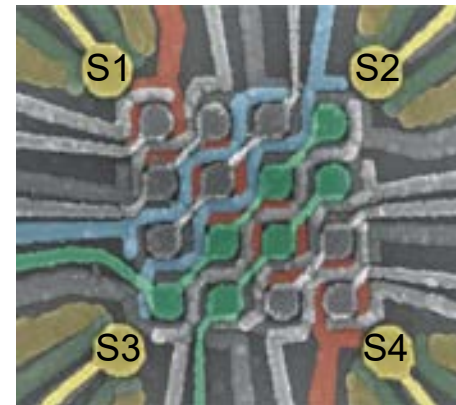
N.W. Hendrickx et al. Nature 2020

3x3 GaAs QDs



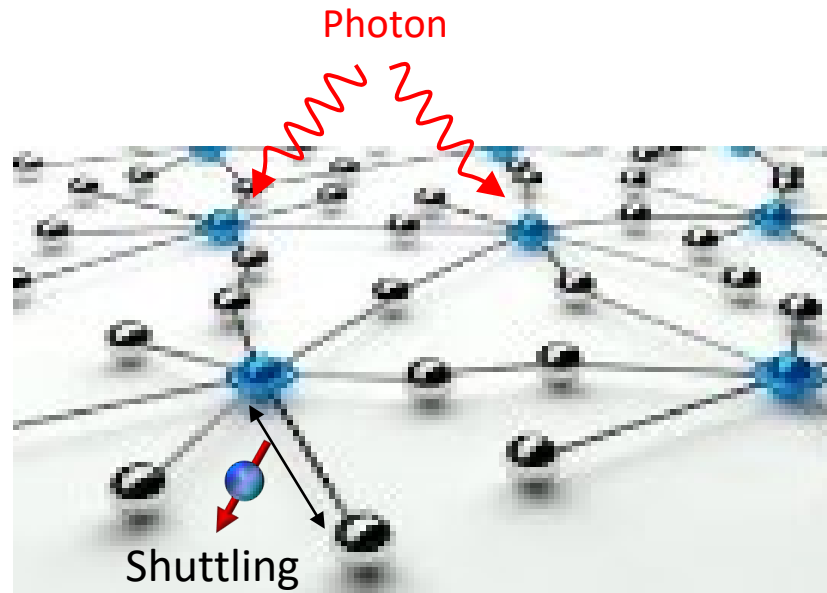
P-A. Mortemousque
et al. Nat.
Nanotechnol. 2020

4x4 Ge QDs with shared control



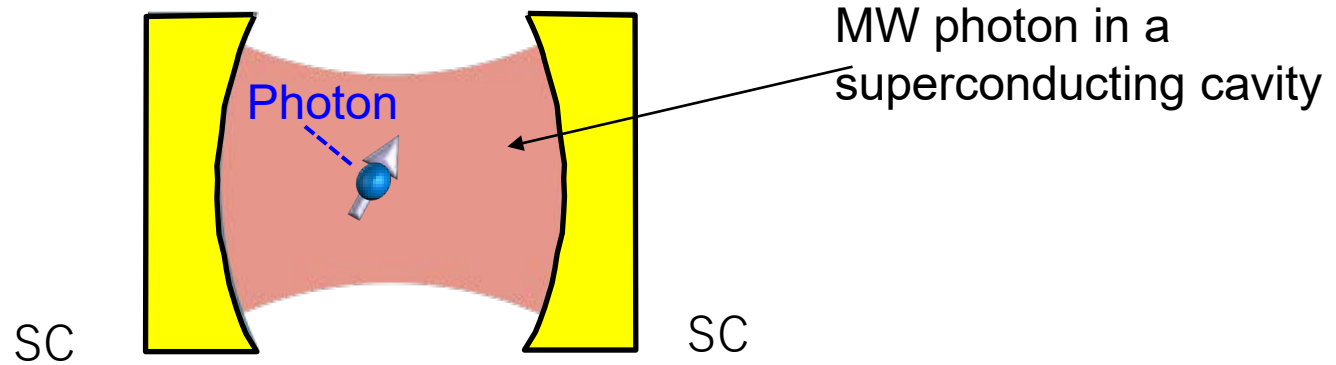
F. Borsoi et al. Nat.
Nanotechnol 2023

Quantum Links between Qubits

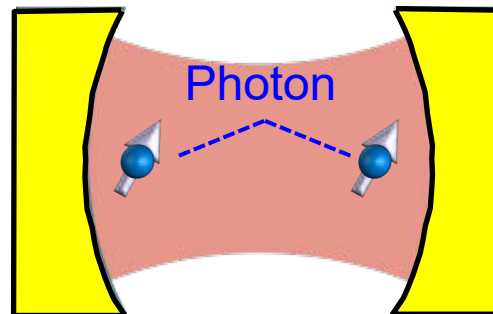


Quantum Link with Spin-photon Coupling

Spin-photon coupling

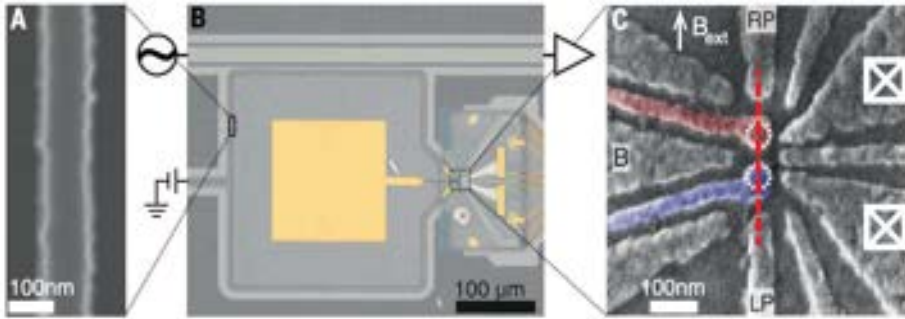


Photon-mediated spin-spin coupling

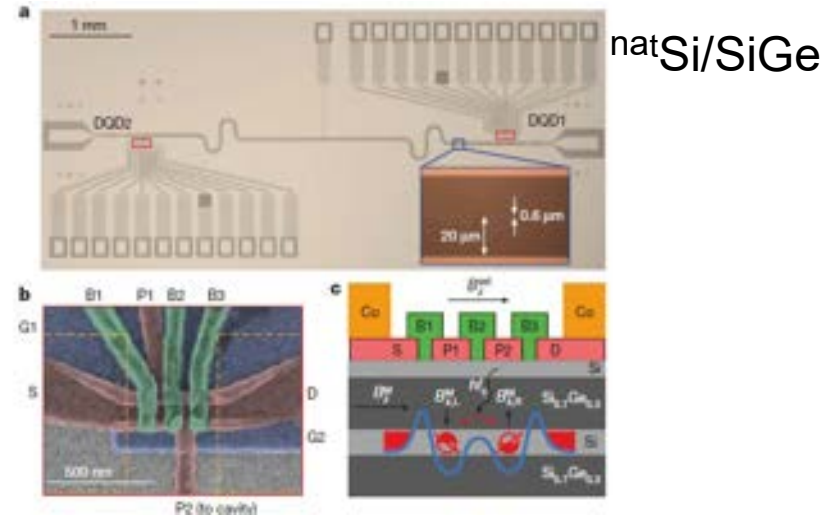


Spin-photon Coupling in a Superconducting Cavity

Spin-photon coupling in a superconducting resonator (~ 6 GHz) $^{28}\text{Si}/\text{SiGe}$



N. Samkharadze et al., Science 2018

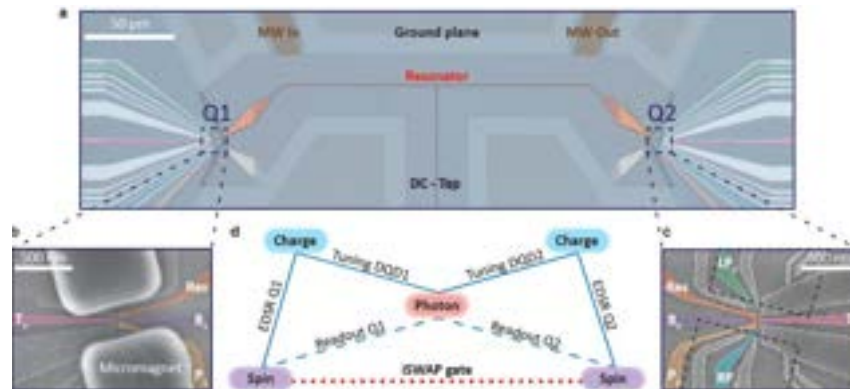


X. Mi et al., Nature 2018

Note: GaAs QD, A.J. Landig et al., Nature 2018;
Carbon nanotube. T. Cubaynes et al., npj QInfo 2019

Photon-mediated coupling of two spins over $250 \mu\text{m}$ apart

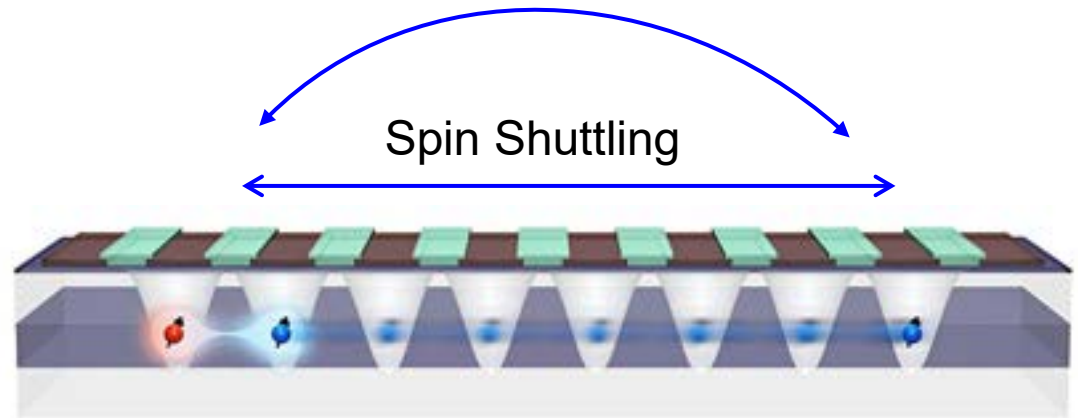
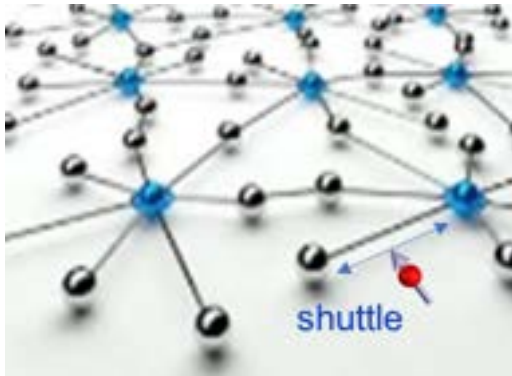
P. Harvey-Collard et al., PRX 12, 021026 (2022); J. Dijkema et al., arXiv:2310.16805v1



$^{28}\text{Si}/\text{SiGe}$

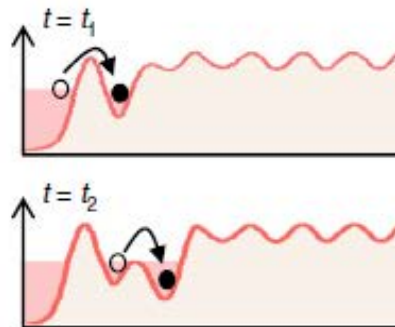
Quantum Link with Spin Shuttling

Gating using two distant spins

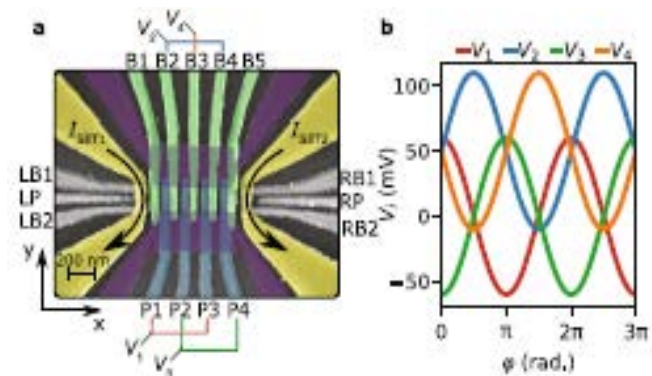


Electron shuttling

Bucket-brigade mode

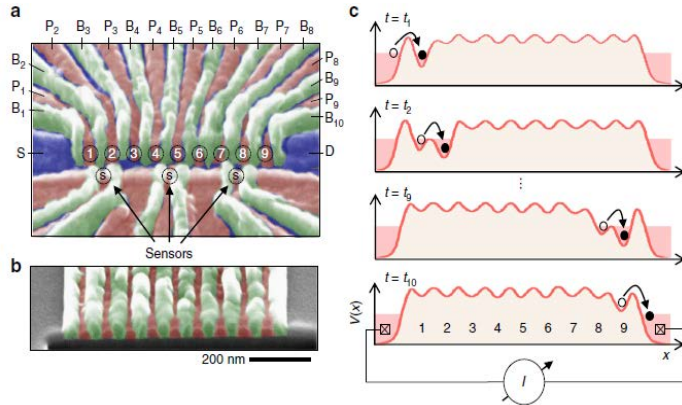


Belt-conveyor mode



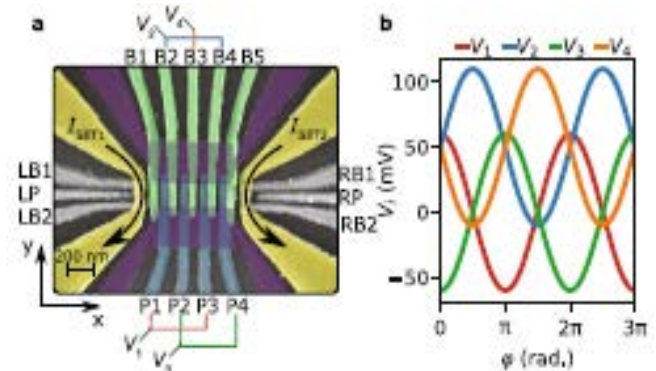
Spin Shuttling through QD Channels

Bucket brigade mode



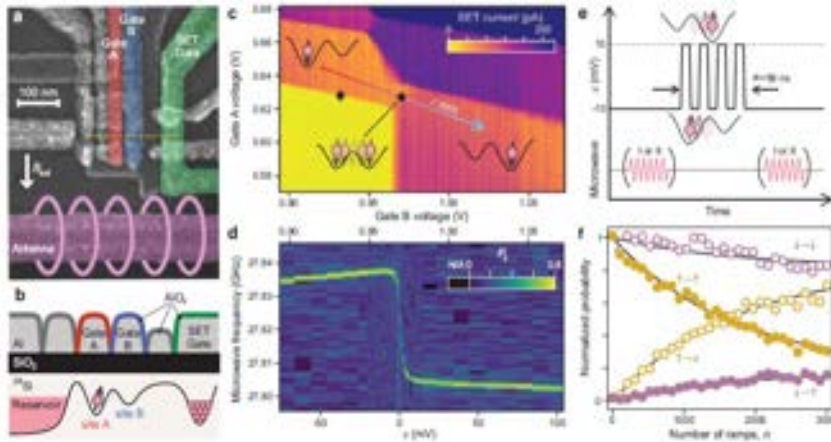
Charge move across 9 QDs in $^{28}\text{Si}/\text{SiGe}$
A.R. Mills et al., Nat. Commun. 2019

Conveyor-belt mode

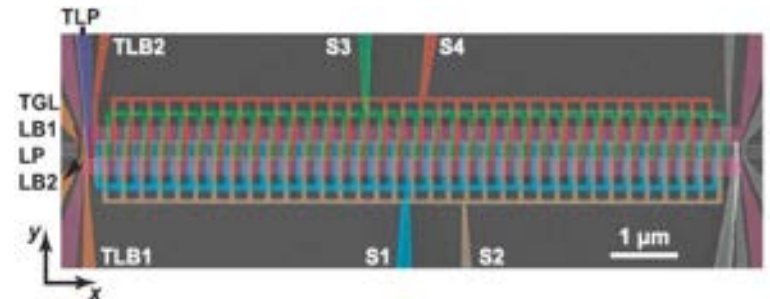


4 sinusoidal voltages for driving a spin
across 4 QDs (420 nm) in Si/SiGe
Single electron shuttling with $F=99.4\%$

I. Seidler et al., npj QuInfo. 2022



Spin move in DQD in ^{28}Si -MOS
Polarization $F=99.97\%$; Coherence $F=99.4\%$
J. Yoneda et al., Nat. Commun. 2021



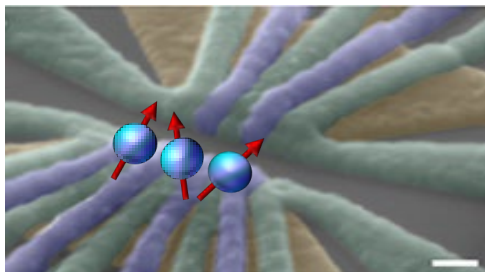
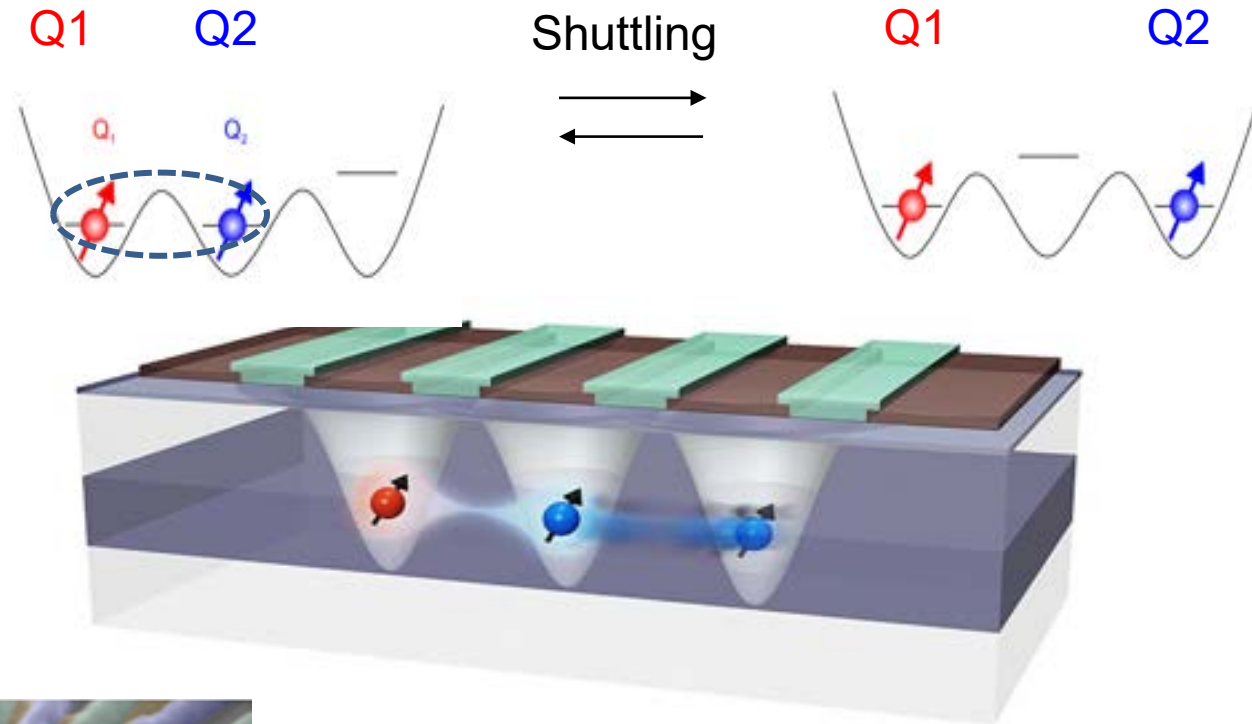
Spin shuttling across a 10 μm long channel
of 34 QDs (19 μm) in Si/SiGe
Single electron shuttling with $F=99.7\%$

R. Xue et al., Nat. Commun. 2023

Quantum Link between Distant Qubits

Exchange coupling on
between neighboring spins

Exchange coupling off
between distant spins



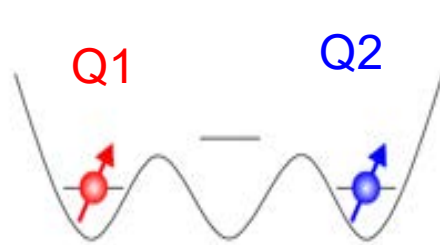
Shuttling Based CPHASE Gate in a Triple QD

A. Noiri et al. Nat. Commun. 2022

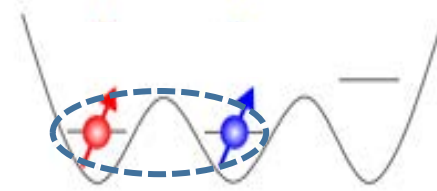
Exchange off before electron-move

Exchange on after electron-move

Transfer time
= 3 ns



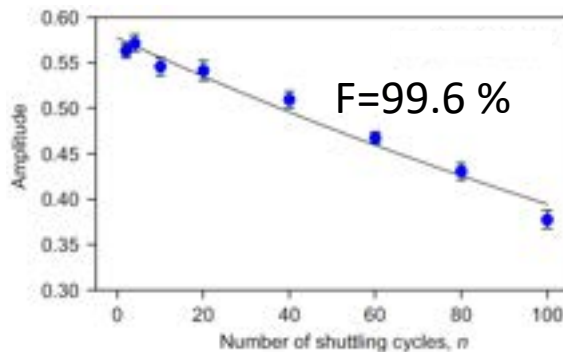
Shuttling
→
←



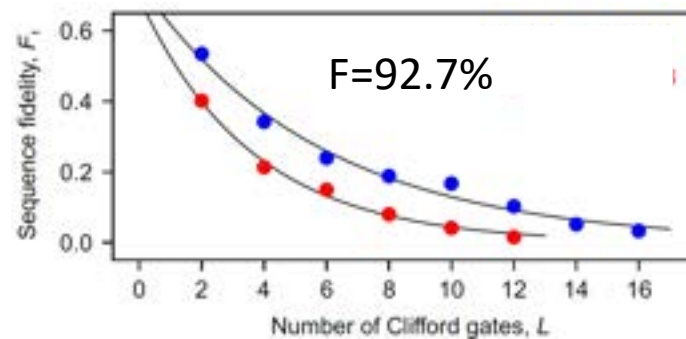
$T_2^* = 3$ to 4 us

CPHASE time
= 0.4 us

Shuttling



Two-qubit CPHASE gate



Limited by slow CPHASE

Summary

Basics of QC

- : Superposition, entanglement and computation

Implementation of semiconductor qubits

- : Spin qubits using concept of spin resonance

 - Two-qubit operation using spin exchange coupling

 - Readout and initialization

 - Spin dynamics

Operation of spin qubits

- : High-fidelity quantum gates

 - Error correction

Challenges for semiconductor QC

- : Multi-qubit devices

 - 2D qubit arrays and quantum links for scale-up